

RESEARCH TO DETERMINE FAILURE MODES FOR TRANSISTORS

CONTRACT #NAS 8-11059

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General Electric Company
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Syracuse, New York

Research to Determine Failure Modes for Transistors
 Contract #NAS 8-11059 5th Quarterly Report
 October - December 1964

Object

The object of this research is to study the effectiveness of screening transistors by stress and by non-destructive tests when applied to transistors manufactured to the same specification by three different processes.

The previous reports covered details of an initial step-stress experiment. A preliminary study of the effectiveness of using noise as a method of screening and a preliminary report covering partial details of the first 1,500 hours of a 3,000 hour life test.

This report shows the bulk of the data from a 3,000 hour life test of three separate processes to manufacture a transistor to the 2N718A specification.

Data in the form of computer calculated distributions for the complete test matrix consisting of:

- 3 - manufacturing processes
- 4 - stress screen conditions
- 10 - parameters
- 8 - test times
- 5 - Life test levels.

Engineering analysis of failures in the high stress screen on one process has been completed.

Abstract

A detailed analysis of failure modes has shown that planar transistors are subject to failures due to transient spikes. This failure mode causes serious damage if the transistor is not limited against thermal runaway.

This mode of failure is most prevalent among transistors which are considered least likely to have channeling modes of failure.

Preliminary computer readout of distribution of values is included with this report. This readout is not corrected for the combined effect of computer, data processing and automatic reading error.

The 250 readings on each transistor cause indicated failures to be several times actual.

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1.0 STATUS OF THE CONTRACT

1.1 Overall Status

The overall status of the contract as of 1 January 1965 is that all life tests have been completed on all lots. Final Phase II measurements are being made on all 800mw life tests.

Analysis is underway and has been completed for Process "A" on the high stress and moderate stress levels.

1.2 Work Remaining on the Contract

1.2.1 Analysis of Phase III life test data for centrifuge only lots and for the control lots in Process "A".

1.2.2 Analysis of Phase III for all lots in Process "B".

1.2.3 Analysis of Phase III for all lots in Process "C".

1.2.4 Centrifuge Phase IV in its entirety.

1.2.5 Analysis of Phase IV

1.2.6 Final analysis and report preparation

1.3 Extension Plans for the Contract

1.3.1 Design computer program to analyze all data to determine relation between noise tests and reliability.

1.3.2 Run and ~~ex~~ noise in relation to failures of the different major cl ~~ass~~ ations and determine the screening effectiveness of noise as a means of screening without life tests.

1.3.3 Use the computer program developed for noise readings to determine if application of screening to initial parameters other than noise will provide similar screening effectiveness.

1.3.4 Determine if noise tests made after the other screens for initial parameters will make a further improvement in reliability.

2.0 MAJOR PROBLEM AREAS IN PRESENT CONTRACT

2.1 Line Transients Plus Thermal Runaway

2.2 Failure Mode Description

One of the new failure mode problems facing the semiconductor industry is the effect of transient spikes which occur on power lines and are generated in other ways.

2.2 Failure Mode Description - Cont'd

Such transient spikes consist of very high peak voltages which appear on power lines due to the operation of various electrical equipment.

Transient spikes of much higher values also occur in every conductor during thunderstorm activities. The actual spike voltage is unknown but it is not unusual to observe arc over across several inches of space from an ungrounded conductor to a grounded conductor during thunderstorms.

Such arc over problems are of serious concern in Industrial Control Standards in N.E.M.A. activities. In this case semiconductor insulator spacing is much too small to meet the requirements for arc over protection.

The project engineer is serving at present on the task force to consider this problem.

In use most transistors must be protected from such high transient voltage spikes in a manner which limits the flow of current through the device to values which will not destroy the device.

Life test racks at General Electric were originally designed to permit thermal runaway when a momentary breakdown did occur. The philosophy was reasonable and though somewhat overcautious when applied to Germanium devices and to Alloy devices, it did guarantee a higher reliability.

The original argument was that a momentary breakdown indicates a defective transistor which should be eliminated.

During the change from alloy to planar construction the problem has developed due to the high impedance of the planar surfaces.

About the time of the start of this Life test, new test cards were introduced having a diode in the base as a protection against high reverse current in the base on a momentary overload.

Such cards were available in sufficient quantities to use at the higher levels with a delay of four weeks in getting the life test started.

The 500mw level was not expected to show problems without the diodes.

The analysis of data in relation to failure effects at the 500mw level failures compared to the failures at other power levels was conducted on Process "A" and covered in Section 3.0.

It is expected that the level of failures due to transient spikes is comparable in Process "B" and Process "C", but the level of miscellaneous failures at the 500mw level and the other levels is sufficiently higher and would be more likely to cancel the most valuable information.

2.3 Data Handling Problems

The data handling problem is very severe in this contract.

There are more than 250 readings, key punching or computer operations involved for each transistor on the test.

The 58 test lots show data assembled by the computer on approximately 10,000 separate sheets.

The percentage of error is reasonable, but the need for data handling reliability percentage is beyond the capability of either human operator or data processing equipment.

With the 250 operations per transistor an error rate of .008% would be required to hold to 2% errors in classification of a device as a failure.

A careful review of the data is required for a cross-check on each indicated failure. Computer system errors tend to show 2 to 5 times the number of failures which are unexplained.

There are only a few of the computer failures which can be identified and the ratio above probably is too low for a true picture of failures.

3.0 LIFE TEST RESULTS

3.1 High Stress Screen

3.1.1 Process "A"

Five lots were tested on the 3,000 hour life test from Process "A". The five lots were subjected to the power and temperature shown in the table.

Conditions for all lots were similar except that the 500mw had no reverse current protection in the base circuit, as explained in Section 2.

It was also found during the high stress experiment as reported in Quarterly Report #3, that a substantial number of units showed a shift in I_{CBO} after the temperature plus reverse voltage.

The units which did show this shift were divided with all units having a ("B" Class) shift of 1 micro-ampere or more sent to failure analysis. The units of the ("C" Class) 100nA to 100 micro-ampere, were divided and some included in the life test and some sent to failure analysis.

Units of the ("E" Class) 10nA to 100nA were included in the life test.

This division did provide the means of understanding the effect of decreasing the limits of leakage allowable.

This distinction ~~was~~ made only in the Process "A" units which shifted and completely recovered.

Some units which were shown to exceed initial limits on the beginning of the life test, were allowed to continue through the test.

Either type of unit is designated as screened out unit in the analysis.

3.1.1.1 Test Conditions High Stress Screen Life Test

Lot No.	419-201	419-202	419-203	419-204	419-205
No. in Lot	14	28	75	14	28
Acceptable	12	23	58	12	21
Screened Out	2	5	17	2	7
% Screened Out	14	18	23	14	25
Power in MW	800	700	*500	200	400
Temperature °C	25	25	25	150	150

*500mw test level was not protected by diode from transient triggered thermal runaway.

Test Limits Used to Define Failure

Test limits used for the classes of failure agree with the limits used in Quarterly Report #3, Page 11 reproduced here:

	G	E	C	B
I_{CEO}	10nA	10-100nA	100-1000nA	1 uA
I_{EBO}	10nA	10-100nA	100-1000nA	1 uA
* BV_{CEO}	40v	30-40v	20-30v	20v
BV_{CEO} % Shift	15%	25%	50%	50%
h_{FE}	40-120	35-40 & 120-150	28-35 150-180	28 or 180
h_{FE} % Shift	15%	15-25%	25-50%	50%
$V_{CE(SAT)}$	Not Used			
$V_{CE(SAT)}$ % Shift	15%	15-25%	25-50%	50%
$V_{BE(SAT)}$	Not Used			
$V_{BE(SAT)}$ % Shift	15%	15-25%	25-50%	50%

*The specification rates V_{CEO} as 32v maximum in the absolute limit. Test limits of BV_{CEO} are not given and the limit of 40 volts was chosen as representative of the entire distribution at the current chosen for the test.

3.1.1.2 Failures in Units Screened Out

This lot was tested as part of the full lot as reported on the distribution graphs (Figures 3.1.1.1 through 3.1.1.5).

Lot	419-201	202	203	204	205	Total
Good at End of Test	(G) (1)	(2)	(11)	(1)	(4)	(18)
Passes "E" Limit	(E) (0)	(2)	(2)	(0)	(0)	(4)
Passes "C" Limit	(C) 1	0	1	0	0	2
Fails (Bad)	(B) 0	1	0	1	1	3
Failures (B & C)	<u>1</u>	<u>1</u>	<u>1</u>	<u>1</u>	<u>1</u>	<u>5</u>

Numbers in () do not count as failures in (B+C)

3.1.1.3 Shifters in Units Screened Out

This table shows the units which shifted on any parameters in the units which were screened out.

	419-201	202	203	204	205	Total
15-25% Shift	(E) 0	0	(2)	0	0	(2)
25-50% Shift	(C) 0	0	0	0	0	0
Over 50% Shift	(B) 0	0	0	0	2	0
Shifters B+C	<u>0</u>	<u>0</u>	<u>0</u>	<u>0</u>	<u>2</u>	<u>0</u>

3.1.1.4 Screened Out Units which Responded to Life Test (Shifters & Failures to "E", "C", & "B" Limits)

Lot Number	419-201	202	203	204	205	Total
No. Screened Out	2	5	16	2	7	32
No. Responding	1	1	5	1	1	7
Failure Rate % Per "K" hours for 3,000 hour test			10.4			7.3

This shows the percent of units which responded in some way to the life test to be 10.4%/K hours for the 500mw units but this is above the 7.3 %/K hours.

If we count only failures at the 500mw (C+B) level the percent is very low with one failure in each lot.

3.1.1.5 Failures in the Life Test Lot Which Were Accepted by the Screen

Lot Number	419-201	202	203	204	205	Total
Number in Lot	12	23	58	12	21	126
Failure "C"	0	0	0	2	1	3
Failure "B"	2	2	7	0	0	11
Number Failed	<u>2</u>	<u>2</u>	<u>7</u>	<u>2</u>	<u>1</u>	<u>14</u>
Percent Failed	16.7	8.7	12	16.7	4.8	11.1
%/K Hours	5.6	2.9	4	5.6	1.6	

3.1.1.6 Shifted in Life Test

	419-201	202	203	204	205	Total
Shifted 15 to 25%	0	0	(6)	(2)	(2)	(10)
Shift 25-50% "C"	0	0	9	3	3	15
Shift Over 50% "B"	0	0	3	0	3	6
C&B Limits						
Percent to C&B	0	0	20.6	25	29	8
Rate %/K Hours	0	0	6.9	8.3	9.7	2.7

3.1.1.7 Total Number of Units Which Showed Some Response to Life Test
"E", "C", & "B" Limit Failures Plus "E", "C", & "B" Limit Shifters

	419-201	202	203	204	205	Total
Failed E	0	0	2	1	1	4
C	0	0	0	2	1	3
B	2	2	7	0	0	11
Shift E	0	0	6	2	3	11
C	0	0	9	3	3	15
B	0	0	3	0	6	9
Number Responded	2/12	2/23	27/58	8/12	14/21	53/126
Percent Responded	16.7	8.7	46.5	66.7	66.7	42.1
Rate in %/K Hours	5.6	2.9	15.5	33.3	33.3	14.0

3.1.1.8 Characteristics of the Devices Screened From the 500mw Lot

This table shows the failure items in the life test history of the lot each item is listed in accordance with the method used in Report #3 and #4. See Quarterly Report #3, Page 10, reproduced below.

Failure Tabulation Code for Correlation Tables -

Failures shown in the correlation tables are indicated by a three part code which consists of the 3 number groups shown below.

	<u>First Group</u>	<u>Second Group</u>	<u>Third Group</u>
1	I	1 Initial Value	G - Good
2	ICBO	2 After 1st Step	E - End of Life
	EBO		
9	BV	2S Shift on 1st Step	C - Catastrophic
	CEO		
13	h	3 After 3rd Step	B - Bad
	V _{FE}		
15	V _{CE(SAT)}	3S 3rd Step Shift	(limit passed)
16	V _{VE(SAT)}	4 After 4th Step	
660	Noise 100 μ 1MA	4S 4th Step Shift	
661	Noise 1000 μ 1MA		
662	Noise 1000 μ 30MA		
663	Noise 100KC 30MA		

In addition the second group is extended to include Steps 5 through 16 using 5S, 6S, etc. as the shift items for each step. Second group is extended as follows.

5 = 00 hours Phase III
 6 = 170 hours
 7 = 340 hours
 8 = 680 hours
 9 = 1,000 hours
 10 = 1,500 hours
 11 = 2,000 hours
 12 = 3,000 hours
 13 = 30KG Centrifuge Phase IV
 14 = 50Kg Centrifuge Phase IV
 15 = 90Kg Centrifuge Phase IV
 16 = 150KG Centrifuge Phase IV

3.1.1.9 Characteristics of the Transistor Screened from the 500mw Lot

Units Which Passed 500mw Tests

Unit No.	203	101			
A444	3	48	(1-2-E)		
A119	9	54	(1-2-E)	(9-3-E)	(9-4-E)
A364	31	78	(13-4S+E)		
A450	33	80	(13-4S+C)		
A122	35	83	(9-4-E)	(9-4S-E)	(13-2S+C)(13-3S+C) (13-4S+C)
A170	36	84	(9-3S-E)		
A261	53	102	(1-2-C)		
A430	57	106	(1-2-C)		
A438	58	107	(1-2-C)		
A542	61	110	(1-2-C)		
A344	66	115	(13-3S+E)	(13-4S+E)	

Units Which Showed "E" Limits on Life Test

A113	19	65	(13-4S+C)	(13-11-E)	(13-12-E)
A543	51	100	(1-2-C)	(9-2-E)	(9-4-E) (9-12-E)

Units Which Shifted "E" Limit on Life Test 15-25%

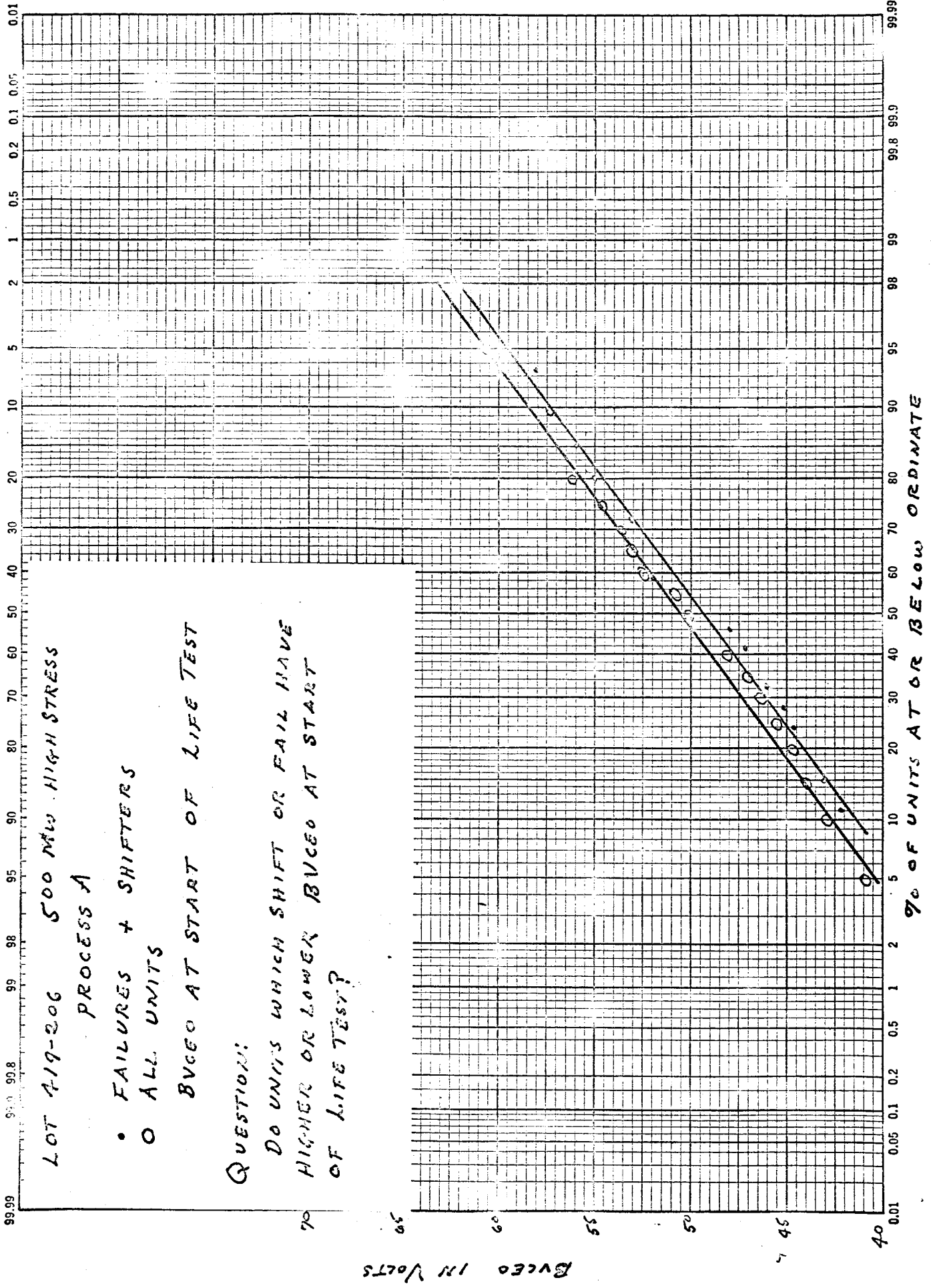
A149	27	73	(13-3S-E)	(15-9S+C)
A236	37	85	(9-3S-E)	(15-10S +E)

Units Which Failed Life Test

A-6	34	81	(1-2-E)	(13-4S-E)	(9-11S-E)	(9-12S-E)	(13-11S+C)	(13-12S+C)
-----	----	----	---------	-----------	-----------	-----------	------------	------------

From the above table we can see that units which shifted in I_{CBO} after temperature pulse reverse voltage (1-2-E) or 1-2-C) did not fail life test or shift on life test unless some other shift occurred, also No. A543 and No. A-6.

FIGURE 3.1.1.10.1



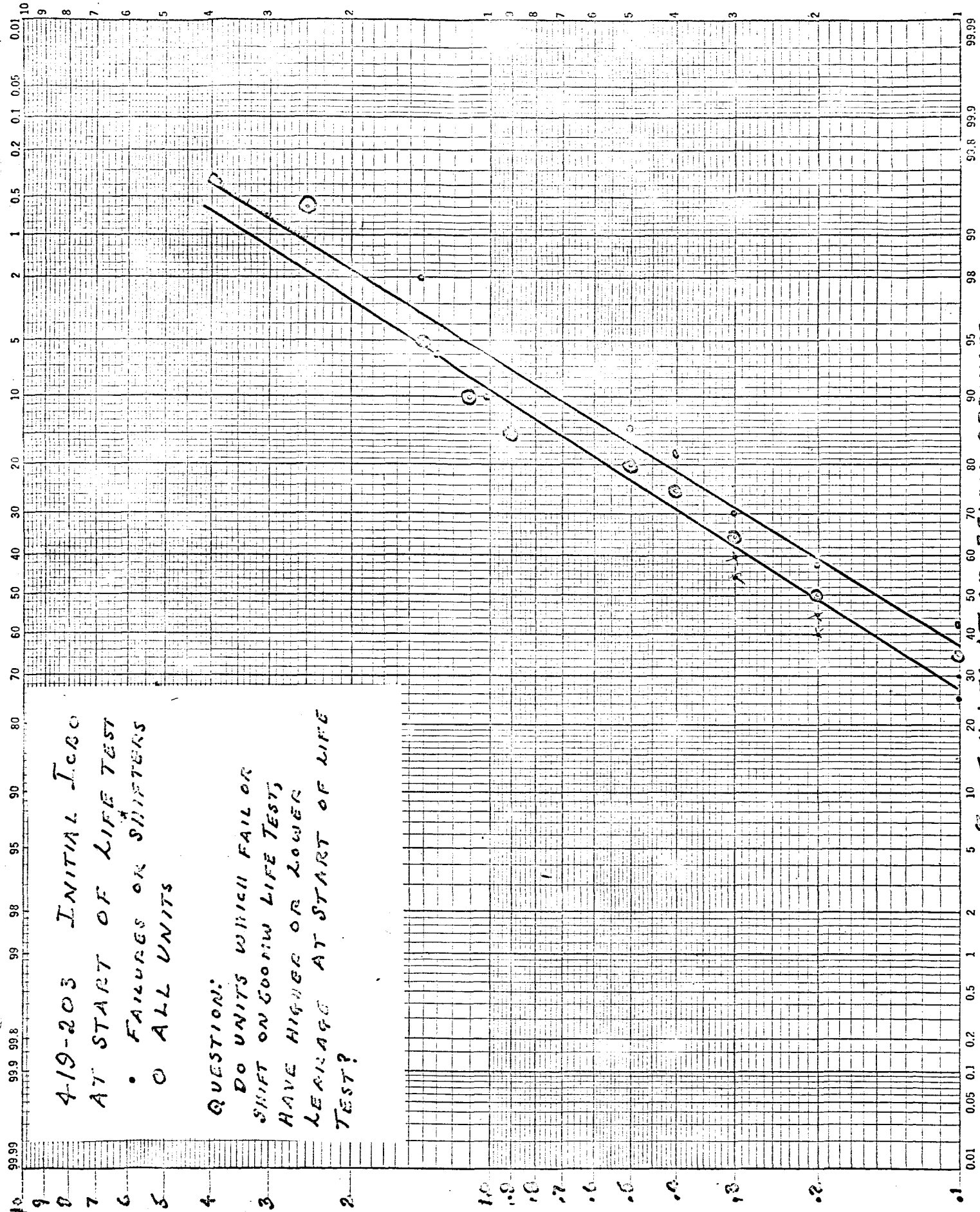
ROB Y SC
X 90 DIVISIONS
KEUFFEL & ESSER CO. MADE IN U.S.A.

BVCEO IN Volts

% OF UNITS AT OR BELOW ORDINATE

FIGURE 3.1.10.2

PROBABILITY X LOGARITHMIC
REPRESENTATION U.S.A.

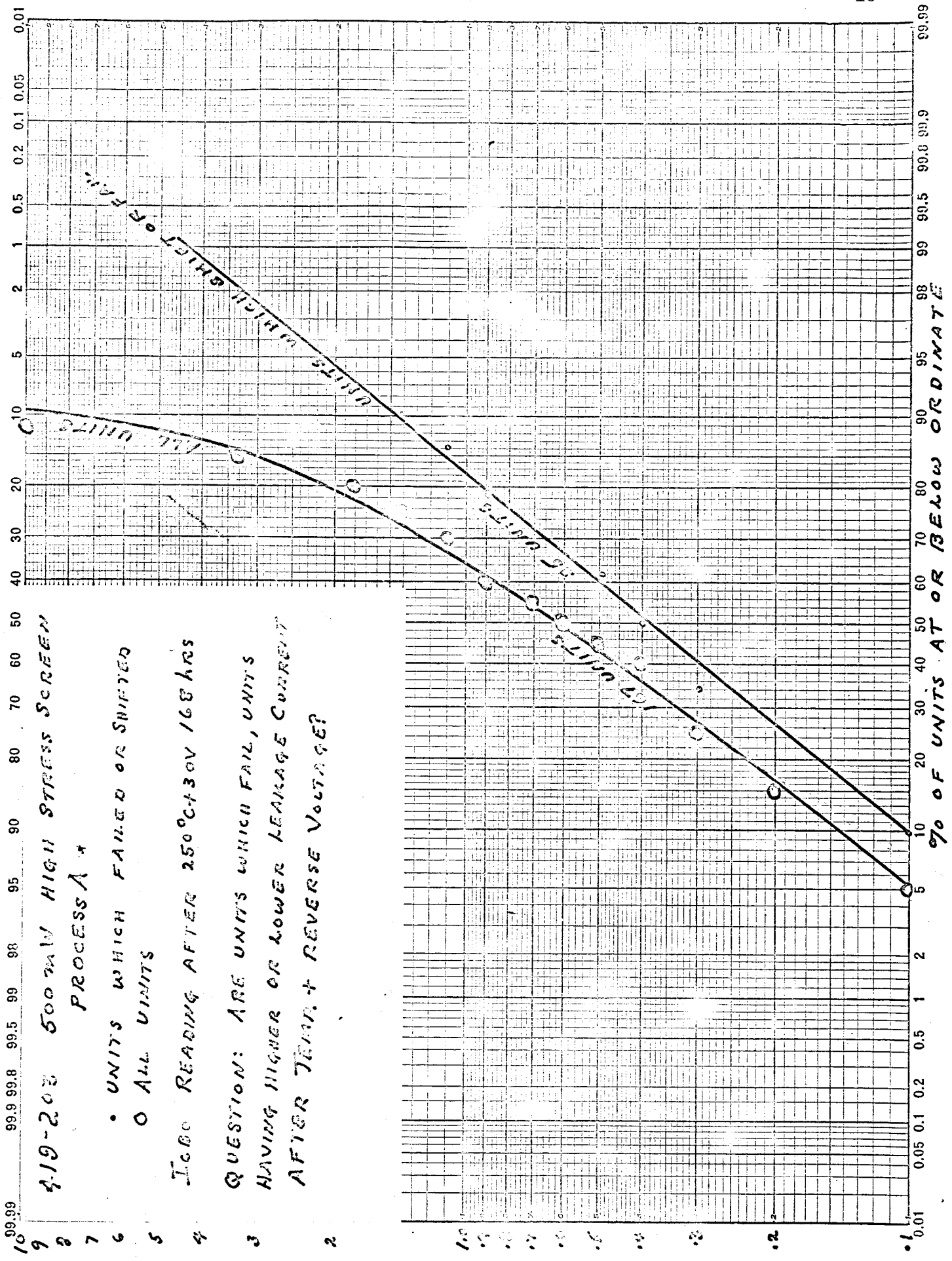


90 OF UNITS AT OR BELOW ORDINATE

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FIGURE 3.1.10.3

CODEx BOOK COMPANY, INC. NORWOOD, MASSACHUSETTS.
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4.19-203 500 MW HIGH STRESS SCREEN

PROCESS A *

- UNITS WHICH FAILED OR SHIFTED
- ALL UNITS

Tc60 READING AFTER 250°C+30V 168 HRS

QUESTION: ARE UNITS WHICH FAIL, UNITS
HAVING HIGHER OR LOWER LEAKAGE CURRENT
AFTER TEST + REVERSE VOLTAGE?

Tc60 IN THOUSANDS

% OF UNITS AT OR BELOW ORDINATE

3.1.1.10 Failure Mechanisms

The above suggests that a different failure mechanism is involved in the 500mw failures than that which is expected in I_{CBO} shift.

Figure 3.1.1.10.1 shows a comparative distribution of the BV_{CEO} for all units in the lot and for the units which failed at 500mw. This shows a suggestion that the expected BV_{CEO} is a cause when units are selected on an initial test. The results of the graph could be obtained by chance alone and a relation is not clear. Figure 3.1.1.10.2 shows the relation between I_{CBO} measured initially and the distribution of units. The percentage accuracy of I_{CBO} is apparent in this and also there is a slight indication that I_{CBO} does enter into the problem but there is no clear evidence. Figure 3.1.1.10.3 shows the comparison when I_{CBO} is measured after the temperature plus reverse voltage.

This distribution chart shows that the units which failed had a substantially lower I_{CBO} after temperature plus reverse voltage.

This is a reversal of the results that commonly would be expected and justifies further exploration.

The lot investigated in this distribution includes both the units which would be screened out by temperature plus reverse voltage as well as those which would be accepted by the screen.

The shape of the distribution curve for the units which failed indicate that less than 0.1% of the units which failed would have a leakage above 10nA after temperature plus reverse voltage.

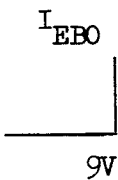
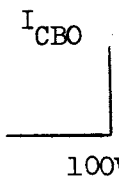
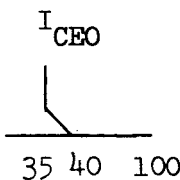
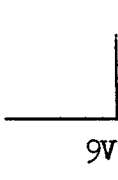
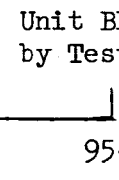
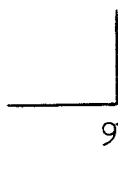
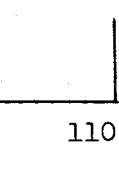
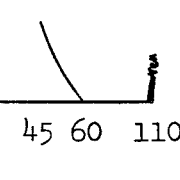
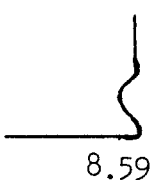
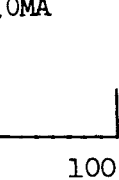
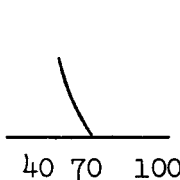
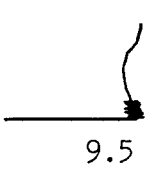
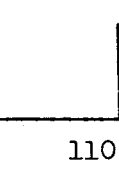
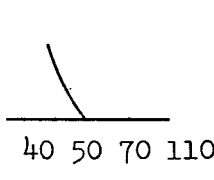
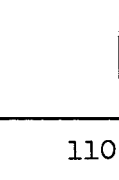
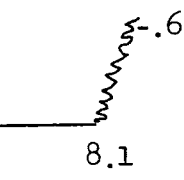
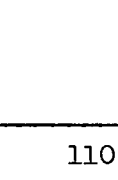
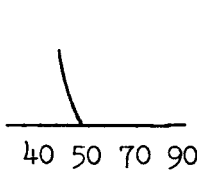
This indicates that the mechanism of failure by the 500mw test is directly opposite to failures by channeling.

The possibilities of this problem are further explored in Section 4.

3.1.1.11 Characteristics of the Devices Which were Screened Out of Life Test and Not Subjected to Life Test.

The following units were removed from the lot on Phase II and not subjected to Phase III.

Unit No	Phase III	Phase II
		101
A240	None	15 (1-2-B)
A285	None	45 (1-2-C)
A110	None	64 (1-2-B) (9-2S-C) (9-2S-E)
A186	None	74 (1-2-B) (9-2S-C)
A40	None	82 (2-3-13) (13-3-13) (13-3S-13) (16-3S-E)
A294	None	87 (2-1-C) (2-2-C) (2-3-B)
A192	None	135 (1-2-B) (9-2-B)

Unit	I_{EBO}	I_{CBO}	I_{CEO}	Notes
A240				Base Ring Melted in one spot
A285		Unit Blasted by Test 		Gold alloyed into silicon from base
A110				Gold alloyed into silicon at base
A186				Spot broken off AL base ring silicon
A192				Aluminum base ring melted in one spot
A40	Bad		Same as I_{CBO}	Out of alignment E-B junction too close to base aluminum ring
A294				Nothing visible

3.1.1.12 Truncation Screening

The theory of truncation screening as used in Quarterly Report #2, #3, and #4 is also shown in Technical Documentary Report RADC TDR-64-311 Rome Air Development Command.

Truncation screening is advanced as a means of detecting any condition which is out of normal.

3.1.1.12 Truncation Screening Cont'd

The theory as advanced in RADC or as used in the Quarterly Reports #2, #3, and #4 is that any out of normal condition within a device will cause one or more of the parameters to have a bi-model distribution. If such is true, eliminating the upper or lower percentiles of the distribution of same parameter, should improve reliability.

Paragraph 3.1.1.10 shows the difference in distribution of units which went through the high stress screen. In effect the percentage difference between failures and all units is very small when applied to I_{CBO} except I_{CBO} after temperature plus reverse voltage.

There may be an unjustified assumption in this reasoning because Lot 419-203 had the 7 units removed as bad prior to life test.

Figure 3.1.1.12.1 shows a comparison of units which either failed on the 500mW life tests or shifted more than 50%. The "B" level of failure and shifter is used for selection.

This shows that there is little difference between units which failed and all units.

The units which change in I_{CBO} due to temperature plus reverse voltage are clearly not the units which will fail.

The lot used in 3.1.1.12.1 includes all 500mw on the 4 lots for:

High Stress Screen	Lot 419-203
Moderate Stress Screen	419-208
Centrifuge Only	419-213
Control Lot	419-218

The above data indicates that the failure mode associated with 500mw failures is most likely to occur to the best units when judged by the high stress temperature plus reverse voltage.

Units which are most likely to form a channel are much less likely to fail due to the failure mode which is associated with the lack of diode protection against thermal runaway.

Truncation Screening to Other Parameters

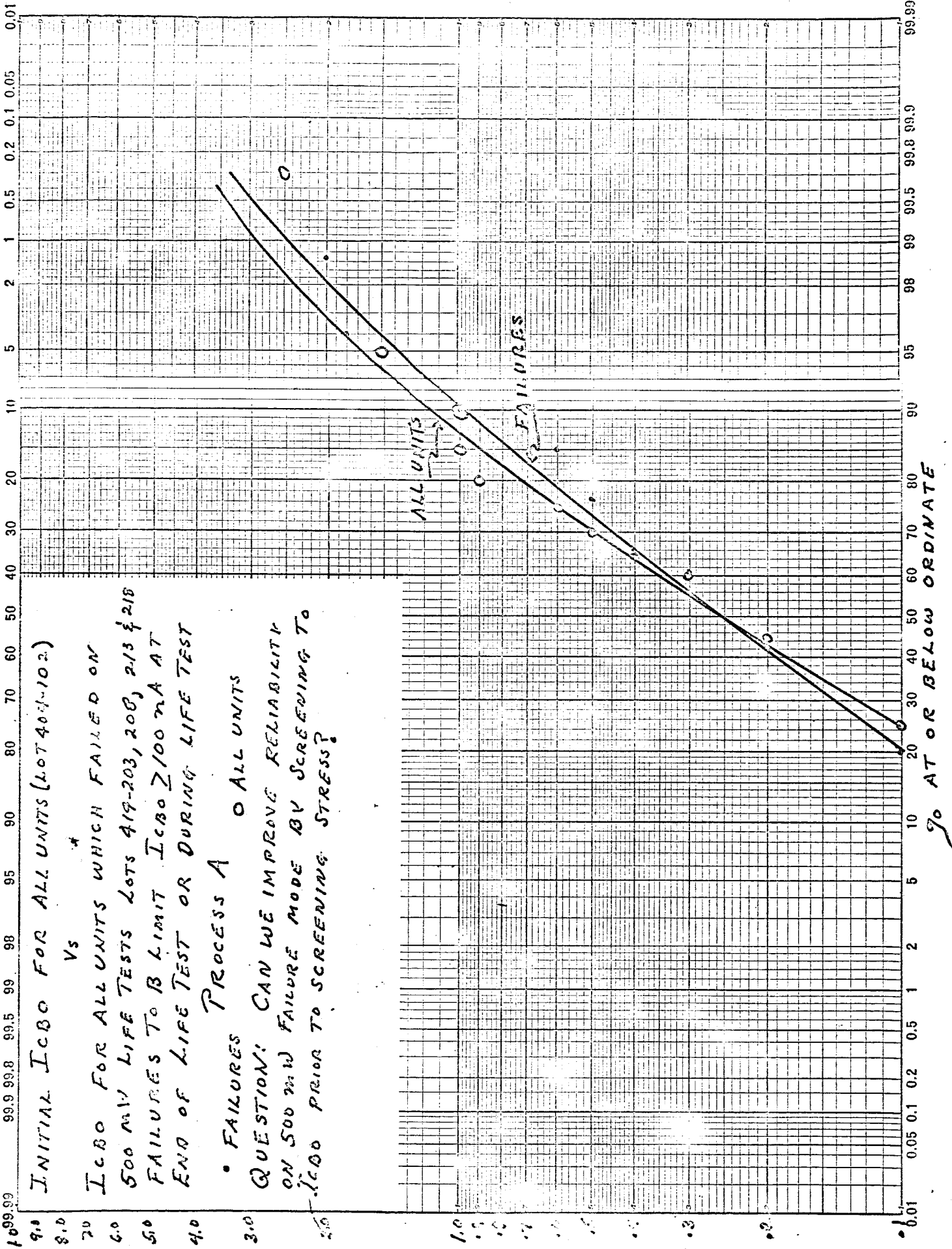
Table 3.1.1.2 shows the effect of truncation screening when applied to the control lot, which showed 11 failures to the "C" and "B" levels during the 3,000 hours.

If screened to remove the upper limit of I_{CBO} equal to the upper 15th percentile of the entire distribution, there would be no significant improvement in reliability.

Similarly upper 15th percent are removed on other parameters produces no results lower limits also produce no significant results.

FIGURE 3.1.12.1

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ICB0 IN 1000 HOURS

FIGURE 3.1.1.12.2
EFFECT OF SCREENING LOT 419-218 TO 15TH PERCENT POINTS
MEASURED AT START OF LIFE TEST

UNIT NO.	CLASS	1	2	3	4	5	6	7	8	9	REDUNDANT TRUNCATION SCREENING
		I _{CBO}	I _{EBO}	BV _{CEO}	h _{FE} HIGH LOW	V _{CE(SAT)} HIGH LOW	V _{BE(SAT)} HIGH LOW				
1					G						
2	B		B				(B)		(B)		2-6-8 B
3											
4								G			
5			G								
6				G					(G)		3-9 G
7		G					(G)		(G)		1-6-9 G
8				G							
9								G	(G)		7-9 G
10											
11			G				(G)		(G)		2-6-8 G
12	B										
13	C				C						
14	C										
15											
16											
17											
18		G			(G)			(G)	(G)		1-4-7-9 G
19											
20	C										
21	B				B						
22		G		G							
23			G			(G)					
24	C			C				(C)			
25					G		(G)		(G)		4-6-8 G
26	E										
27							G				
28	C	C	(C)			(C)			(C)		1-2-5-8 G
29								G	(G)		7-8 G
30											
31	E										
32	B					B					
33	B	B							(B)		1-9 B
34											
35						G					
36	E	E									
37											
38	B			(B)		(B)					3-5 B
Total	38	32	33	33	34	33	32	33	33	32	28
B	6	5	5	5	5	4	5	6	5	5	3
C	5	4	4	4	4	4	5	4	4	4	4
E	3	2	3	3	3	3	3	3	3	3	3
G	24	21	21	21	22	22	19	20	21	20	17
% E+G	71	72	73	73	73.5	76	69	70	72	71.8	71

Table 3.1.1.12.2

The effect of truncation screening at the 15% point when truncation is applied to initial parameters. Measured at beginning of Life test Step 5.

This shows no correlation between initial parameters and failure when truncation is applied to either a single parameter or to two or more parameters.

FIGURE 3.1.1.12.3
 SCREENING AFTER FIRST STEP (6) 419-218

UNIT NO.	CLASS	1	2	3	4	5	6	7	8	9	REDUNDANT TRUNCATION SCREENING
		I_{CBO}	I_{EBO}	V_{CEO}	h_{FE} HIGH LOW		$V_{CE(SAT)}$ HIGH LOW		$V_{BE(SAT)}$ HIGH LOW		
1											
2	B						B		(B)		6-9 B
3											
4								G		G	
5											
6				G							
7							G				
8				G							
9		G						G			1-7 G
10											
11											
12	B				B						
13	C	C	(C)		(C)						1-2-4 C
14	C									C	
15		G	(G)						(G)		1-2-8 G
16						G					
17											
18		G			(G)			(G)		(G)	4-7-9 G
19											
20	C										
21	B										
22				G						(G)	3-9 G
23						G					
24	C			C				(C)			3-7 C
25					G		(G)		(G)		4-6-8 G
26	E										
27			G		(G)		(G)				2-4-6 G
28	C	C							(C)		1-8 C
29								G	(G)		7-8 G
30							G				
31	E										
32	B					B					
33											
34											
35						G					
36	E										
37			G								
38	B			B		(B)					3-5 B
No.	38	33	34	33	33	33	33	33	33	34	26
B	6	6	6	5	5	4	5	6	5	6	4
C	5	3	4	4	4	5	5	4	4	4	2
E	3	3	3	3	3	3	3	3	3	3	3
G	24	21	21	21	21	21	20	20	21	21	17
%E+G	71	73	71	73	73	73	70	70	73	71	77

When the units are studied on the basis of removing devices which are out of limits on 2 or more 15th percent points there is also no improvement

Figure 3.1.1.12.3 shows the same comparison when tests are taken after the first 168 hours of operation.

This table shows no effect of truncation screening. A 7% improvement does show in use of inclusion in 2 or more fringes as a screening limit. There is no common pattern for the improvement and no conclusions are possible.

Table 3.1.1.12.2 The effect of truncation screening at the 15% point when applied after the first life test.

This shows no significant improvement in screening to an individual parameter but some improvement when screening is done to redundant truncation.

The fact that truncation screening has little or no effect on reliability tends to confirm that these failures are not related to degradation processes but due to the transient spike condition.

3.1.1.13 Characteristics of Failures at 800mw 419-201

Unit No.	III 201-	II 101-	No. in Lot =14
A528	8	9	Screened out failure (2-3-C) did not recover (2-12-C)
			Life Test Failure Not Screened Out
A492	7	8	(9-11+B) (13-11-B) (16-11+B) Open on 12
A74	1	2	(13-7-B) (15-7-B) Recovered after 7
			Screened Out Good on Life Test
A286	14	16	(9-2S-E) Recovered and no further change
			A74 may be an intermittent condition

3.1.1.14 Characteristics of Failures at 700mw 419-202

Unit No.	III	II	No. in Lot = 28
			Screened Out Units Good on Life Test
A417	18	2	(1-2-c) (1-10-E) (9-2S-E)
A583	2-	4	(1-2-E)
A355	27	11	(9-3-E) (9-4-E) (9-5-E)
A51	41	25	(13-2S-E)
			Failures
A479	29	13	Opened @ 1,000 hours
A388	26	20	Opened @ 1,500 hours
			Screened Out Failure
A412	28	12	(13-2S+C) (Opened at 8)
			All 3 Failures are definite failures

3.1.1.15 Characteristics of Failures at 200mw +150°C 419-204

Unit	204	10A	No. in Lot =14
			Screened out Good
A508	13	138	(13-2S-B) (13-3S-B) (13-4S-B)

Screened Out Failure

A589	14	139	(13-4S+E) (1-12-C) (9-12-B) (9-12S-B)(13-12S-B) In this case a shift in h _{FE} on centrifuge of 15 to 25% signaled a failure at 3,000 hours.
------	----	-----	--

Life Test Failures

A529	5	129	(9-11+E) (9-12+E) This would not be counted as a failure on normal end of life limits
------	---	-----	--

A353	3	127	(13-12-C) (13-11S-C) (15-10S-B)
A419	4	128	(1-9-#) (1-10-E) (1-11-C) (1-12-C)

Unit A419 is the only unit found in this lot which fails on the leakage mode of failure that was expected in the development of this screen.

Life Test Shifters

A252	2	126	(13-11S-E) (13-12S-E)
A201	11	136	(13-11S-E) (13-12S-E)
A419	1	125	(1-10-E) (1-11-E) (1-12-E) (15-10S-C)
A170	10	134	(1-11S-C) (1-12S+C)
A472	12	137	(13-12-C)

3.1.1.16 Characteristics of Failures at 400mw + 150°C

Lot 419-205 Units in Test 22 Units Screened Out but good on Life Test

Unit	205	101	
A108	3	142	(13-4S+E)
A88	13	152	(13-4S+E)
A160	16	155	(13-3S+E) (13-4S+C)
A171	26	165	(1-2-B) (9-2-B) (9-2S-B)

Screened Out Failures

A154	27	166	(1-6-C) (1-7-C) (13-3S+E) (13-4S+C) (1-12+B)
------	----	-----	--

This unit shows results of the screen as a means of removing leakage type failures

Screened Out Shifter

A382	9	148	(1-2-C) (13-11S-B)
A123	25	164	(13-5-E) (Through 13-9-E) (15-9S-B)

Life Test Failure

A423	11	150	(1-8-E)
------	----	-----	---------

Life Test Shifter

A412	10	149	(15-8S-E)
A169	17	156	(15-8S-E)
A597	1	140	(15-8S+C)
A181	5	144	(15-8S-C)
A131	14	153	(15-8S+C)
A269	6	145	(13-11S+B)
A158	15	154	(15-8S+B)
A216	19	158	(16-9S-B)

The shifting which occurs on the 8th readout to $V_{CE(SAT)}$ only is a shift which tended to both higher and lower levels. This is not understood at present. The occurrence of so many shifters at one step only must have some significance.

It is possible that instrument trouble may be an explanation though problem is not observed in the other readings made at the same time.

Other possibilities are changes in period between oven and test and in the way the unit was cooled on removal from 150°C.

Casual examination of failures at all four 500mw life test conditions show that failure mode is similar percentage of failures and that shifting in characteristics is much more pronounced in the 500mw life tests than in other life tests which had diode protection.

Casual examination of the data shows that this condition is present in process "B" units though somewhat complicated by a larger number of failure modes which are active in the lots.

A more detailed study of these failures will be completed in later quarterly reports.

3.1.1.17 Conclusions Relating to Process "A"

Failures in Process "A" units were mainly due to a failure mode which is probably associated with a better surface.

Evidence in this experiment tends to confirm the hypothesis that: Transient spikes on power lines or connections can cause minute thermal runaway conditions which cause shifting of the device characteristics and also cause destruction in a large number.

The problem is expected to become more serious as surfaces are improved because the voltage drop across a high impedance is much greater than across low impedances.

4.0 COMPUTER ANALYSIS FOR PARAMETER DISTRIBUTION

The working copies of the computer analyzed data is attached for advance information. This data is subject to the usual types of computer - automation errors as follows and is being corrected as part of the engineering analysis now underway.

4.1 Computer Errors

The program written for the computer cannot recognize the differences between an empty test socket and an open transistor.

If a transistor opens during a test it will be recognized by the computer for ICBO or I_{EBO} as a unit having very low leakage. The distribution is then calculated on the basis of the full number of units and the opened units as being very good. In practice the transistor may have progressively degraded in leakage, runaway and become open.

This makes the noticeable changes in improvement of the high end of the distribution. Correction for this error is difficult and requires manual computations.

A second form of error is due to mis-registration of cards and other normal types of trouble. These normally show up in groups of four numbers out of line. The computer accepts the error and includes this in the computed data.

4.2 Other Errors

Each transistor requires a total of 250 readings, mechanical or manual and key punch operations. The combined error rate then necessary to provide a 1% indicated failure rate is .004%. This is much too low for human operators or present automatic equipment.

4.3 Correction Procedure

Many of the computer errors can be eliminated by examination because a typical computer error is large and frequently occurs in groups of four or more times. Other cross checks are made as part of determining failure mode for each failure.

4.4 Examination in detail of the data has been completed through lot 419-228. Failures due to computer error are approximately five times as frequent as actual device failures. This only proves that computer error rate is somewhat less than 250 times as good as the probably failure rate.

PROCESS: A PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C. MIN 3.67. MAX 96.47. CELL NO.: 419201 NO. OF UNITS: 12

FRS.	ICBO (VCB - 60V) (Nanamps)			
	Init	168	340	680
Min	0.2	0.5	1.1	2.1
5%	0.2	0.6	1.1	2.1
10%	0.2	0.6	1.1	2.1
25%	0.3	0.7	1.2	2.2
50%	0.4	1.1	1.5	2.5
75%	0.7	1.5	2.0	3.0
90%	1.3	2.0	2.7	4.0
95%	1.5	2.3	3.1	4.5
Max	1.5	2.3	3.1	4.5

FRS.	IEBO (VEB - 5V) (Nanamps)			
	Init	168	340	680
Min	0.1	0.2	0.4	0.8
5%	0.1	0.2	0.4	0.8
10%	0.1	0.2	0.4	0.8
25%	0.1	0.2	0.4	0.8
50%	0.1	0.2	0.4	0.8
75%	0.1	0.2	0.4	0.8
90%	0.1	0.2	0.4	0.8
95%	0.1	0.2	0.4	0.8
Max	0.1	0.2	0.4	0.8

FRS.	BVCEO (IC - 0.1 ma) (Volts)			
	Init	168	340	680
Min	41	41	41	41
5%	41	41	41	41
10%	41	41	41	41
25%	43	43	43	43
50%	47	47	47	47
75%	50	50	50	50
90%	57	57	57	57
95%	58	58	58	58
Max	58	58	58	58

FRS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	-3	-4	-4
5%	-	-3	-4	-4
10%	-	-3	-3	-3
25%	-	-1	-1	-1
50%	-	0	0	0
75%	-	0	0	0
90%	-	+1	+1	+1
95%	-	+1	+1	+1
Max	-	+1	+1	+1

FRS.	VCE (SAT) (IC-50ma, IB-5 ma) (Mv.)			
	Init	168	340	680
Min	147	149	149	152
5%	147	149	149	152
10%	163	170	171	172
25%	204	203	197	204
50%	228	234	231	234
75%	275	280	284	285
90%	331	341	342	346
95%	375	379	376	380
Max	375	379	376	380

FRS.	VCE (SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	-1	-4	-1
5%	-	-1	-4	-1
10%	-	-1	-4	-1
25%	-	+1	0	+1
50%	-	+2	+2	+2
75%	-	+2	+3	+3
90%	-	+6	+6	+7
95%	-	+6	+6	+8
Max	-	+6	+6	+8

FRS.	VBE (SAT) (IC-50 ma, IB-5 ma) (Mv.)			
	Init	168	340	680
Min	785	784	785	787
5%	785	784	785	787
10%	785	785	789	783
25%	790	788	789	789
50%	794	791	792	794
75%	796	798	798	796
90%	807	811	815	813
95%	817	817	826	812
Max	817	817	826	812

FRS.	VBE (SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	-2	-12	-1
5%	-	-2	-12	-1
10%	-	-2	-7	-2
25%	-	0	0	-1
50%	-	0	0	0
75%	-	0	0	0
90%	-	+2	+3	+2
95%	-	+3	+4	+2
Max	-	+3	+4	+2

FRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	57	57	57	58
5%	57	57	57	58
10%	64	63	63	64
25%	78	80	74	80
50%	82	86	82	84
75%	91	93	93	93
90%	102	103	98	101
95%	103	106	99	104
Max	103	106	99	104

FRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-3	-7	-4
5%	-	-3	-7	-4
10%	-	-2	-4	-4
25%	-	+1	-3	-2
50%	-	+3	+1	0
75%	-	+6	+5	+9
90%	-	+8	+6	+11
95%	-	+8	+6	+11
Max	-	+8	+6	+11

FRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	57	57	57	58
5%	57	57	57	58
10%	64	63	63	64
25%	78	80	74	80
50%	82	86	82	84
75%	91	93	93	93
90%	102	103	98	101
95%	103	106	99	104
Max	103	106	99	104

FRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-3	-7	-4
5%	-	-3	-7	-4
10%	-	-2	-4	-4
25%	-	+1	-3	-2
50%	-	+3	+1	0
75%	-	+6	+5	+9
90%	-	+8	+6	+11
95%	-	+8	+6	+11
Max	-	+8	+6	+11

PROCESS: A PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C. MIN 1.8% MAX 9.8.2%

CELL NO.: 419202 NO. OF UNITS: 28

HRS.	ICBO (V _{CB} - 60V)(Nanamps)				
	Init	168	340	680	1000L50020003000
Min	<0.1	<0.1	<0.1	<0.1	<0.1
5%	<0.1	<0.1	<0.1	<0.1	<0.1
10%	<0.1	<0.1	<0.1	<0.1	<0.1
25%	0.1	0.1	0.1	0.1	0.1
50%	0.3	0.4	0.3	0.3	0.6
75%	1.0	1.9	1.3	0.9	2.4
90%	1.4	2.7	2.6	2.1	7.9
95%	2.1	3.0	4.0	4.5	20.8
Max	2.3	3.2	4.6	6.4	44.3

HRS.	IEBO (V _{EB} - 5V)(Nanamps)				
	Init	168	340	680	1000L50020003000
Min	<0.1	<0.1	<0.1	<0.1	<0.1
5%	<0.1	<0.1	<0.1	<0.1	<0.1
10%	<0.1	<0.1	<0.1	<0.1	<0.1
25%	0.1	0.4	0.1	0.1	0.1
50%	0.1	0.5	0.1	0.2	0.2
75%	0.2	0.6	0.2	0.3	0.5
90%	0.8	1.2	0.6	0.4	0.6
95%	2.3	1.6	1.2	0.8	0.7
Max	3.3	1.8	1.3	1.3	0.7

HRS.	BV _{CEO} (I _C - 0.1 ma)(Volts)				
	Init	168	340	680	1000L50020003000
Min	39	39	40	39	37
5%	40	40	40	39	37
10%	42	43	42	41	41
25%	45	45	45	45	45
50%	47	47	47	47	47
75%	52	52	52	53	55
90%	57	56	56	57	58
95%	59	58	58	58	58
Max	60	60	60	60	60

HRS.	BV _{CEO} (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-2	-3	-2	-5
5%	-	-2	-3	-2	-5
10%	-	-2	-2	-2	-3
25%	-	-1	-1	-1	-1
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	+2	+1	+2	+2
Max	-	+3	+1	+1	+2

HRS.	VCE(SAT)(I _C -50ma, I _B -5 ma)(Mv.)				
	Init	168	340	680	1000L50020003000
Min	145	148	146	149	149
5%	155	159	159	161	159
10%	171	172	173	177	179
25%	177	181	179	192	198
50%	207	210	211	219	223
75%	232	236	230	239	245
90%	263	265	264	272	279
95%	269	287	287	287	287
Max	273	304	305	305	305

HRS.	VCE(SAT)(% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-1	0	0	-1
5%	-	-1	0	0	-1
10%	-	0	0	0	-1
25%	-	+1	+1	+2	+1
50%	-	+2	+1	+3	+3
75%	-	+3	+3	+4	+5
90%	-	+5	+4	+10	5.87
95%	-	+10	+10	3.166	5.805
Max	-	+11	+12	5.787	5.854

HRS.	VBE(SAT)(I _C -50 ma, I _B -5 ma)(Mv.)				
	Init	168	340	680	1000L50020003000
Min	775	775	777	777	775
5%	779	780	784	779	779
10%	784	784	785	788	784
25%	787	787	787	790	787
50%	790	792	799	795	792
75%	794	795	792	798	797
90%	799	800	799	814	793
95%	813	816	811	816	811
Max	816	819	812	812	812

HRS.	VBE(SAT)(% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-1	-1	0	-1
5%	-	-1	-1	0	-1
10%	-	0	-1	0	-1
25%	-	0	-1	0	-1
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	+1	0	+1	+1
95%	-	+2	+1	+2	+2
Max	-	+2	+1	+1	+2

HRS.	hFE (I _C - 20 ma, VCE - 5V)				
	Init	168	340	680	1000L50020003000
Min	67	69	65	69	70
5%	68	69	65	70	70
10%	69	70	68	73	70
25%	74	74	73	76	71
50%	82	83	79	86	80
75%	89	89	87	88	91
90%	99	98	98	101	106
95%	105	104	106	104	113
Max	106	106	107	106	113

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-9	-11	-7	-7
5%	-	-7	-10	-4	-7
10%	-	-4	-9	-2	-7
25%	-	0	-5	0	-1
50%	-	+1	+1	+1	+2
75%	-	+3	+4	+3	+6
90%	-	+4	+6	+4	+10
95%	-	+6	+8	+6	+16
Max	-	+6	+8	+7	+20

HRS.	BV _{BE} (I _C - 0.1 ma)(Volts)				
	Init	168	340	680	1000L50020003000
Min	39	39	40	39	37
5%	40	40	40	39	37
10%	42	43	42	41	41
25%	45	45	45	45	45
50%	47	47	47	47	47
75%	52	52	52	53	55
90%	57	56	56	57	58
95%	59	58	58	58	58
Max	60	60	60	60	60

HRS.	BV _{BE} (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-2	-3	-2	-5
5%	-	-2	-3	-2	-5
10%	-	-2	-2	-2	-3
25%	-	-1	-1	-1	-1
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	+2	+1	+2	+2
Max	-	+3	+1	+1	+2

PROCESS: A PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.
 OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419203 NO. OF UNITS: 75

HRS.	ICBO (V _{CB} - 60V)(Nanoamps)				IEBO (V _{EB} - 5V)(Nanoamps)				BV _{CEO} (I _C - 0.1 ma)(Volts)				BV _{CEO} (% Change from Initial)												
	Min	5%	10%	25%	50%	75%	90%	95%	Max	Init	168	340	680	1000L	500C	2000	3000	Init	168	340	680	1000L	500C	2000	3000
5%	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	-96	-96	-96	-96	-96	-96	-96	-96
10%	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	-1	-1	-1	-1	-1	-1	-1	-1
25%	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	<0.1	-1	-1	-1	-1	-1	-1	-1	-1
50%	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0	0	0	0	0	0	0	0
75%	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0.4	0	0	0	0	0	0	0	0
90%	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	1.1	0	0	0	0	0	0	0	0
95%	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.4	0	0	0	0	0	0	0	0
Max	2.5	101.2	229	10.2	21ma	7.8	9.3	350										+2	+1	+1	+2	+2	+2	+2	+2

HRS.	VCE(SAT)(I _C -50ma, I _B -5 ma)(Mv.)				VBE(SAT)(I _C -50 ma, I _B -5 ma)(Mv.)												
	Min	5%	10%	25%	50%	75%	90%	95%	Max	Init	168	340	680	1000L	500C	2000	3000
5%	142	146	144	147	148	148	147	147	147	779	772	772	772	772	772	772	772
10%	160	157	159	160	157	159	159	159	159	783	784	783	783	783	783	783	783
25%	172	174	173	170	165	168	168	168	168	785	786	786	786	786	786	786	786
50%	202	203	204	203	204	203	203	203	203	788	789	789	789	789	789	789	789
75%	227	231	227	227	227	227	227	227	227	790	791	791	791	791	791	791	791
90%	265	269	270	270	267	266	266	266	266	793	792	792	792	792	792	792	792
95%	353	356	350	359	367	367	367	367	367	795	808	808	808	808	808	808	808
Max	400	403	406	499	500	500	500	500	500	800	823	824	824	824	824	824	824

HRS.	VCE(SAT)(% Change from Initial)				hFE (% Change from Initial)				
	Min	5%	10%	25%	50%	75%	90%	95%	Max
5%	-1	-2	-2	-1	-1	-1	-1	-1	-1
10%	-1	-2	-1	0	0	0	0	0	0
25%	0	-1	-1	0	0	0	0	0	0
50%	+1	+1	0	+1	+1	+1	+1	+1	+1
75%	+2	+2	+1	+3	+3	+3	+3	+3	+3
90%	+3	+3	+2	+4	+4	+4	+4	+4	+4
95%	+5	+5	+5	+5	+5	+5	+5	+5	+5
Max	+6	+9	+9	+14	+14	+14	+14	+14	+14

HRS.	VCE(SAT)(I _C -20 ma, V _{CE} - 5V)			
	Min	5%	10%	25%
5%	48	41	41	20
10%	61	64	65	51
25%	77	74	73	69
50%	86	83	82	78
75%	92	86	89	84
90%	99	97	99	99
95%	104	101	103	103
Max	119	116	116	118

HRS.	VBE(SAT)(% Change from Initial)			
	Min	5%	10%	25%
5%	-3	-3	-3	-3
10%	-1	-1	0	-1
25%	0	0	0	0
50%	0	0	0	0
75%	0	0	0	0
90%	+2	+2	+2	+3
95%	+4	+4	+4	+4
Max	8	8	8	8

HRS.	hFE (% Change from Initial)			
	Min	5%	10%	25%
5%	-19	-19	-19	-19
10%	-10	-10	-10	-10
25%	-9	-9	-9	-9
50%	-6	-6	-6	-6
75%	-3	-3	-3	-3
90%	0	0	0	0
95%	+1	+1	+1	+1
Max	+2	+2	+2	+2

HRS.	hFE (% Change from Initial)			
	Min	5%	10%	25%
5%	-19	-19	-19	-19
10%	-10	-10	-10	-10
25%	-9	-9	-9	-9
50%	-6	-6	-6	-6
75%	-3	-3	-3	-3
90%	0	0	0	0
95%	+1	+1	+1	+1
Max	+2	+2	+2	+2

HRS.	hFE (% Change from Initial)			
	Min	5%	10%	25%
5%	-19	-19	-19	-19
10%	-10	-10	-10	-10
25%	-9	-9	-9	-9
50%	-6	-6	-6	-6
75%	-3	-3	-3	-3
90%	0	0	0	0
95%	+1	+1	+1	+1
Max	+2	+2	+2	+2

HRS.	BV _{CEO} (% Change from Initial)			
	Min	5%	10%	25%
5%	-96	-96	-96	-96
10%	-1	-1	-1	-1
25%	-1	-1	-1	-1
50%	0	0	0	0
75%	0	0	0	0
90%	+1	+1	+1	+1
95%	+2	+2	+2	+2
Max	8	8	8	8

HRS.	VBE(SAT)(% Change from Initial)			
	Min	5%	10%	25%
5%	-3	-3	-3	-3
10%	-1	-1	0	-1
25%	0	0	0	0
50%	0	0	0	0
75%	0	0	0	0
90%	+2	+2	+2	+3
95%	+4	+4	+4	+4
Max	8	8	8	8

HRS.	hFE (% Change from Initial)			
	Min	5%	10%	25%
5%	-19	-19	-19	-19
10%	-10	-10	-10	-10
25%	-9	-9	-9	-9
50%	-6	-6	-6	-6
75%	-3	-3	-3	-3
90%	0	0	0	0
95%	+1	+1	+1	+1
Max	+2	+2	+2	+2

HRS.	hFE (% Change from Initial)			
	Min	5%	10%	25%
5%	-19	-19	-19	-19
10%	-10	-10	-10	-10
25%	-9	-9	-9	-9
50%	-6	-6	-6	-6
75%	-3	-3	-3	-3
90%	0	0	0	0
95%	+1	+1	+1	+1
Max	+2	+2	+2	+2

PROCESS: A PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419204 NO. OF UNITS: 14

FRS.	ICBO (VCB - 60V)(Nanoamps)			
	Init	168	340	680
Min	0.1	0.4	0.1	0.1
5%	0.1	0.4	0.1	0.1
10%	0.1	0.5	0.1	0.1
25%	0.1	0.7	0.3	0.2
50%	0.2	0.8	0.4	0.3
75%	0.4	1.3	0.7	0.5
90%	0.8	3.0	3.2	5.1
95%	0.9	4.2	5.3	6.3
Max	0.9	4.2	5.3	6.3

FRS.	IEBO (VEB - 5V)(Nanoamps)			
	Init	168	340	680
Min	0.1	0.2	0.1	0.1
5%	0.1	0.2	0.1	0.1
10%	0.1	0.2	0.1	0.1
25%	0.1	0.4	0.1	0.1
50%	0.1	0.4	0.1	0.1
75%	0.1	0.5	0.2	0.2
90%	0.2	1.3	0.7	0.6
95%	0.2	2.0	1.1	0.9
Max	0.2	2.0	1.1	0.9

FRS.	BVCEO (IC - 0.1 ma)(Volts)			
	Init	168	340	680
Min	41	41	31	40
5%	41	41	31	40
10%	43	43	35	41
25%	47	46	43	46
50%	50	50	50	50
75%	54	55	55	53
90%	58	58	59	57
95%	59	60	60	59
Max	59	60	60	59

FRS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	-4	-26	-6
5%	-	-4	-26	-6
10%	-	-4	-24	-6
25%	-	-2	-8	-4
50%	-	0	0	-2
75%	-	+1	+2	0
90%	-	+9	+10	+6
95%	-	+15	+13	+10
Max	-	+15	+13	+10

FRS.	VCE(SAT) (IC-50ma, IB-5 ma)(Mv.)			
	Init	168	340	680
Min	173	172	171	175
5%	173	172	171	175
10%	175	178	178	178
25%	190	194	192	190
50%	206	211	208	210
75%	245	247	252	248
90%	376	390	397	399
95%	396	405	408	410
Max	396	405	408	410

FRS.	VCE(SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	-1	-1	0
5%	-	-1	-1	0
10%	-	-1	-1	0
25%	-	+1	+1	+1
50%	-	+2	+2	+2
75%	-	+3	+4	+4
90%	-	+5	+6	+10
95%	-	+5	+8	+10
Max	-	+5	+8	+10

FRS.	VBE(SAT) (IC-50 ma, IB-5 ma)(Mv.)			
	Init	168	340	680
Min	784	782	781	786
5%	784	782	781	786
10%	784	784	783	780
25%	789	791	789	791
50%	791	795	791	795
75%	794	798	795	800
90%	795	806	797	815
95%	796	812	797	815
Max	796	812	797	815

FRS.	VBE(SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	0	-1	-10
5%	-	0	-1	-10
10%	-	0	-1	-5
25%	-	0	0	0
50%	-	+1	0	+1
75%	-	+1	0	+1
90%	-	+2	+1	+3
95%	-	+2	+1	+3
Max	-	+2	+1	+3

FRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	64	58	64	53
5%	64	58	64	53
10%	73	60	65	60
25%	84	81	86	81
50%	89	89	87	88
75%	100	94	97	90
90%	106	97	103	100
95%	107	97	104	104
Max	107	97	104	104

FRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-26	-21	-21
5%	-	-26	-21	-21
10%	-	-20	-17	-19
25%	-	-8	-4	-14
50%	-	-1	0	-8
75%	-	+1	+3	-1
90%	-	+6	+6	+5
95%	-	+6	+7	+9
Max	-	+6	+7	+9

FRS.	BVCE (IC - 0.1 ma)(Volts)			
	Init	168	340	680
Min	41	41	31	40
5%	41	41	31	40
10%	43	43	35	41
25%	47	46	43	46
50%	50	50	50	50
75%	54	55	55	53
90%	58	58	59	57
95%	59	60	60	59
Max	59	60	60	59

FRS.	BVCE (% Change from Initial)			
	Init	168	340	680
Min	-	-4	-26	-6
5%	-	-4	-26	-6
10%	-	-4	-24	-6
25%	-	-2	-8	-4
50%	-	0	0	-2
75%	-	+1	+2	0
90%	-	+9	+10	+6
95%	-	+15	+13	+10
Max	-	+15	+13	+10

PROCESS: A PAB-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge. CELL NO.: A19205 NO. OF UNITS: 28

OPERATING POWER CONDITIONS: 200 mw, 30 V, 150°C. MIN. 1.87. MAX 98.27.

FRS.	ICBO (VCB - 60V) (Nanoamps)				
	Init	168	340	680	1000L50C20003000
Min	<0.1	<0.1	<0.1	<0.1	<0.1
5%	<0.1	<0.1	<0.1	<0.1	<0.1
10%	<0.1	<0.1	<0.1	<0.1	<0.1
25%	<0.1	0.8	0.2	0.3	0.1
50%	0.2	0.9	0.5	0.4	0.3
75%	0.4	1.4	1.0	1.2	0.8
90%	0.9	13.5	2.0	1.8	1.5
95%	1.5	127.7	107.1	11.1	6.4
Max	2.0	142.4	196.6	18.6	7.3

FRS.	IFBO (VFB - 5V) (Nanoamps)				
	Init	168	340	680	1000L50C20003000
Min	<0.1	0.3	<0.1	<0.1	<0.1
5%	<0.1	0.3	<0.1	<0.1	<0.1
10%	<0.1	0.3	<0.1	<0.1	<0.1
25%	<0.1	0.4	<0.1	<0.1	0.2
50%	0.1	0.5	0.1	0.1	0.2
75%	0.1	0.6	0.2	0.2	0.3
90%	0.2	0.7	0.4	0.3	0.4
95%	0.4	0.9	0.5	0.6	0.4
Max	0.5	1.0	0.5	0.6	0.4

FRS.	BVCEO (IC - 0.1 ma) (Volts)				
	Init	168	340	680	1000L50C20003000
Min	41	41	41	41	41
5%	42	42	42	42	42
10%	44	44	44	44	44
25%	47	47	47	47	47
50%	51	51	51	51	51
75%	54	54	54	54	54
90%	58	58	58	58	58
95%	62	62	62	62	62
Max	64	64	64	64	64

FRS.	BVCF0 (% Change from Initial)				
	Init	168	340	680	1000L50C20003000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

FRS.	VCE (SAT) (IC-50ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000L50C20003000
Min	150	152	155	154	157
5%	153	156	157	157	159
10%	171	174	175	174	178
25%	207	209	212	203	210
50%	230	241	245	233	246
75%	284	294	303	296	302
90%	406	433	431	418	430
95%	432	448	449	440	450
Max	437	451	453	442	453

FRS.	VCE (SAT) (% Change from Initial)				
	Init	168	340	680	1000L50C20003000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

FRS.	VBE (SAT) (IC-50 ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000L50C20003000
Min	779	725	784	724	726
5%	781	729	785	729	726
10%	785	784	788	785	785
25%	787	788	789	788	789
50%	793	793	796	794	793
75%	796	801	803	803	800
90%	800	808	810	809	805
95%	803	810	819	814	810
Max	805	810	819	814	812

FRS.	VBE (SAT) (% Change from Initial)				
	Init	168	340	680	1000L50C20003000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

FRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	680	1000L50C20003000
Min	54	54	54	53	53
5%	56	56	56	55	59
10%	60	60	60	58	60
25%	74	75	72	74	71
50%	83	83	82	82	83
75%	90	88	88	87	88
90%	104	99	98	102	104
95%	118	115	114	110	117
Max	122	123	124	125	123

FRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000L50C20003000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

FRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	680	1000L50C20003000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

FRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000L50C20003000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

PROCESS: A PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C. Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITIONS: 800 mw, 30 V, 25°C. MIN. 3.6% MAX. 96.4% CELL NO.: 419206 NO. OF UNITS: 14

FRS.	ICBO (V _{CB} - 60V)(Nanoamps)			
	Init	168	340	680
Min	<0.1	<0.1	<0.1	<0.1
5%	<0.1	0.1	<0.1	<0.1
10%	0.1	0.3	0.2	0.1
25%	0.1	0.5	0.2	0.2
50%	0.3	0.9	0.4	0.4
75%	0.5	1.9	1.7	1.5
90%	1.5	4.9	4.9	3.0
95%	2.0	6.9	6.9	3.7
Max	2.0	6.9	6.9	3.7

FRS.	IEBO (V _{EB} - 5V)(Nanoamps)			
	Init	168	340	680
Min	<0.1	0.2	<0.1	<0.1
5%	<0.1	0.2	<0.1	<0.1
10%	<0.1	0.2	<0.1	<0.1
25%	<0.1	0.3	<0.1	<0.1
50%	0.1	0.5	0.1	0.2
75%	0.2	0.7	0.3	0.4
90%	0.3	0.7	0.4	0.5
95%	0.3	0.7	0.4	0.5
Max	0.3	0.7	0.4	0.5

FRS.	BVCEO (I _C - 0.1 ma)(Volts)			
	Init	168	340	680
Min	42	42	42	42
5%	42	42	42	42
10%	42	42	42	42
25%	45	44	44	44
50%	48	48	50	50
75%	51	52	53	55
90%	55	55	55	55
95%	57	57	57	57
Max	57	57	57	57

FRS.	BVCF0 (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	0	0	0
50%	0	0	0	0
75%	0	0	0	0
90%	0	0	0	0
95%	0	0	0	0
Max	0	0	0	0

FRS.	VCE(SAT)(I _C -50ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	0.38	1.51	1.58	1.53
5%	0.38	1.51	1.53	1.53
10%	0.38	1.58	1.58	1.59
25%	1.62	1.67	1.68	1.68
50%	1.98	2.16	2.17	2.34
75%	2.47	2.48	2.49	2.53
90%	2.66	2.69	2.70	2.70
95%	2.81	2.84	2.87	2.87
Max	2.81	2.84	2.87	2.87

FRS.	VCE(SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	0	-	0
5%	-	0	-	0
10%	-	0	-	0
25%	-	+1	+1	+1
50%	-	+2	+2	+2
75%	-	+3	+3	+3
90%	-	+5	+5	+5
95%	-	+5	+5	+5
Max	-	+5	+5	+5

FRS.	VBE(SAT)(I _C -50 ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	696	784	783	782
5%	696	784	783	782
10%	739	785	783	783
25%	783	787	785	785
50%	788	789	790	787
75%	792	792	790	790
90%	792	794	793	793
95%	792	794	793	793
Max	792	794	793	793

FRS.	VBE(SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	0	0	0
5%	-	0	0	0
10%	-	0	0	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	0	0	0
95%	-	0	0	0
Max	-	0	0	0

FRS.	hFE (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	680
Min	67	68	64	20
5%	67	68	64	20
10%	68	68	64	44
25%	73	74	75	70
50%	88	89	91	87
75%	92	92	94	90
90%	98	97	100	99
95%	98	98	102	99
Max	98	98	102	99

FRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-2	-11	-79
5%	-	-2	-11	-79
10%	-	-2	-10	-42
25%	-	-1	-5	-2
50%	-	+2	+3	+2
75%	-	+4	+6	+4
90%	-	+5	+7	+5
95%	-	+5	+7	+5
Max	-	+5	+7	+5

FRS.	bFE (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	680
Min	67	68	64	20
5%	67	68	64	20
10%	68	68	64	44
25%	73	74	75	70
50%	88	89	91	87
75%	92	92	94	90
90%	98	97	100	99
95%	98	98	102	99
Max	98	98	102	99

FRS.	bFE (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

PROCESS: A. PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C. MIN: 1.7% MAX: 98.3%

CELL NO.: 419207 NO. OF UNITS: 29

HRS.	ICBO (VCB - 60V)(Nanoamps)			
	Init	168	340	680
Min	<0.1	<0.1	<0.1	<0.1
5%	<0.1	<0.1	<0.1	<0.1
10%	<0.1	<0.1	<0.1	<0.1
25%	0.1	0.1	0.1	0.1
50%	0.2	0.4	0.3	0.1
75%	0.9	1.7	1.1	0.3
90%	1.0	2.0	1.3	1.1
95%	1.9	2.9	2.2	1.9
Max	2.7	3.7	3.0	2.7

HRS.	IEBO (VEB - 5V)(Nanoamps)			
	Init	168	340	680
Min	<0.1	<0.1	<0.1	<0.1
5%	<0.1	<0.1	<0.1	<0.1
10%	<0.1	<0.1	<0.1	<0.1
25%	<0.1	<0.1	<0.1	<0.1
50%	0.1	0.6	0.1	0.2
75%	0.3	0.9	0.3	0.3
90%	0.5	1.1	0.5	0.5
95%	0.6	1.2	0.6	0.5
Max	0.6	1.2	0.6	0.5

HRS.	BVCEO (IC - 0.1 ma)(Volts)			
	Init	168	340	680
Min	41	41	41	41
5%	42	42	42	42
10%	44	44	44	44
25%	45	45	45	45
50%	52	52	52	52
75%	55	55	55	55
90%	59	59	59	59
95%	60	60	60	60
Max	61	61	61	61

HRS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	0	-2	-3
5%	-	0	-2	-2
10%	-	0	-1	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	0	+1	+1
95%	-	+4	+4	+4
Max	-	+5	+6	+6

HRS.	VCE(SAT)(IC-50ma, IB-5 ma)(Mv.)			
	Init	168	340	680
Min	169	170	173	173
5%	170	171	174	173
10%	174	175	175	176
25%	190	194	199	199
50%	219	223	224	227
75%	255	257	257	258
90%	316	326	325	327
95%	334	339	343	343
Max	339	346	343	350

HRS.	VCE(SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	-2	-2	0
5%	-	-2	-2	0
10%	-	-1	0	0
25%	-	0	+1	+3
50%	-	+2	+2	+4
75%	-	+3	+3	+5
90%	-	+4	+5	+6
95%	-	+4	+5	+6
Max	-	+4	+5	+6

HRS.	VBE(SAT)(IC-50 ma, IB-5 ma)(Mv.)			
	Init	168	340	680
Min	783	779	780	779
5%	783	781	781	781
10%	785	785	785	786
25%	786	787	787	787
50%	790	791	790	790
75%	794	795	797	797
90%	797	796	800	798
95%	798	796	803	799
Max	798	796	803	799

HRS.	VBE(SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	0	0	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	+1	+1
90%	-	+1	+1	+1
95%	-	+1	+1	+1
Max	-	+1	+1	+1

HRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	62	60	63	63
5%	63	63	64	64
10%	67	66	67	66
25%	77	77	77	77
50%	84	83	84	85
75%	90	90	90	91
90%	98	94	92	99
95%	102	100	97	103
Max	105	105	99	106

HRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-8	-23	-7
5%	-	-8	-19	-4
10%	-	-6	-7	-1
25%	-	-1	0	0
50%	-	+1	+2	+2
75%	-	+1	+2	+2
90%	-	+5	+5	+6
95%	-	+6	+7	+7
Max	-	+6	+7	+7

HRS.	hFE			
	Init	168	340	680
Min	62	60	63	63
5%	63	63	64	64
10%	67	66	67	66
25%	77	77	77	77
50%	84	83	84	85
75%	90	90	90	91
90%	98	94	92	99
95%	102	100	97	103
Max	105	105	99	106

HRS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	0	-2	-3
5%	-	0	-2	-2
10%	-	0	-1	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	0	+1	+1
95%	-	+4	+4	+4
Max	-	+5	+6	+6

PROCESS: A FRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.
 OPERATING POWER CONDITION: 500 mw, 30 V, 25°C. MIN 0.6% MAX 99.47% CELL NO.: 419208 NO. OF UNITS: 78

ERS.	ICBO (VCB - 60V)(Nanocamps)			
	Init	168	340	680
Min	<0.1	<0.1	0.4	0.8
5%	0.1	0.1	0.4	0.9
10%	0.1	0.1	0.5	1.0
25%	0.2	0.1	0.7	1.1
50%	0.3	0.4	0.9	1.3
75%	0.9	0.6	1.5	1.8
90%	1.3	1.2	2.1	2.5
95%	2.4	2.3	3.4	3.4
Max	26.5	7.4	3.5	3.5

ERS.	IEBO (VEB - 5V)(Nanocamps)			
	Init	168	340	680
Min	<0.1	<0.1	0.2	0.2
5%	<0.1	<0.1	0.2	0.2
10%	<0.1	<0.1	0.3	0.3
25%	<0.1	0.3	0.4	0.5
50%	0.2	0.7	0.8	1.0
75%	0.4	0.8	1.0	1.4
90%	0.6	0.8	1.6	2.2
95%	2.2	1.4	3.7	3.0
Max	2.2	1.4	3.7	3.0

ERS.	BVCEO (IC - 0.1 ma)(Volts)			
	Init	168	340	680
Min	40	40	40	40
5%	42	41	42	42
10%	43	42	43	44
25%	45	45	45	46
50%	49	49	49	51
75%	53	53	53	57
90%	56	56	56	63
95%	57	58	58	65
Max	65	65	65	110

ERS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	-1	-1	-1
5%	-	0	0	0
10%	-	0	0	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	+1	+1	+1
95%	-	+1	+1	+1
Max	-	+7	+22	+22

ERS.	VCE (SAT) (IC-50ma, IB-5 ma)(Mv.)			
	Init	168	340	680
Min	0.29	1.45	1.46	1.45
5%	1.52	1.57	1.56	1.57
10%	1.67	1.68	1.69	1.69
25%	1.88	1.92	1.91	1.95
50%	2.18	2.20	2.19	2.24
75%	2.60	2.63	2.60	2.67
90%	2.86	2.87	2.84	3.05
95%	3.04	3.10	3.07	3.23
Max	3.29	3.32	3.30	3.27

ERS.	VCE (SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	-2	-3	-2
5%	-	-1	-1	-1
10%	-	0	0	0
25%	-	+1	+1	+1
50%	-	+2	+1	+2
75%	-	+3	+2	+3
90%	-	+3	+4	+3
95%	-	+3	+4	+3
Max	-	+3	+4	+3

ERS.	VBE (SAT) (IC-50 ma, IB-5 ma)(Mv.)			
	Init	168	340	680
Min	0.01	7.74	7.74	7.74
5%	7.76	7.76	7.79	7.80
10%	7.80	7.79	7.80	7.79
25%	7.83	7.86	7.87	7.86
50%	7.87	7.88	7.90	7.90
75%	7.90	7.88	7.93	7.93
90%	7.92	7.90	7.94	7.98
95%	7.93	7.94	7.99	8.07
Max	8.07	8.02	8.09	8.27

ERS.	VBE (SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	-1	-1	-1
5%	-	-1	0	0
10%	-	-1	0	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	+1	+1	+1
95%	-	+1	+1	+1
Max	-	+1	+1	+1

ERS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	53	54	52	52
5%	64	64	62	62
10%	68	65	64	64
25%	77	75	74	72
50%	87	82	83	80
75%	92	90	91	87
90%	97	96	96	91
95%	99	98	97	97
Max	103	102	102	101

ERS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-19	-39	-38
5%	-	-9	-8	-15
10%	-	-7	-7	-13
25%	-	-5	-3	-9
50%	-	-2	-1	-3
75%	-	0	-1	-2
90%	-	+1	0	-1
95%	-	+1	0	-1
Max	-	+3	+3	+3

ERS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	53	54	52	52
5%	64	64	62	62
10%	68	65	64	64
25%	77	75	74	72
50%	87	82	83	80
75%	92	90	91	87
90%	97	96	96	91
95%	99	98	97	97
Max	103	102	102	101

ERS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-19	-39	-38
5%	-	-9	-8	-15
10%	-	-7	-7	-13
25%	-	-5	-3	-9
50%	-	-2	-1	-3
75%	-	0	-1	-2
90%	-	+1	0	-1
95%	-	+1	0	-1
Max	-	+3	+3	+3

PROCESS: A PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 400 mw, 30 V, 150°C. MIN. 3.67% MAX. 9.6.4

CELL NO.: 419209 NO. OF UNITS: 14

HRS.	ICBO (VCB - 60V)(Nanoamps)			
	Init	168	340	680
Min	0.1	0.6	<.1	<.1
5%	0.1	0.6	<.1	<.1
10%	0.1	0.6	<.1	<.1
25%	0.1	0.7	0.3	0.4
50%	0.3	0.9	0.5	0.4
75%	0.5	1.1	0.7	0.6
90%	1.3	1.7	1.4	1.3
95%	1.3	3.1	2.7	2.3
Max	1.3	3.2	2.7	2.3

HRS.	IEBO (VEB - 5V)(Nanoamps)			
	Init	168	340	680
Min	0.1	0.3	0.1	0.1
5%	0.1	0.3	0.1	0.1
10%	0.1	0.3	0.1	0.1
25%	0.1	0.3	0.1	0.1
50%	0.1	0.5	0.1	0.1
75%	0.1	0.6	0.1	0.2
90%	0.2	0.7	0.2	0.4
95%	0.3	0.7	0.2	0.4
Max	0.3	0.7	0.2	0.4

HRS.	BVCEO (IC - 0.1 ma)(Volts)			
	Init	168	340	680
Min	42	42	42	42
5%	42	42	42	42
10%	43	43	43	43
25%	46	46	46	46
50%	50	50	50	50
75%	53	53	53	53
90%	56	56	57	57
95%	59	59	59	59
Max	59	59	59	59

HRS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	-1	-24	-3
5%	-	-1	-24	-3
10%	-	-1	-24	-3
25%	-	0	-22	-1
50%	-	0	-10	0
75%	-	0	0	0
90%	-	+1	0	+1
95%	-	+1	0	+1
Max	-	+1	0	+1

HRS.	VCE(SAT)(IC-50ma, IB-5 ma)(Mv.)			
	Init	168	340	680
Min	175	174	178	179
5%	175	174	178	179
10%	184	184	187	185
25%	204	207	204	205
50%	216	221	214	218
75%	265	269	266	268
90%	346	349	349	344
95%	350	349	352	350
Max	350	349	352	350

HRS.	VCE(SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	-1	0	-4
5%	-	-1	0	-4
10%	-	-1	0	-2
25%	-	0	0	+1
50%	-	+2	+1	+2
75%	-	+2	+2	+3
90%	-	+3	+3	+5
95%	-	+3	+4	+5
Max	-	+3	+4	+5

HRS.	VBE(SAT)(IC-50 ma, IB-5 ma)(Mv.)			
	Init	168	340	680
Min	781	781	784	781
5%	781	781	784	781
10%	782	783	785	783
25%	784	786	787	787
50%	787	788	788	790
75%	790	794	795	795
90%	794	799	799	800
95%	797	801	802	803
Max	797	801	802	803

HRS.	VBE(SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	0	0	-1
5%	-	0	0	-1
10%	-	0	0	-1
25%	-	0	0	0
50%	-	0	0	0
75%	-	+1	+1	+1
90%	-	+1	+1	+1
95%	-	+1	+1	+1
Max	-	+1	+1	+1

HRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	57	57	59	59
5%	57	57	59	59
10%	62	60	62	60
25%	67	66	66	66
50%	87	86	86	84
75%	91	92	92	90
90%	97	98	99	97
95%	98	98	100	99
Max	98	98	100	99

HRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-4	-2	-29
5%	-	-4	-2	-29
10%	-	-3	-2	-16
25%	-	-1	-1	-12
50%	-	0	+1	-5
75%	-	+1	+4	-3
90%	-	+1	+5	-1
95%	-	+1	+7	-4
Max	-	+1	+7	-4

HRS.	BVCE0 (IC - 0.1 ma)(Volts)			
	Init	168	340	680
Min	42	42	42	42
5%	42	42	42	42
10%	43	43	43	43
25%	46	46	46	46
50%	50	50	50	50
75%	53	53	53	53
90%	56	56	57	57
95%	59	59	59	59
Max	59	59	59	59

HRS.	BVCE0 (% Change from Initial)			
	Init	168	340	680
Min	-	-1	-24	-3
5%	-	-1	-24	-3
10%	-	-1	-24	-3
25%	-	0	-22	-1
50%	-	0	-10	0
75%	-	0	0	0
90%	-	+1	0	+1
95%	-	+1	0	+1
Max	-	+1	0	+1

PROCESS: A PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 200 mw, 30 V, 150°C. CELL NO.: 419210 NO. OF UNITS: 29

HRS.	ICBO (V _{CB} - 60V) (Nanoamps)				IEBO (V _{EB} - 5V) (Nanoamps)				BV _{CEO} (I _C - 0.1 ma) (Volts)				BV _{CEO} (% Change from Initial)												
	Init	168	340	680	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L	1000L					
Min	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1					
5%	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1				
10%	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1			
25%	0.2	0.7	0.2	0.2	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1		
50%	0.3	0.8	0.4	0.4	0.2	0.2	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	
75%	0.6	1.2	0.7	0.6	0.3	0.3	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2
90%	1.3	2.0	1.6	1.6	1.5	1.4	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2	1.2
95%	2.0	4.6	2.1	2.1	2.1	2.1	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8
Max	2.3	6.3	2.4	2.5	2.5	2.5	2.0	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2

HRS.	VCE (SAT) (I _C - 50ma, I _B - 5 ma) (Mv.)				VCE (SAT) (% Change from Initial)				VBE (SAT) (I _C - 50 ma, I _B - 5 ma) (Mv.)				VBE (SAT) (% Change from Initial)			
	Init	168	340	680	1000L	1000L	1000L	1000L	Init	168	340	680	1000L	1000L	1000L	1000L
Min	168	168	170	168	170	170	170	170	168	168	168	168	168	168	168	168
5%	169	168	171	171	169	172	170	170	174	175	172	172	172	172	172	172
10%	171	170	173	172	172	173	173	172	181	180	183	184	184	184	184	184
25%	194	194	196	198	196	198	198	199	186	186	186	186	186	186	186	186
50%	219	211	220	220	221	220	221	221	186	186	186	186	186	186	186	186
75%	247	250	249	250	255	249	250	250	186	186	186	186	186	186	186	186
90%	278	276	278	275	278	278	277	279	186	186	186	186	186	186	186	186
95%	297	301	299	302	304	298	297	299	186	186	186	186	186	186	186	186
Max	311	317	315	317	319	313	313	315	186	186	186	186	186	186	186	186

HRS.	hFE (I _C - 20 ma, VCE - 5V)				hFE (% Change from Initial)			
	Init	168	340	680	1000L	1000L	1000L	1000L
Min	62	62	62	62	62	62	62	62
5%	64	64	63	63	63	63	63	63
10%	66	65	65	65	65	65	65	65
25%	71	71	70	70	70	70	70	70
50%	83	80	79	79	80	81	82	82
75%	89	87	86	86	87	87	88	88
90%	98	96	95	95	97	95	97	97
95%	102	100	99	99	99	101	102	102
Max	102	101	101	101	101	101	102	102

PROCESS: A PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C.

CELL NO.: 419211 NO. OF UNITS: 7

FRS.	ICBO (VCB - 60V) (Nanoamps)			
	Init	168	340	680
Min	0.1	0.5	0.1	0.1
5%	0.1	0.5	0.1	0.1
10%	0.1	0.5	0.1	0.1
25%	0.1	0.5	0.1	0.1
50%	0.4	0.8	0.4	0.2
75%	0.7	1.0	0.8	0.5
90%	1.0	2.2	1.8	1.5
95%	1.9	2.2	1.8	1.5
Max	1.9	2.2	1.8	1.5

FRS.	IEBO (VEB - 5V) (Nanoamps)			
	Init	168	340	680
Min	0.1	0.3	0.1	0.1
5%	0.1	0.3	0.1	0.1
10%	0.1	0.3	0.1	0.1
25%	0.1	0.3	0.1	0.1
50%	0.1	0.3	0.1	0.1
75%	0.1	0.3	0.1	0.1
90%	0.3	0.6	0.1	0.3
95%	0.3	0.6	0.1	0.3
Max	0.3	0.6	0.1	0.3

FRS.	BVCEO (IC - 0.1 ma) (Volts)			
	Init	168	340	680
Min	42	42	42	42
5%	42	42	42	42
10%	42	42	42	42
25%	44	43	43	44
50%	45	44	45	45
75%	55	55	55	55
90%	57	57	57	58
95%	57	57	57	58
Max	57	57	57	58

FRS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

FRS.	VCE(SAT)(IC-50ma, IB=5 ma) (Mv.)			
	Init	168	340	680
Min	193	193	194	192
5%	193	193	194	192
10%	193	193	194	192
25%	198	199	200	199
50%	231	233	231	234
75%	312	312	316	313
90%	344	343	346	346
95%	344	343	346	346
Max	344	343	346	346

FRS.	VCE(SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	0	0	-
5%	-	0	0	-
10%	-	0	0	-
25%	-	0	0	-
50%	-	0	0	-
75%	-	0	0	-
90%	-	0	0	-
95%	-	0	0	-
Max	-	0	0	-

FRS.	VBE(SAT)(IC-50 ma, IB=5 ma) (Mv.)			
	Init	168	340	680
Min	788	786	787	790
5%	788	786	787	790
10%	788	786	787	790
25%	791	790	790	790
50%	791	791	794	789
75%	800	797	801	802
90%	801	802	801	802
95%	801	802	801	802
Max	801	802	801	802

FRS.	VBE(SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

FRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	62	63	57	62
5%	62	63	57	62
10%	62	63	57	62
25%	76	80	71	79
50%	90	91	77	87
75%	93	94	86	92
90%	101	101	101	99
95%	101	101	101	99
Max	101	101	101	99

FRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	0	-14	-5
5%	-	0	-14	-5
10%	-	0	-14	-5
25%	-	0	-8	-2
50%	-	0	-7	-1
75%	-	0	-3	+3
90%	-	0	+8	+6
95%	-	0	+8	+6
Max	-	0	+8	+6

FRS.	hFE			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

FRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

PROCESS: A PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C.

CELL NO.: 419212 NO. OF UNITS: 16

HRS.	ICBO (VCB - 60V) (Nanoamps)				
	Init	168	340	680	1000L50020003000
Min	0.1	0.6	0.2	0.1	0.1
5%	0.1	0.6	0.2	0.1	0.1
10%	0.2	0.7	0.2	0.1	0.1
25%	0.3	0.8	0.2	0.1	0.1
50%	0.5	1.0	0.5	0.4	0.4
75%	1.1	1.4	0.9	0.9	1.1
90%	1.4	1.8	1.3	1.0	1.3
95%	1.4	1.9	1.4	1.0	1.3
Max	1.4	1.9	1.4	1.0	1.3

HRS.	IEBO (VEB - 5V) (Nanoamps)				
	Init	168	340	680	1000L50020003000
Min	0.1	0.3	0.1	0.1	0.1
5%	0.1	0.3	0.1	0.1	0.1
10%	0.1	0.4	0.1	0.1	0.1
25%	0.1	0.4	0.1	0.1	0.1
50%	0.1	0.5	0.1	0.1	0.1
75%	0.3	0.6	0.1	0.2	0.2
90%	0.6	0.8	0.3	0.3	0.4
95%	0.9	1.0	0.4	0.4	0.5
Max	0.9	1.0	0.4	0.4	0.5

HRS.	BVCSO (IC - 0.1 ma) (Volts)				
	Init	168	340	680	1000L50020003000
Min	43	43	43	43	43
5%	43	43	43	43	43
10%	43	43	43	43	43
25%	46	46	46	46	46
50%	48	48	48	48	48
75%	51	51	51	51	51
90%	54	53	53	53	54
95%	56	56	56	56	56
Max	56	56	56	56	56

HRS.	BVCSO (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-1	-2	-2	-1
5%	-	-1	-2	-2	-1
10%	-	-1	-1	-1	0
25%	-	-1	-1	0	0
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	0	0	0	0
Max	-	0	0	0	0

HRS.	VCE (SAT) (IC-50ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000L50020003000
Min	0.21	1.58	1.60	1.59	1.62
5%	0.21	1.58	1.60	1.59	1.62
10%	0.25	1.66	1.68	1.67	1.67
25%	1.73	2.02	2.05	2.09	2.07
50%	2.26	2.34	2.34	2.35	2.37
75%	2.57	2.60	2.60	2.62	2.61
90%	3.24	3.29	3.31	3.27	3.34
95%	3.60	3.65	3.67	3.66	3.69
Max	3.60	3.65	3.67	3.66	3.69

HRS.	VCE (SAT) (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	0	0	0	0
5%	-	0	0	0	0
10%	-	0	0	0	0
25%	-	0	0	0	0
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	0	0	0	0
Max	-	0	0	0	0

HRS.	VBE (SAT) (IC-50 ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000L50020003000
Min	616	728	751	709	761
5%	616	728	751	709	761
10%	678	781	782	781	783
25%	781	785	785	787	786
50%	788	788	787	792	790
75%	793	791	790	796	790
90%	800	801	801	807	805
95%	801	802	802	808	806
Max	801	802	802	807	806

HRS.	VBE (SAT) (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-1	0	0	0
5%	-	-1	0	0	0
10%	-	0	0	0	0
25%	-	0	0	0	0
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	0	0	0	0
Max	-	0	0	0	0

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	680	1000L50020003000
Min	49	51	52	51	52
5%	49	51	52	51	52
10%	57	58	58	58	57
25%	71	75	75	73	74
50%	77	83	83	81	84
75%	87	93	93	91	92
90%	92	94	95	92	94
95%	94	95	95	94	95
Max	94	95	95	94	95

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	0	0	-2	-1
5%	-	0	0	-2	-1
10%	-	0	0	-2	0
25%	-	0	0	-1	0
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	0	0	0	0
Max	-	0	0	0	0

HRS.	hFE				
	Init	168	340	680	1000L50020003000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

PROCESS: A PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419243 NO. OF UNITS: 39

HRS.	ICBO (V _{CB} - 60V)(Nanamps)				BV _{CEO} (I _C - 0.1 ma)(Volts)				BV _{CEO} (% Change from Initial)							
	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000
Min	0.1	<0.1	0.5	0.8	<0.1	<0.1	<0.1	<0.1	42	42	42	42	10	42	00	00
5%	0.1	<0.1	0.5	0.8	<0.1	<0.1	<0.1	<0.1	42	42	42	42	33	42	42	42
10%	0.1	<0.1	0.5	1.0	<0.1	<0.1	<0.1	<0.1	43	43	43	42	42	43	43	43
25%	0.2	<0.1	0.7	1.0	<0.1	<0.1	<0.1	<0.1	45	45	45	45	45	45	45	45
50%	0.4	0.4	0.8	1.2	0.3	0.3	0.3	0.3	49	49	49	49	49	49	49	49
75%	0.9	0.5	1.3	1.6	0.8	0.8	0.8	1.0	54	54	54	54	55	56	55	56
90%	1.3	0.7	2.1	2.0	1.3	1.4	1.5	1.9	57	57	57	57	62	63	119	80
95%	1.6	2.2	2.3	2.6	1.5	1.6	3.4	80	58	58	58	58	88	88	88	88
Max	1.8	4.1	4.0	3.3	3.4	80	80	80	64	63	63	63	107	80	80	80

HRS.	VCE(SAT) (% Change from Initial)				VBE(SAT) (I _C -50 ma, I _B -5 ma)(Mv.)			
	Init	168	340	680	1000	1500	2000	3000
Min	-16	-15	-15	-15	-16	-14	-15	-15
5%	-2	-1	-1	0	0	-2	-3	-3
10%	-1	0	0	0	0	0	0	0
25%	0	0	0	0	0	0	0	0
50%	+1	+2	+1	+3	+3	+2	+2	+2
75%	+2	+3	+2	+4	+5	+7	+6	+6
90%	+3	+4	+3	+9	+8	+14	+15	+15
95%	+9	+7	+9	+13	+14	+17	+17	+17
Max	+22	+20	+20	+20	+20	+20	+20	+20

HRS.	VCE(SAT) (I _C -50ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	010	160	160	160
5%	034	168	169	167
10%	166	184	184	180
25%	190	195	198	198
50%	228	234	233	233
75%	251	254	257	256
90%	288	314	313	310
95%	313	324	325	320
Max	320	365	366	363

HRS.	VBE(SAT) (% Change from Initial)				hFE (% Change from Initial)			
	Init	168	340	680	1000	1500	2000	3000
Min	-2	-2	-2	-2	-2	-2	-2	-2
5%	-1	-1	-1	-1	-1	-1	-1	-1
10%	-1	-1	-1	-1	-1	-1	-1	-1
25%	0	0	0	0	0	0	0	0
50%	+1	+1	+1	+1	+1	+1	+1	+1
75%	+2	+2	+2	+2	+2	+2	+2	+2
90%	+3	+3	+3	+3	+3	+3	+3	+3
95%	+12	+12	+12	+12	+12	+12	+12	+12
Max	+12	+12	+12	+12	+12	+12	+12	+12

HRS.	BV _{CEO} (I _C - 0.1 ma)(Volts)				VBE(SAT) (% Change from Initial)			
	Init	168	340	680	1000	1500	2000	3000
Min	42	42	42	42	10	42	00	00
5%	42	42	42	42	33	42	42	42
10%	43	43	43	42	42	43	43	43
25%	45	45	45	45	45	45	45	45
50%	49	49	49	49	49	49	49	49
75%	54	54	54	54	55	56	55	56
90%	57	57	57	57	62	63	119	80
95%	58	58	58	58	88	88	88	88
Max	64	63	63	63	107	80	80	80

HRS.	VBE(SAT) (I _C -50 ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	708	773	726	004
5%	776	778	779	778
10%	781	780	781	785
25%	785	784	785	787
50%	789	788	789	791
75%	792	791	791	796
90%	798	795	800	809
95%	808	813	813	816
Max	810	814	805	807

HRS.	VCE(SAT) (% Change from Initial)				hFE (% Change from Initial)			
	Init	168	340	680	1000	1500	2000	3000
Min	-16	-15	-15	-15	-16	-14	-15	-15
5%	-2	-1	-1	0	0	-2	-3	-3
10%	-1	0	0	0	0	0	0	0
25%	0	0	0	0	0	0	0	0
50%	+1	+2	+1	+3	+3	+2	+2	+2
75%	+2	+3	+2	+4	+5	+7	+6	+6
90%	+3	+4	+3	+9	+8	+14	+15	+15
95%	+9	+7	+9	+13	+14	+17	+17	+17
Max	+22	+20	+20	+20	+20	+20	+20	+20

HRS.	VBE(SAT) (I _C -50ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	010	160	160	160
5%	034	168	169	167
10%	166	184	184	180
25%	190	195	198	198
50%	228	234	233	233
75%	251	254	257	256
90%	288	314	313	310
95%	313	324	325	320
Max	320	365	366	363

HRS.	BV _{CEO} (I _C - 0.1 ma)(Volts)				VBE(SAT) (% Change from Initial)			
	Init	168	340	680	1000	1500	2000	3000
Min	42	42	42	42	10	42	00	00
5%	42	42	42	42	33	42	42	42
10%	43	43	43	42	42	43	43	43
25%	45	45	45	45	45	45	45	45
50%	49	49	49	49	49	49	49	49
75%	54	54	54	54	55	56	55	56
90%	57	57	57	57	62	63	119	80
95%	58	58	58	58	88	88	88	88
Max	64	63	63	63	107	80	80	80

HRS.	VBE(SAT) (I _C -50 ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	708	773	726	004
5%	776	778	779	778
10%	781	780	781	785
25%	785	784	785	787
50%	789	788	789	791
75%	792	791	791	796
90%	798	795	800	809
95%	808	813	813	816
Max	810	814	805	807

HRS.	VCE(SAT) (% Change from Initial)				hFE (% Change from Initial)			
	Init	168	340	680	1000	1500	2000	3000
Min	-16	-15	-15	-15	-16	-14	-15	-15
5%	-2	-1	-1	0	0	-2	-3	-3
10%	-1	0	0	0	0	0	0	0
25%	0	0	0	0	0	0	0	0
50%	+1	+2	+1	+3	+3	+2	+2	+2
75%	+2	+3	+2	+4	+5	+7	+6	+6
90%	+3	+4	+3	+9	+8	+14	+15	+15
95%	+9	+7	+9	+13	+14	+17	+17	+17
Max	+22	+20	+20	+20	+20	+20	+20	+20

HRS.	VBE(SAT) (I _C -50ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	010	160	160	160
5%	034	168	169	167
10%	166	184	184	180
25%	190	195	198	198
50%	228	234	233	233
75%	251	254	257	256
90%	288	314	313	310
95%	313	324	325	320
Max	320	365	366	363

PROCESS: A PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITIONS: 400 mw, 30 V, 150°C.

CELL NO.: 419214 NO. OF UNITS: 7

HRS.	ICBO (V _{CB} - 60V) (Nanoamps)			
	Init	168	340	680
Min	0.2	0.2	0.2	0.1
5%	0.2	0.2	0.2	0.1
10%	0.2	0.2	0.2	0.1
25%	0.3	0.3	0.3	0.2
50%	0.3	0.4	0.3	0.3
75%	0.4	0.7	0.6	0.5
90%	0.7	1.2	0.7	0.8
95%	0.7	1.2	0.7	0.8
Max	0.7	1.2	0.7	0.8

HRS.	IEBO (V _{EB} - 5V) (Nanoamps)			
	Init	168	340	680
Min	0.1	0.2	0.1	0.1
5%	0.1	0.2	0.1	0.1
10%	0.1	0.2	0.1	0.1
25%	0.1	0.4	0.1	0.1
50%	0.1	0.6	0.2	0.2
75%	0.2	0.6	0.3	0.3
90%	0.4	0.8	0.4	0.5
95%	0.4	0.8	0.4	0.5
Max	0.4	0.8	0.4	0.5

HRS.	BV _{CEO} (I _C - 0.1 ma) (Volts)			
	Init	168	340	680
Min	43	43	42	43
5%	43	43	42	43
10%	43	43	42	43
25%	48	48	48	48
50%	51	51	51	51
75%	52	52	52	52
90%	57	57	57	57
95%	57	57	57	57
Max	57	57	57	57

HRS.	BV _{CFO} (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

HRS.	V _{CE} (SAT) (I _C - 50ma, I _B - 5 ma) (Mv.)			
	Init	168	340	680
Min	164	166	162	166
5%	164	166	162	166
10%	164	166	162	166
25%	177	179	180	182
50%	229	231	232	234
75%	271	277	278	276
90%	324	327	328	327
95%	324	327	328	327
Max	324	327	328	327

HRS.	V _{CE} (SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	0	-	0
5%	-	0	-	0
10%	-	0	-	0
25%	-	+1	0	+1
50%	-	+1	+1	+2
75%	-	+2	+1	+2
90%	-	+2	+3	+3
95%	-	+2	+3	+3
Max	-	+2	+3	+3

HRS.	V _{BE} (SAT) (I _C - 50 ma, I _B - 5 ma) (Mv.)			
	Init	168	340	680
Min	783	782	787	787
5%	783	782	787	787
10%	783	782	787	787
25%	788	786	788	787
50%	792	787	793	792
75%	799	787	800	802
90%	812	813	810	813
95%	812	814	810	813
Max	812	813	810	813

HRS.	V _{BE} (SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	-	0	0
5%	-	-	0	0
10%	-	-	0	0
25%	-	-	0	0
50%	-	-	0	0
75%	-	-	0	0
90%	-	-	0	0
95%	-	-	0	0
Max	-	-	0	0

HRS.	h _{FE} (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	680
Min	69	69	65	67
5%	69	69	65	67
10%	69	69	65	67
25%	72	73	67	63
50%	74	78	78	69
75%	84	88	80	76
90%	85	91	81	77
95%	85	91	81	77
Max	85	91	81	77

HRS.	h _{FE} (% Change from Initial)			
	Init	168	340	680
Min	-	-1	-12	-15
5%	-	-1	-12	-15
10%	-	-1	-12	-15
25%	-	-1	-10	-14
50%	-	+4	-5	-10
75%	-	+6	-3	-8
90%	-	+9	-3	-3
95%	-	+9	-3	-3
Max	-	+9	-3	-3

HRS.	BV _{CEO} (I _C - 0.1 ma) (Volts)			
	Init	168	340	680
Min	43	43	42	43
5%	43	43	42	43
10%	43	43	42	43
25%	48	48	48	48
50%	51	51	51	51
75%	52	52	52	52
90%	57	57	57	57
95%	57	57	57	57
Max	57	57	57	57

HRS.	BV _{CFO} (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

PROCESS: A PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 200 mw, 30 V, 150°C.

CELL NO.: 419215 NO. OF UNITS: 16

FRS.	ICBO (VCB - 60V)(Nanamps)					IEBO (VEB - 5V)(Nanamps)					BV _{CEO} (I _c - 0.1 ma)(Volts)					BV _{CEO} (% Change from Initial)								
	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000
Min	0.1	0.6	0.3	0.1	0.1	0.1	0.1	0.1	0.1	0.4	0.1	0.1	0.1	0.1	0.1	0.1	38	38	38	37	38	37	38	37
5%	0.1	0.6	0.3	0.1	0.1	0.1	0.1	0.1	0.1	0.4	0.1	0.1	0.1	0.1	0.1	0.1	30	38	38	37	38	37	38	37
10%	0.1	0.8	0.3	0.1	0.1	0.1	0.1	0.1	0.1	0.5	0.1	0.1	0.1	0.1	0.1	0.1	40	40	40	40	40	40	40	40
25%	0.3	0.9	0.6	0.3	0.2	0.2	0.2	0.2	0.2	0.6	0.1	0.1	0.1	0.1	0.1	0.1	42	42	42	42	42	42	42	42
50%	0.4	1.1	0.8	0.5	0.4	0.4	0.4	0.4	0.4	0.6	0.3	0.2	0.2	0.2	0.2	0.2	47	46	46	47	47	46	47	47
75%	1.2	1.7	1.3	1.2	1.1	0.8	1.0	1.1	0.2	0.8	0.4	0.2	0.2	0.3	0.2	0.3	51	49	49	49	51	52	51	52
90%	1.4	1.9	1.4	1.3	1.2	1.0	1.2	1.3	0.3	0.8	0.4	0.3	0.4	0.5	0.5	0.5	55	55	55	55	55	55	55	55
95%	1.5	2.0	1.4	1.3	1.2	1.0	1.3	1.4	0.4	0.8	0.4	0.5	0.6	0.7	0.6	0.6	59	59	59	59	59	59	59	59
Max	1.5	2.0	1.4	1.3	1.2	1.0	1.3	1.4	0.4	0.4	0.4	0.5	0.6	0.7	0.6	0.6	59	59	59	59	59	59	59	59

FRS.	VCE (SAT) (IC-50ma, IB-5 ma)(Mv.)					VCE (SAT) (% Change from Initial)					VBE (SAT) (IC-50 ma, IB-5 ma)(Mv.)					VBE (SAT) (% Change from Initial)								
	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000
Min	167	173	171	175	172	173	170	172	-2	0	0	-1	-1	0	0	0	784	623	787	787	787	787	787	787
5%	167	173	171	175	172	173	170	172	-2	0	0	-1	-2	0	0	0	784	623	787	787	787	787	787	787
10%	175	177	178	182	178	177	178	180	-1	0	0	0	-1	0	0	0	786	721	787	787	787	787	787	787
25%	188	187	184	194	188	187	185	191	0	0	0	-1	-1	0	0	0	788	786	786	786	786	786	786	786
50%	237	238	238	243	237	240	240	243	+1	+1	+3	0	+1	+3	+2	+2	790	780	782	790	792	788	786	789
75%	267	251	252	266	258	259	254	260	+2	+2	+4	+1	+3	+3	+3	+3	793	793	794	794	795	798	790	792
90%	272	275	271	275	272	275	275	277	+3	+3	+2	1077	1025	1077	1077	1077	833	845	842	843	843	848	837	832
95%	273	280	277	280	280	280	282	282	+4	+4	+3	3576	3576	3576	3576	3576	906	906	904	906	906	906	906	906
Max	273	280	277	280	280	282	282	282	+4	+4	+3	3576	3576	3576	3576	3576	906	906	904	906	906	906	906	906

FRS.	hFE (IC - 20 ma, VCE - 5V)					hFE (% Change from Initial)										
	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000
Min	66	69	64	20	20	20	47	20	-2	-6	-7	-9	-9	-35	-7	-7
5%	66	69	64	20	20	20	47	20	-2	-6	-7	-9	-9	-35	-7	-7
10%	67	69	64	53	52	20	59	39	-1	-6	-8	-7	-7	-13	-4	-4
25%	73	74	70	71	69	67	71	70	+1	-5	-1	-4	-6	+1	-1	-1
50%	79	81	80	80	78	76	82	80	+2	-3	0	-3	-2	+1	0	0
75%	91	94	85	90	87	86	93	89	+5	0	+4	+1	+1	+5	+3	+3
90%	96	97	91	97	93	96	97	96	+8	+6	+5	+4	+5	+6	+5	+5
95%	97	98	91	97	94	96	97	97	+8	+7	+6	+4	+6	+7	+6	+6
Max	97	98	91	97	94	96	97	97	+8	+7	+6	+4	+6	+7	+6	+6

PROCESS: A PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C.

CELL NO.: 419216 NO. OF UNITS: 7

HRS.	ICBO (VCB - 60V) (Nanoamps)			
	Init	168	340	680
Min	0.3	0.6	0.2	0.1
5%	0.3	0.6	0.2	0.1
10%	0.3	0.6	0.2	0.1
25%	0.3	0.7	0.2	0.1
50%	0.4	1.1	0.6	0.3
75%	0.7	1.3	0.6	0.3
90%	1.1	1.5	1.1	0.7
95%	1.1	1.5	1.1	0.7
Max	1.1	1.5	1.1	0.7

HRS.	IEBO (VEB - 5V) (Nanoamps)			
	Init	168	340	680
Min	0.1	0.3	0.1	0.1
5%	0.1	0.3	0.1	0.1
10%	0.1	0.3	0.1	0.1
25%	0.1	0.4	0.1	0.1
50%	0.1	0.5	0.1	0.1
75%	0.2	0.6	0.1	0.1
90%	0.4	1.1	0.5	0.3
95%	0.4	1.1	0.5	0.3
Max	0.4	1.1	0.5	0.3

HRS.	BVCEO (IC - 0.1 ma) (Volts)			
	Init	168	340	680
Min	45	45	44	45
5%	45	45	44	45
10%	45	45	44	45
25%	46	46	46	47
50%	52	52	52	52
75%	55	55	55	55
90%	56	56	57	56
95%	56	56	57	56
Max	56	56	57	56

HRS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

HRS.	VCE (SAT) (IC-50ma, IB-5 ma) (Mv.)			
	Init	168	340	680
Min	0.31	1.83	1.86	1.84
5%	0.31	1.83	1.86	1.84
10%	0.31	1.83	1.86	1.84
25%	1.82	2.00	2.00	2.00
50%	2.09	2.24	2.24	2.24
75%	3.13	3.13	3.13	3.16
90%	3.20	3.19	3.27	3.27
95%	3.20	3.19	3.27	3.27
Max	3.20	3.19	3.27	3.27

HRS.	VCE (SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	0	0	0
5%	-	0	0	0
10%	-	0	0	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	0	0	0
95%	-	0	0	0
Max	-	0	0	0

HRS.	VBE (SAT) (IC-50 ma, IB-5 ma) (Mv.)			
	Init	168	340	680
Min	704	783	787	786
5%	704	783	787	786
10%	704	783	787	786
25%	781	783	788	788
50%	787	789	784	789
75%	788	797	785	797
90%	790	799	780	795
95%	790	799	780	795
Max	790	799	780	795

HRS.	VBE (SAT) (% Change from Initial)			
	Init	168	340	680
Min	-	0	0	0
5%	-	0	0	0
10%	-	0	0	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	0	0	0
95%	-	0	0	0
Max	-	0	0	0

HRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	74	74	68	73
5%	74	74	68	73
10%	74	74	68	73
25%	74	74	68	73
50%	78	79	80	81
75%	84	77	78	87
90%	85	87	79	87
95%	85	87	79	87
Max	85	87	79	87

HRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

HRS.	BVCEO (IC - 0.1 ma) (Volts)			
	Init	168	340	680
Min	45	45	44	45
5%	45	45	44	45
10%	45	45	44	45
25%	46	46	46	47
50%	52	52	52	52
75%	55	55	55	55
90%	56	56	57	56
95%	56	56	57	56
Max	56	56	57	56

HRS.	BVCEO (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

PROCESS: A PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C.

CELL NO.: 419217 NO. OF UNITS: 14

FRS.	ICBO (V _{CB} - 60V) (Nanoamps)				
	Init	168	340	680	1000
Min	0.3	0.6	0.1	0.1	0.1
5%	0.3	0.6	0.1	0.1	0.1
10%	0.3	0.7	0.1	0.1	0.1
25%	0.3	1.8	0.3	0.4	0.3
50%	0.4	0.9	0.4	0.5	0.4
75%	0.6	1.0	0.7	0.8	0.6
90%	1.7	3.6	2.7	4.4	4.3
95%	2.1	3.4	3.5	5.7	5.9
Max	2.1	3.4	3.5	5.7	5.9

FRS.	IEBO (V _{EB} - 5V) (Nanoamps)				
	Init	168	340	680	1000
Min	<0.1	0.3	0.1	0.1	0.1
5%	<0.1	0.3	0.1	0.1	0.1
10%	<0.1	0.4	0.1	0.1	0.1
25%	<0.1	0.7	0.1	0.2	0.1
50%	0.1	0.8	0.1	0.3	0.2
75%	0.2	0.9	0.1	0.3	0.2
90%	0.4	0.9	0.4	0.3	0.4
95%	0.4	0.9	0.4	0.3	0.5
Max	0.4	0.9	0.4	0.3	0.5

FRS.	BV _{CEO} (I _C - 0.1 ma.) (Volts)				
	Init	168	340	680	1000
Min	44	44	44	44	44
5%	44	44	44	44	44
10%	44	44	44	44	44
25%	45	45	45	45	45
50%	49	49	49	49	49
75%	54	53	54	54	53
90%	61	66	60	61	61
95%	62	70	68	68	68
Max	62	70	68	68	68

FRS.	BV _{CEO} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-2	-2	-2	-2
5%	-	-2	-2	-2	-2
10%	-	-2	-2	-2	-2
25%	-	-1	-1	0	0
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	+9	0	+1	+2
95%	-	+17	0	+2	+3
Max	-	+17	0	+2	+3

FRS.	V _{CE} (SAT) (I _C -50ma, I _B -5 ma.) (Mv.)				
	Init	168	340	680	1000
Min	049	174	171	174	173
5%	049	174	171	174	173
10%	109	176	174	175	176
25%	184	195	196	197	194
50%	197	211	212	215	214
75%	232	241	242	244	243
90%	252	260	261	265	264
95%	266	272	273	278	277
Max	266	272	273	278	277

FRS.	V _{CE} (SAT) (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-1	-1	+1	+1
5%	-	-1	-1	+1	+1
10%	-	-1	-1	+1	+1
25%	-	+2	0	+3	+2
50%	-	+3	+3	+4	+2
75%	-	+3	+4	+4	+3
90%	-	+20	+20	+20	+20
95%	-	+40	+40	+40	+40
Max	-	+40	+40	+40	+40

FRS.	V _{BE} (SAT) (I _C -50 ma, I _B -5 ma.) (Mv.)				
	Init	168	340	680	1000
Min	695	777	773	775	777
5%	695	777	773	775	777
10%	736	779	777	778	777
25%	784	784	781	780	780
50%	788	787	783	785	783
75%	790	788	787	789	786
90%	793	791	790	792	790
95%	795	791	791	793	790
Max	795	791	791	793	790

FRS.	V _{BE} (SAT) (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-1	-1	-1	-1
5%	-	-1	-1	-1	-1
10%	-	-1	-1	-1	-1
25%	-	0	-1	-1	-1
50%	-	0	0	0	0
75%	-	+7	+7	+7	+7
90%	-	+13	+13	+13	+13
95%	-	+13	+13	+13	+13
Max	-	+13	+13	+13	+13

FRS.	h _{FE} (I _C - 20 ma, V _{CE} - 5V)				
	Init	168	340	680	1000
Min	65	66	67	66	66
5%	65	66	67	66	66
10%	66	66	67	67	66
25%	67	69	69	69	68
50%	81	80	86	85	87
75%	88	89	90	89	89
90%	89	92	92	91	93
95%	90	92	93	92	93
Max	90	92	93	92	93

FRS.	h _{FE} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-8	+1	0	-2
5%	-	-8	+1	0	-2
10%	-	-5	+1	0	-2
25%	-	+1	+1	+1	+1
50%	-	+2	+2	+2	+1
75%	-	+3	+5	+4	+6
90%	-	+5	+8	+7	+9
95%	-	+8	+10	+9	+10
Max	-	+5	+10	+9	+10

FRS.	BV _{BE} (I _C - 20 ma, V _{CE} - 5V)				
	Init	168	340	680	1000
Min	65	66	67	66	66
5%	65	66	67	66	66
10%	66	66	67	67	66
25%	67	69	69	69	68
50%	81	80	86	85	87
75%	88	89	90	89	89
90%	89	92	92	91	93
95%	90	92	93	92	93
Max	90	92	93	92	93

FRS.	BV _{BE} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-1	-1	-1	-1
5%	-	-1	-1	-1	-1
10%	-	-1	-1	-1	-1
25%	-	0	-1	-1	-1
50%	-	0	0	0	0
75%	-	+7	+7	+7	+7
90%	-	+13	+13	+13	+13
95%	-	+13	+13	+13	+13
Max	-	+13	+13	+13	+13

PROCESS: A PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419219 NO. OF UNITS: 7

HRS.	ICBO (VCB - 60V) (Nanamps)				
	Init	168	340	680	1000L50020003000
Min	0.2	0.7	0.1	0.3	0.2
5%	0.2	0.7	0.1	0.3	0.2
10%	0.2	0.7	0.1	0.3	0.2
25%	0.2	0.9	0.2	0.3	0.2
50%	0.4	1.2	0.4	0.4	0.3
75%	0.6	1.4	0.6	0.5	0.3
90%	0.8	2.0	0.8	1.0	1.3
95%	0.8	3.0	0.8	1.0	1.3
Max	0.8	3.0	0.8	1.0	1.3

HRS.	IEBO (VEB - 5V) (Nanamps)				
	Init	168	340	680	1000L50020003000
Min	0.1	0.4	0.1	0.1	0.1
5%	0.1	0.4	0.1	0.1	0.1
10%	0.1	0.4	0.1	0.1	0.1
25%	0.1	0.5	0.1	0.1	0.1
50%	0.2	0.6	0.1	0.1	0.1
75%	0.2	0.7	0.2	0.4	0.2
90%	1.6	2.2	1.2	1.9	3.1
95%	1.6	2.2	1.2	1.9	3.1
Max	1.6	2.2	1.2	1.9	3.1

HRS.	BVCEO (IC - 0.1 ma) (Volts)				
	Init	168	340	680	1000L50020003000
Min	47	47	47	47	47
5%	47	47	47	47	47
10%	47	47	47	47	47
25%	48	48	48	48	48
50%	50	50	50	50	50
75%	55	55	56	56	57
90%	58	57	58	57	57
95%	58	57	58	57	57
Max	58	57	58	57	57

HRS.	BVCEO (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-1	-22	-1	-1
5%	-	-1	-22	-1	-1
10%	-	-1	-22	-1	-1
25%	-	-1	-21	0	0
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	0	0	0	0
Max	-	0	0	0	0

HRS.	VCE(SAT)(IC-50ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000L50020003000
Min	133	132	134	130	132
5%	133	132	134	130	132
10%	133	132	134	130	132
25%	153	156	155	157	154
50%	196	199	196	198	197
75%	216	219	218	215	217
90%	289	293	289	290	288
95%	289	293	289	290	288
Max	289	293	289	290	288

HRS.	VCE(SAT)(% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-1	0	-2	-1
5%	-	-1	0	-2	-1
10%	-	-1	0	-2	-1
25%	-	0	0	0	0
50%	-	4	1	1	0
75%	-	2	1	1	0
90%	-	2	1	3	1
95%	-	2	1	3	1
Max	-	2	1	3	1

HRS.	VBE(SAT)(IC-50 ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000L50020003000
Min	778	779	782	780	780
5%	778	779	782	780	780
10%	778	779	782	780	780
25%	780	781	783	784	782
50%	786	787	790	788	787
75%	791	790	793	792	792
90%	793	796	794	796	795
95%	793	796	794	796	795
Max	793	796	794	796	795

HRS.	VBE(SAT)(% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	-1	0	0	0
5%	-	-1	0	0	0
10%	-	-1	0	0	0
25%	-	0	0	0	0
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	0	0	0	0
Max	-	0	0	0	0

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	680	1000L50020003000
Min	56	57	56	54	55
5%	56	57	56	54	55
10%	56	57	56	54	55
25%	63	63	63	60	61
50%	77	82	84	78	79
75%	81	85	85	80	82
90%	91	92	91	87	89
95%	91	92	91	87	89
Max	91	92	91	87	89

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min	-	0	0	-5	-3
5%	-	0	0	-5	-3
10%	-	0	0	-5	-3
25%	-	0	0	-4	-3
50%	-	2	0	-4	-3
75%	-	6	8	3	3
90%	-	9	10	3	6
95%	-	9	10	3	6
Max	-	9	10	3	6

HRS.	hFE				
	Init	168	340	680	1000L50020003000
Min					
5%					
10%					
25%					
50%					
75%					
90%					
95%					
Max					

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000L50020003000
Min					
5%					
10%					
25%					
50%					
75%					
90%					
95%					
Max					

PROCESS: A FRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 200 mw, 30 V, 150°C.

HRS.	ICBO (V _{CB} - 60V)(Nanoamps)			
	Init	168	340	680
Min	0.1	0.6	0.1	0.2
5%	0.1	0.6	0.1	0.2
10%	0.1	0.6	0.1	0.2
25%	0.2	0.8	0.4	0.3
50%	0.5	1.0	0.5	0.6
75%	0.9	1.5	0.8	0.9
90%	1.5	1.9	1.4	1.7
95%	1.7	2.1	1.7	2.0
Max	1.7	2.1	1.7	2.0

HRS.	IEBO (V _{EB} - 5V)(Nanoamps)			
	Init	168	340	680
Min	0.1	0.3	0.1	0.1
5%	0.1	0.3	0.1	0.1
10%	0.1	0.3	0.1	0.1
25%	0.1	0.5	0.1	0.1
50%	0.1	0.7	0.2	0.1
75%	0.2	0.8	0.3	0.2
90%	0.3	1.2	0.9	0.6
95%	0.3	1.4	1.2	0.6
Max	0.3	1.4	1.2	0.6

HRS.	BV _{CEO} (I _C - 0.1 ma)(Volts)			
	Init	168	340	680
Min	4.6	4.6	4.7	4.6
5%	4.6	4.6	4.7	4.6
10%	4.7	4.6	4.7	4.7
25%	4.8	4.8	4.8	4.8
50%	5.0	5.0	5.0	5.0
75%	5.6	5.5	5.6	5.6
90%	6.0	6.0	6.0	6.0
95%	6.2	6.2	6.2	6.2
Max	6.2	6.2	6.2	6.2

HRS.	BV _{CEO} (% Change from Initial)			
	Init	168	340	680
Min	-	0	0	-1
5%	-	0	0	-1
10%	-	0	0	-1
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	0	0	0
95%	-	0	0	0
Max	-	0	0	0

HRS.	VCE (SAT)(I _C -50ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	167	163	162	159
5%	167	163	162	159
10%	169	168	168	166
25%	180	183	183	184
50%	206	208	209	212
75%	290	294	293	293
90%	412	417	417	418
95%	414	419	420	421
Max	414	419	420	421

HRS.	VCE (SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	-2	-3	-5
5%	-	-2	-3	-5
10%	-	-2	-2	-3
25%	-	0	0	0
50%	-	+1	+1	+2
75%	-	+1	+2	+3
90%	-	+3	+2	+4
95%	-	+3	+2	+4
Max	-	+3	+2	+4

HRS.	VBE (SAT)(I _C -50 ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	698	698	698	698
5%	698	698	698	698
10%	741	741	741	741
25%	785	785	785	785
50%	786	786	786	786
75%	795	795	795	795
90%	801	801	801	801
95%	802	802	802	802
Max	802	802	802	802

HRS.	VBE (SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	-19	0	0
5%	-	-19	0	0
10%	-	-10	0	0
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	0	0	0
95%	-	0	0	0
Max	-	0	0	0

HRS.	hFE (I _C - 20 ma, VCE - 5V)			
	Init	168	340	680
Min	57	59	56	59
5%	57	59	56	59
10%	63	64	61	64
25%	74	76	72	76
50%	78	83	77	83
75%	83	88	87	87
90%	99	92	89	91
95%	99	94	89	94
Max	99	94	89	94

HRS.	hFE (% Change from Initial)			
	Init	168	340	680
Min	-	-9	-10	-10
5%	-	-9	-10	-10
10%	-	-4	-8	-5
25%	-	+1	-5	+1
50%	-	+3	-2	+4
75%	-	+7	+1	+7
90%	-	+13	+5	+11
95%	-	+15	+11	+12
Max	-	+15	+11	+12

HRS.	BV _{CE0} (% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

HRS.	VBE (SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

PROCESS: B PRE-SCREEN STRESS: 153 HRS. OF 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 800 mA, 30 V, 25°C.

CELL NO.: 419221 NO. OF UNITS: 13

HRS.	ICEO (VCB - 60V) (Nanoamps)				
	168	340	580	1000	1500
Min	0.6	0.3	0.1	1.0	0.2
5%	0.6	0.3	0.1	1.0	0.2
10%	0.6	0.3	0.1	1.0	0.2
25%	0.4	0.6	0.3	1.3	0.4
50%	0.8	1.8	1.0	3.0	0.5
75%	1.7	14.2	7.8	7.7	2.2
90%	3.3	98.2	47.5	38.1	54.4
95%	3.4	132.0	62.8	58.3	54.4
Max	3.4	132.0	62.8	58.3	54.4

HRS.	IEBO (VEB - 5V) (Nanoamps)				
	168	340	580	1000	1500
Min	0.4	0.4	0.1	0.1	0.3
5%	0.4	0.4	0.1	0.1	0.3
10%	0.5	0.4	0.1	0.1	0.3
25%	0.1	0.6	0.2	0.3	0.4
50%	0.3	1.0	0.7	0.4	0.5
75%	8.2	10.0	13.7	9.9	20.1
90%	29.0	39.8	38.9	38.0	55.0
95%	36.7	55.8	45.1	45.7	55.0
Max	36.7	55.8	45.1	45.7	55.0

HRS.	BVCEO (IC - 0.1 ma) (Volts)				
	168	340	580	1000	1500
Min	61	60	60	63	62
5%	61	60	60	63	62
10%	62	61	61	63	63
25%	65	63	65	64	64
50%	67	66	66	67	70
75%	75	73	70	78	74
90%	80	78	79	81	81
95%	80	78	80	81	81
Max	80	78	80	81	81

HRS.	BVCEO (% Change from Initial)				
	168	340	580	1000	1500
Min	-5	-5	-3	-3	-3
5%	-5	-5	-3	-3	-3
10%	-5	-4	-3	-3	-3
25%	-4	-3	-2	-2	-3
50%	-2	-2	-1	-1	-1
75%	-1	-1	0	0	0
90%	0	0	13.15	+1	152.2
95%	0	0	14.05	+1	155.0
Max	0	0	14.05	+1	155.0

HRS.	VCE(SAT) (IC-50ma, IB-5 ma) (V.)				
	168	340	580	1000	1500
Min	100	091	092	095	100
5%	100	091	092	095	100
10%	101	094	093	097	100
25%	102	099	099	102	109
50%	104	101	101	103	110
75%	108	111	114	131	113
90%	121	147	149	149	144
95%	122	148	163	144	144
Max	122	148	163	144	144

HRS.	VCE(SAT) (% Change from Initial)				
	168	340	580	1000	1500
Min	-16	-15	-12	-5	-11
5%	-16	-15	-12	-5	-11
10%	-12	-13	-9	-5	-9
25%	-5	-7	-3	-4	-3
50%	-3	-3	0	-1	+2
75%	-2	0	+21	+2	+2
90%	56.4	+42	498	+5	946
95%	92.3	+60	488	+5	943
Max	92.3	+60	488	+5	943

HRS.	VBE(SAT) (IC-50 ma, IB-5 ma) (Mv.)				
	168	340	580	1000	1500
Min	786	785	780	783	777
5%	786	785	780	783	777
10%	786	786	781	782	778
25%	795	793	789	784	781
50%	802	799	799	797	796
75%	804	803	803	824	799
90%	812	822	850	809	809
95%	813	800	866	819	800
Max	813	800	866	819	800

HRS.	VBE(SAT) (% Change from Initial)				
	168	340	580	1000	1500
Min	-1	-2	-2	-2	-2
5%	-1	-2	-2	-2	-2
10%	-1	-2	-2	-2	-2
25%	-1	0	-1	-1	-1
50%	0	0	0	0	0
75%	0	0	0	0	0
90%	+687	+6	1154	0	1154
95%	1145	+8	1158	0	1158
Max	1145	+8	1158	0	1158

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	168	340	580	1000	1500
Min	37	20	67	20	68
5%	37	20	67	20	68
10%	68	40	68	20	68
25%	17	75	74	20	82
50%	92	96	92	96	99
75%	110	108	109	115	113
90%	151	119	151	159	122
95%	174	121	179	155	122
Max	174	121	179	155	122

HRS.	hFE (% Change from Initial)				
	168	340	580	1000	1500
Min	-89	-7	-77	-1	-89
5%	-89	-7	-77	-1	-89
10%	-54	-6	-77	-1	-84
25%	+2	-5	0	+2	-73
50%	+4	-2	+4	+4	+4
75%	+9	+3	+2	+2	+8
90%	+16	+12	+10	+13	+11
95%	+20	+14	+11	+13	+11
Max	+20	+14	+11	+13	+11

HRS.	BVCE0 (% Change from Initial)				
	168	340	580	1000	1500
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

PROCESS: B PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OF RATING POWER CONDITION: 700 mw, 30 V, 25°C. MIN 1.8% MAX 96.4 CELL NO.: 419222 NO. OF UNITS: 20

HRS.	Min	ICEO (VCB - 60V) (Nanamps)			
		168	340	680	1000
Init	0.5	0.1	0.1	0.1	0.1
50	0.5	0.1	0.1	0.1	0.1
100	0.5	0.2	0.2	0.1	0.2
200	0.4	0.5	0.3	0.2	0.2
300	0.4	0.9	0.7	0.5	0.4
400	1.3	2.4	2.2	1.9	1.7
500	6.9	17.0	12.6	11.0	10.3
600	55.8	94.4	32.2	28.7	24.1
700	123.1	53.8	0	0	0
Max					

HRS.	Min	IEBO (VEB - 5V) (Nanamps)			
		168	340	680	1000
Init	0.1	0.1	0.1	0.1	0.1
50	0.1	0.1	0.1	0.1	0.1
100	0.1	0.1	0.1	0.1	0.1
200	0.1	0.1	0.1	0.1	0.1
300	0.3	0.6	0.6	0.5	0.4
400	1.5	2.3	2.1	2.6	2.2
500	11.3	16.1	18.7	23.5	22.9
600	75.0	102.3	122.1	138.2	142.0
700	143.2	129.1	102.5	0	0
Max					

HRS.	Min	BV _{CEO} (IC - 0.1 ma) (Volts)			
		168	340	680	1000
Init	56	56	56	56	56
50	57	57	57	57	57
100	59	59	59	59	59
200	64	62	61	61	61
300	73	73	74	74	73
400	78	83	81	86	87
500	85	99	89	87	85
600	86	116	115	100	100
700	87	127	128	100	100
Max					

HRS.	Min	BV _{CEO} (% Change from Initial)			
		168	340	680	1000
Init	-21	-21	-21	-21	-21
50	-18	-18	-17	-17	-17
100	-12	-12	-12	-11	-11
200	-3	-4	-5	-4	-5
300	-1	-2	0	0	0
400	0	0	+2	+2	+1
500	+13	+12	+24	+23	+21
600	+125	+122	+123	+128	+129
700	+166	+159	+129	+128	+129
Max					

HRS.	Min	VCE(SAT) (IC-50ma, IB-5 ma) (Mv.)			
		168	340	680	1000
Init	000	087	087	087	087
50	040	086	087	088	087
100	069	087	087	089	087
200	093	091	091	092	094
300	102	099	097	101	099
400	109	105	106	114	104
500	123	118	115	116	116
600	134	139	139	140	130
700	140	147	148	132	132
Max					

HRS.	Min	VCE(SAT) (% Change from Initial)			
		168	340	680	1000
Init	-14	-13	-10	-9	-13
50	-13	-12	-10	-9	-13
100	-10	-10	-8	-8	-11
200	-5	-5	-4	-3	-6
300	-2	-2	-1	0	-3
400	+1	+1	+4	+5	+1
500	+4	+5	0	0	0
600	5502	5502	0	0	0
700	0	0	0	0	0
Max					

HRS.	Min	VBE(SAT) (IC-50 ma, IB-5 ma) (Mv.)			
		168	340	680	1000
Init	784	784	783	783	781
50	784	784	784	783	783
100	788	786	787	784	786
200	793	788	790	790	789
300	799	797	795	798	795
400	802	800	801	803	803
500	804	802	802	802	802
600	817	819	816	800	800
700	824	837	826	800	800
Max					

HRS.	Min	VBE(SAT) (% Change from Initial)			
		168	340	680	1000
Init	-1	-2	-2	-2	-1
50	-1	-2	-2	-2	-1
100	-1	-1	-1	-1	-1
200	0	-1	-1	-1	0
300	0	0	0	0	0
400	0	0	+1	0	+1
500	0	+1	+15	+13	+1
600	+1	+1	+155	+160	+2
700	+1	+1	+169	+169	+2
Max					

HRS.	Min	hFE (IC - 20 ma, VCE - 5V)			
		168	340	680	1000
Init	49	57	59	62	66
50	56	59	62	66	66
100	86	83	84	86	89
200	99	98	99	99	102
300	109	106	112	119	117
400	118	158	162	167	163
500	128	175	180	178	193
600	131	185	189	187	196
700					
Max					

HRS.	Min	hFE (% Change from Initial)			
		168	340	680	1000
Init	-22	-23	-28	-27	-30
50	-18	-18	-21	-26	-28
100	-12	-12	-25	-26	-28
200	-1	0	-5	-1	-6
300	+2	+5	+5	+3	+9
400	+11	+15	+18	+14	+16
500	+37	+42	+53	+33	+45
600	+52	+57	+88	+56	+67
700	+55	+61	+54	+60	+57
Max					

HRS.	Min	hFE			
		168	340	680	1000
Init	49	57	59	62	66
50	56	59	62	66	66
100	86	83	84	86	89
200	99	98	99	99	102
300	109	106	112	119	117
400	118	158	162	167	163
500	128	175	180	178	193
600	131	185	189	187	196
700					
Max					

HRS.	Min	BV _{CEO} (% Change from Initial)			
		168	340	680	1000
Init	-21	-21	-21	-21	-21
50	-18	-18	-17	-17	-17
100	-12	-12	-12	-11	-11
200	-3	-4	-5	-4	-5
300	-1	-2	0	0	0
400	0	0	+2	+2	+1
500	+13	+12	+24	+23	+21
600	+125	+122	+123	+128	+129
700	+166	+159	+129	+128	+129
Max					

PROCESS: B PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419223 NO. OF UNITS: 69

HRS.	ICBO (VCB - 60V) (Nanoamps)				
	Init	168	340	680	1000
5	0.1	0.6	0.7	0.1	0.1
10	0.2	0.8	1.1	0.4	0.1
25	0.3	1.1	1.3	0.5	0.1
50	0.7	1.3	1.6	0.7	0.5
75	1.0	1.9	2.2	1.3	1.1
90	2.5	3.6	3.4	2.7	2.5
95	3.2	4.6	4.5	2.8	3.3
100	4.4	9.1	7.3	3.3	2.1
105	13.3	∞	∞	∞	∞

HRS.	IEDO (VEB - 5V) (Nanoamps)				
	Init	168	340	680	1000
5	0.1	0.2	0.2	0.1	0.1
10	0.1	0.5	0.3	0.1	0.1
25	0.1	0.6	0.3	0.1	0.1
50	0.4	1.1	0.7	0.6	0.5
75	2.1	2.5	2.2	1.9	1.5
90	10.7	13.7	10.5	9.0	8.1
95	29.8	20.2	17.2	10.2	18.1
100	241.2	208.0	196.4	177.7	206.6
105	∞	∞	∞	∞	∞

HRS.	BVCEO (IC - 0.1 ma) (Volts)				
	Init	168	340	680	1000
5	58	67	69	71	71
10	63	61	61	60	59
25	65	64	64	63	63
50	69	66	66	66	66
75	73	72	71	71	71
90	79	78	78	78	79
95	84	85	85	85	84
100	86	89	98	89	96
105	105	114	∞	111	∞

HRS.	BVCEO (% Change from Initial)				
	Init	168	340	680	1000
5	-	-90	-88	-74	-93
10	-	-11	-13	-13	-18
25	-	-3	-3	-5	-10
50	-	-1	0	-1	-3
75	-	0	0	0	0
90	-	0	0	0	0
95	-	+1	+1	+1	+2
100	-	+3	+30	+3	+4
105	-	+55	+13	+50	+48

HRS.	VCE(SAT) (IC-50ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000
5	0.16	0.78	0.77	0.22	0.15
10	0.91	0.90	0.93	0.90	0.92
25	0.92	0.93	0.93	0.92	0.96
50	0.98	0.96	0.97	0.98	1.00
75	1.04	1.03	1.03	1.04	1.05
90	1.12	1.09	1.10	1.13	1.14
95	1.23	1.18	1.20	1.19	1.20
100	1.30	1.34	1.25	1.25	1.26
105	1.47	1.52	∞	1.65	∞

HRS.	VCE(SAT) (% Change from Initial)				
	Init	168	340	680	1000
5	-	-31	-29	-29	-87
10	-	-9	-9	-11	-10
25	-	-5	-5	-6	-4
50	-	-4	-3	-3	-3
75	-	-2	-1	0	+1
90	-	+1	+1	+3	+3
95	-	+2	+4	+5	+7
100	-	+4	+5	+8	+11
105	-	+54	∞	+56	+55

HRS.	VBE(SAT) (IC-50 ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000
5	717	612	284	283	215
10	786	287	285	283	280
25	787	284	286	285	284
50	790	287	289	288	286
75	795	292	295	292	293
90	800	296	299	297	299
95	808	301	305	302	305
100	810	307	310	308	314
105	900	328	∞	343	∞

HRS.	VBE(SAT) (% Change from Initial)				
	Init	168	340	680	1000
5	-	-23	-12	-12	-13
10	-	-3	-1	-1	-2
25	-	-1	-1	-1	-1
50	-	-1	0	-1	0
75	-	0	0	0	0
90	-	0	0	0	0
95	-	0	+1	+1	+1
100	-	+9	+16	+10	+9
105	-	∞	∞	∞	∞

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	680	1000
5	55	72	72	69	70
10	70	74	77	71	70
25	75	76	77	74	72
50	86	86	83	85	84
75	99	99	95	99	97
90	109	111	106	111	113
95	115	117	115	117	117
100	121	130	126	140	142
105	153	147	153	153	153

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000
5	-	-7	-8	-10	-83
10	-	-5	-11	-9	-80
25	-	-4	-8	-6	-3
50	-	-2	-5	-1	-3
75	-	0	-1	0	+1
90	-	+2	+1	+3	+1
95	-	+8	+6	+11	+15
100	-	+16	+13	+21	+26
105	-	+34	+27	+40	+42

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	680	1000
5	55	72	72	69	70
10	70	74	77	71	70
25	75	76	77	74	72
50	86	86	83	85	84
75	99	99	95	99	97
90	109	111	106	111	113
95	115	117	115	117	117
100	121	130	126	140	142
105	153	147	153	153	153

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000
5	-	-7	-8	-10	-83
10	-	-5	-11	-9	-80
25	-	-4	-8	-6	-3
50	-	-2	-5	-1	-3
75	-	0	-1	0	+1
90	-	+2	+1	+3	+1
95	-	+8	+6	+11	+15
100	-	+16	+13	+21	+26
105	-	+34	+27	+40	+42

PROCESS: 8 PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419224 NO. OF UNITS: 13

HRS.	ICEO (V _{CB} - 60V)(Nanoamps)					IEBO (V _{EB} - 5V)(Nanoamps)					BV _{CEO} (IC - 0.1 ma)(Volts)					BV _{CFO} (% Change from Initial)								
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
Min	0.1	1.2	0.7	0.5	0.5	0.1	0.3	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	62	62	63	63	62	62	61	61	61
5%	0.1	1.2	0.7	0.5	0.5	0.1	0.3	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	62	62	63	63	62	62	61	61	61
10%	0.2	1.2	0.8	0.5	0.5	0.2	0.3	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	63	63	63	63	63	63	62	62	62
25%	0.5	1.5	1.1	0.9	0.8	0.5	0.5	0.2	0.2	0.2	0.2	0.2	0.2	0.2	0.2	67	64	64	64	63	63	64	64	64
50%	0.8	1.8	1.5	1.2	1.0	0.6	0.6	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	72	73	73	73	73	73	73	73	73
75%	1.5	2.5	2.1	1.7	1.6	1.4	1.5	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	80	80	80	80	80	80	80	80	80
90%	2.3	3.1	3.8	2.2	2.0	2.0	2.0	2.0	2.0	2.0	2.0	2.0	2.0	2.0	2.0	82	82	82	82	82	82	82	82	82
95%	2.5	3.3	4.6	2.5	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	83	83	83	83	83	83	83	83	83
99%	2.5	3.2	4.6	2.5	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	83	83	83	83	83	83	83	83	83

HRS.	VCE (SAT) (IC-50ma, IB-5 ma)(Mv.)					VCE (SAT) (% Change from Initial)					VBE (SAT) (IC-50 ma, IB-5 ma)(Mv.)					VBE (SAT) (% Change from Initial)								
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
Min	108	084	088	083	086	087	087	079	-	-23	-19	-22	-21	-21	-23	-27	792	781	778	784	786	785	782	780
5%	108	084	088	083	086	087	087	079	-	-23	-19	-22	-21	-21	-23	-27	792	781	778	784	786	785	782	780
10%	108	088	080	088	088	089	089	082	-	-24	-18	-20	-20	-21	-22	-27	795	781	778	784	786	786	784	781
25%	117	103	101	101	100	102	099	099	-	-15	-14	-15	-17	-14	-17	-19	801	786	779	790	793	790	787	788
50%	119	104	105	105	105	106	104	102	-	-13	-12	-12	-15	-11	-15	-16	810	798	795	799	799	797	795	796
75%	135	123	123	123	117	120	118	118	-	-9	-10	-9	-10	-9	-11	-10	814	801	803	805	804	802	800	801
90%	148	130	131	131	130	133	129	128	-	-6	-9	-7	-9	-7	-8	-8	830	815	818	821	814	816	807	808
95%	150	132	132	131	132	130	130	130	-	-6	-9	-7	-9	-7	-8	-8	836	817	818	823	820	823	812	812
99%	150	132	132	131	132	130	130	130	-	-6	-9	-7	-9	-7	-8	-8	836	817	818	823	820	823	812	812

HRS.	hFE (IC - 20 ma, VCE - 5V)					hFE (% Change from Initial)										
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
Min	61	61	62	58	60	61	60	57	-	-10	-5	-14	-3	-2	-21	-25
5%	61	61	62	58	60	61	60	57	-	-10	-5	-14	-3	-2	-21	-25
10%	67	66	68	63	66	67	60	59	-	-9	-4	-12	-3	-2	-13	-16
25%	82	85	87	82	86	87	87	88	-	-5	+1	-12	-3	-2	-1	-1
50%	99	94	100	89	97	98	98	100	-	-1	+1	-5	-2	-1	0	+1
75%	112	108	107	103	109	110	111	112	-	+2	+3	-1	+3	+5	+5	+7
90%	130	129	145	145	153	128	153	151	-	+4	+13	+14	+19	+21	+22	+26
95%	137	137	159	168	171	212	210	211	-	+4	+16	+13	+25	+25	+21	+27
99%	137	137	159	168	171	212	210	211	-	+4	+16	+13	+25	+25	+21	+27

PROCESS: 6 PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.
 OPERATING POWER CONDITION: 200 mw, 30 V, 150°C. CELL NO.: 419225 NO. OF UNITS: 28

WRS.	V _{CEO} (V _{CB} - 60V) (Microamps)				
	Init	168	340	580	1000
100	0.3	0.6	0.5	0.3	0.2
105	0.3	0.7	0.5	0.4	0.2
110	0.4	0.9	0.7	0.5	0.3
115	1.1	1.5	1.2	1.1	0.7
120	2.0	2.7	2.4	2.0	1.8
125	3.1	3.6	3.4	2.7	2.5
130	3.7	25.7	21.9	6.1	14.5
135	18.6	154.9	211.2	190.3	135.3
140	30.0	199.9	359.4	328.7	221.4

WRS.	I _{EBO} (V _{EB} - 5V) (Microamps)				
	Init	168	340	580	1000
100	0.1	0.5	0.4	0.1	0.1
105	0.1	0.5	0.1	0.1	0.1
110	0.1	0.6	0.1	0.1	0.1
115	0.1	0.7	0.3	0.2	0.1
120	0.4	1.3	0.8	0.6	0.3
125	2.7	3.7	2.9	2.8	2.3
130	4.6	5.1	5.1	5.3	4.0
135	9.8	18.6	17.9	10.9	8.8
140	13.5	22.2	28.1	15.3	12.3

WRS.	V _{CEO} (I _C - 0.1 ma) (Volts)				
	Init	168	340	580	1000
100	59	59	58	58	58
105	59	59	59	58	58
110	61	61	61	61	61
115	64	64	64	64	64
120	71	71	71	71	71
125	79	80	80	80	80
130	86	86	86	86	86
135	87	86	86	86	86
140	87	86	87	87	87

WRS.	V _{V_{CEO}} (% Change from Initial)				
	Init	168	340	580	1000
100	-	-1	-5	-2	-3
105	-	-1	-3	-2	-3
110	-	0	0	0	-2
115	-	0	0	0	0
120	-	0	0	0	0
125	-	+2	+1	+1	+1
130	-	+6	+6	+5	+6
135	-	+7	+7	+1	+7
140	-				

WRS.	V _{CE} (SAT) (I _C - 50 ma, I _B - 5 ma) (Mv.)				
	Init	168	340	580	1000
100	110	088	093	092	091
105	112	090	093	093	091
110	115	095	097	098	095
115	119	101	101	101	100
120	128	108	102	110	108
125	141	123	122	124	125
130	150	130	129	130	126
135	152	136	134	136	134
140	153	137	134	139	135

WRS.	V _{CE} (SAT) (% Change from Initial)				
	Init	168	340	580	1000
100	-	-27	-24	-23	-24
105	-	-25	-24	-23	-24
110	-	-18	-19	-20	-21
115	-	-17	-17	-16	-16
120	-	-14	-15	-14	-15
125	-	-13	-12	-13	-13
130	-	-11	-11	-9	-12
135	-	-8	-9	-6	-8
140	-	-6	-8	-5	-8

WRS.	V _{BE} (SAT) (I _C - 50 ma, I _B - 5 ma) (Mv.)				
	Init	168	340	580	1000
100	794	778	779	780	785
105	795	776	780	781	785
110	798	788	782	785	785
115	802	784	786	787	788
120	809	791	792	795	794
125	818	802	802	804	803
130	828	809	812	815	816
135	839	819	821	824	813
140	846	824	824	830	822

WRS.	V _{BE} (SAT) (% Change from Initial)				
	Init	168	340	580	1000
100	-	-4	-4	-3	-3
105	-	-4	-4	-3	-3
110	-	-3	-3	-3	-3
115	-	-3	-2	-2	-3
120	-	-2	-2	-2	-2
125	-	-2	-2	-1	-1
130	-	-2	-1	-1	-1
135	-	-1	-1	-1	-1
140	-	-1	-1	-1	-1

WRS.	h _{FE} (I _C - 20 ma, V _{CE} - 5V)				
	Init	168	340	580	1000
100	64	65	64	61	63
105	65	65	64	61	64
110	66	67	68	65	66
115	85	84	83	79	82
120	98	98	98	92	96
125	112	108	107	110	110
130	118	115	114	117	119
135	125	116	120	112	120
140	129	117	122	115	121

WRS.	h _{FE} (% Change from Initial)				
	Init	168	340	580	1000
100	-	-14	-12	-16	-9
105	-	-11	-11	-16	-8
110	-	-7	-9	-14	-5
115	-	-5	-4	-11	-3
120	-	-1	-1	-7	-3
125	-	0	0	-5	-1
130	-	+1	0	-3	+1
135	-	+2	+3	-2	+4
140	-	+2	+3	-2	+6

WRS.	V _{BE} (SAT) (% Change from Initial)				
	Init	168	340	580	1000
100	-	-	-	-	-
105	-	-	-	-	-
110	-	-	-	-	-
115	-	-	-	-	-
120	-	-	-	-	-
125	-	-	-	-	-
130	-	-	-	-	-
135	-	-	-	-	-
140	-	-	-	-	-

PROCESS: β PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C. Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C. CELL NO.: 419226 NO. OF UNITS: 14

HRS.	ICEO (VCB - 60V) (Nanamps)				
	Init	168	340	580	1000
Min	0.2	0.3	0.3	0.3	0.1
5%	0.2	0.3	0.3	0.3	0.1
10%	0.3	0.3	0.3	0.3	0.1
25%	0.9	1.6	0.9	0.7	0.3
50%	1.5	1.8	1.2	1.0	1.0
75%	3.5	4.1	3.8	3.2	3.5
90%	4.6	4.9	4.4	4.0	4.2
95%	4.6	5.0	4.4	4.0	4.2
Max	4.6	5.0	4.4	4.0	4.2

HRS.	IEBO (VEB - 5V) (Nanamps)				
	Init	168	340	580	1000
Min	0.1	0.5	0.1	0.1	0.1
5%	0.1	0.5	0.1	0.1	0.1
10%	0.1	0.5	0.1	0.1	0.1
25%	0.1	0.7	0.1	0.2	0.2
50%	0.3	1.2	0.5	0.3	0.5
75%	1.7	2.7	2.3	2.3	1.1
90%	13.9	14.0	14.8	13.5	13.1
95%	22.0	14.1	16.6	17.8	14.0
Max	22.0	14.1	16.6	17.8	14.0

HRS.	BV _{CEO} (IC - 0.1 ma) (Volts)				
	Init	168	340	580	1000
Min	60	60	60	59	59
5%	60	60	60	59	59
10%	63	62	62	63	61
25%	69	69	67	69	66
50%	73	73	72	72	70
75%	81	85	84	83	79
90%	91	91	90	92	92
95%	92	91	91	92	92
Max	92	91	91	92	92

HRS.	BV _{CFO} (% Change from Initial)				
	Init	168	340	580	1000
Min	-	-3	-4	-4	-6
5%	-	-3	-4	-4	-6
10%	-	-3	-4	-3	-5
25%	-	-2	-2	-2	-3
50%	-	-1	-2	-1	-2
75%	-	0	0	-1	0
90%	-	+6	+5	+7	+6
95%	-	+6	+5	+8	+8
Max	-	+6	+5	+8	+8

HRS.	VCE(SAT) (IC-50ma, IB-5 ma) (Mv.)				
	Init	168	340	580	1000
Min	106	89	88	91	90
5%	106	89	88	90	90
10%	107	89	89	90	92
25%	115	98	98	99	101
50%	122	104	101	114	104
75%	137	131	128	124	121
90%	152	128	138	130	127
95%	165	128	130	129	129
Max	165	128	130	129	129

HRS.	VCE(SAT) (% Change from Initial)				
	Init	168	340	580	1000
Min	-	-19	-19	-19	-20
5%	-	-19	-19	-19	-20
10%	-	-18	-17	-18	-19
25%	-	-16	-17	-16	-16
50%	-	-15	-16	-14	-14
75%	-	-13	-13	-10	-11
90%	-	-10	-11	-7	-10
95%	-	-9	-10	-5	-9
Max	-	-9	-10	-5	-9

HRS.	VBE(SAT) (IC-50 ma, IB-5 ma) (Mv.)				
	Init	168	340	580	1000
Min	794	782	783	786	780
5%	794	782	783	786	780
10%	795	783	784	787	782
25%	804	785	785	789	784
50%	811	797	791	793	789
75%	816	796	795	796	796
90%	816	802	800	802	799
95%	816	802	800	802	799
Max	816	802	800	802	799

HRS.	VBE(SAT) (% Change from Initial)				
	Init	168	340	580	1000
Min	-	-2	-2	-2	-3
5%	-	-2	-2	-2	-3
10%	-	-2	-2	-2	-3
25%	-	-2	-2	-2	-3
50%	-	-2	-2	-2	-3
75%	-	-1	-1	-1	-2
90%	-	-1	-1	-1	-2
95%	-	-1	-1	-1	-2
Max	-	-1	-1	-1	-2

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	580	1000
Min	61	63	63	62	63
5%	61	63	63	62	63
10%	65	67	68	66	67
25%	77	78	79	77	78
50%	94	96	91	96	96
75%	98	101	103	100	103
90%	104	111	112	112	113
95%	105	112	115	114	115
Max	105	112	115	114	115

HRS.	hFE (% Change from Initial)				
	Init	168	340	580	1000
Min	-	-8	-7	-10	-9
5%	-	-8	-7	-10	-9
10%	-	-5	-7	-6	-5
25%	-	+1	+1	0	+1
50%	-	+4	+5	+2	+4
75%	-	+6	+7	+5	+6
90%	-	+8	+10	+9	+10
95%	-	+9	+11	+11	+11
Max	-	+9	+11	+11	+11

HRS.	hFE (% Change from Initial)				
	Init	168	340	580	1000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-

PROCESS: B PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C.

CELL NO.: 419227 NO. OF UNITS: 29

HRS.	ICBO (VCB - 60V) (Nanoamps)				
	168	340	680	1000L	5002000
Min	0.1	0.1	0.2	0.4	0.1
5%	0.2	0.3	0.2	0.4	0.3
10%	0.4	0.4	0.3	0.5	0.3
25%	1.0	1.8	1.1	1.3	1.0
50%	2.2	3.4	2.8	3.0	1.6
75%	3.6	4.5	3.5	3.3	2.9
90%	4.7	5.1	4.4	4.5	3.7
95%	4.9	4.8	4.9	4.8	3.9
Max	5.0	4.4	4.2	4.8	4.5

HRS.	IEBO (VEB - 5V) (Nanoamps)				
	168	340	680	1000L	5002000
Min	0.1	0.1	0.1	0.1	0.1
5%	0.1	0.1	0.1	0.1	0.1
10%	0.1	0.1	0.1	0.1	0.1
25%	0.1	0.2	0.2	0.2	0.2
50%	0.4	1.0	0.6	0.6	0.4
75%	1.3	2.0	1.7	1.3	1.1
90%	5.7	6.6	6.4	6.4	6.2
95%	14.9	11.2	12.1	10.0	12.8
Max	19.3	13.9	17.6	13.5	16.3

HRS.	BVCEO (IC - 0.1 ma) (Volts)				
	168	340	680	1000L	5002000
Min	63	63	63	62	59
5%	64	63	63	61	61
10%	65	64	64	63	62
25%	68	68	67	67	66
50%	72	73	71	71	70
75%	79	80	78	80	79
90%	83	86	87	88	88
95%	88	88	88	89	89
Max	90	89	89	89	91

HRS.	BVCEO (% Change from Initial)				
	168	340	680	1000L	5002000
Min	-2	-2	-9	-20	-14
5%	-2	-2	-56	-11	-13
10%	-1	-2	-2	-5	-4
25%	-1	-1	-2	-2	-3
50%	0	-1	-1	-1	-2
75%	+1	0	0	0	0
90%	+4	+3	+3	+5	+4
95%	+7	+7	+6	+7	+7
Max	+8	+8	+7	+7	+9

HRS.	VCE(SAT) (IC-50ma, IB-5 ma) (Mv.)				
	168	340	680	1000L	5002000
Min	0.98	0.92	0.88	0.86	0.82
5%	1.05	0.95	0.89	0.88	0.89
10%	1.12	0.92	0.93	0.85	0.93
25%	1.19	0.98	1.00	0.91	0.97
50%	1.26	1.05	1.06	1.06	1.06
75%	1.32	1.14	1.16	1.15	1.12
90%	1.39	1.19	1.19	1.27	1.22
95%	1.46	1.28	1.28	1.28	1.28
Max	1.51	1.28	1.28	1.28	1.28

HRS.	VCE(SAT) (% Change from Initial)				
	168	340	680	1000L	5002000
Min	-97	-32	-32	-33	-34
5%	-66	-26	-27	-26	-29
10%	-27	-18	-19	-20	-20
25%	-18	-17	-17	-18	-18
50%	-16	-16	-14	-15	-16
75%	-13	-14	-11	-12	-13
90%	-11	-9	-7	-7	-11
95%	-362	-6	233	263	233
Max	-252	-4	248	252	248

HRS.	VBE(SAT) (IC-50 ma, IB-5 ma) (Mv.)				
	168	340	680	1000L	5002000
Min	795	630	780	772	778
5%	796	704	780	782	778
10%	797	780	780	780	780
25%	800	784	784	784	784
50%	807	797	797	797	797
75%	814	796	799	794	797
90%	819	803	803	810	805
95%	831	803	807	807	807
Max	835	808	808	808	809

HRS.	VBE(SAT) (% Change from Initial)				
	168	340	680	1000L	5002000
Min	-22	-5	-5	-5	-5
5%	-14	-4	-4	-4	-4
10%	-3	-3	-2	-3	-2
25%	-2	-2	-2	-2	-2
50%	-2	-2	-2	-2	-2
75%	-2	-2	-2	-2	-2
90%	-1	-1	-1	-1	-1
95%	565	-1	1129	564	1129
Max	1130	-1	1130	1130	1130

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	168	340	680	1000L	5002000
Min	67	20	20	20	22
5%	69	44	20	44	20
10%	75	73	68	73	20
25%	85	84	82	85	85
50%	93	92	92	94	85
75%	102	99	103	103	104
90%	105	105	108	110	109
95%	109	106	112	115	116
Max	109	107	115	116	117

HRS.	hFE (% Change from Initial)				
	168	340	680	1000L	5002000
Min	-87	-11	-87	-87	-87
5%	-45	-11	-80	-46	-80
10%	-8	-10	-7	-10	-9
25%	-2	-4	-2	-1	-1
50%	0	+3	+5	+6	+5
75%	+2	+3	+7	+10	+11
90%	+5	+8	+9	+11	+12
95%	+5	+8	+9	+11	+12
Max	+5	+8	+9	+11	+12

HRS.	BVCEO (% Change from Initial)				
	168	340	680	1000L	5002000
Min	-2	-2	-9	-20	-14
5%	-2	-2	-56	-11	-13
10%	-1	-2	-2	-5	-4
25%	-1	-1	-2	-2	-3
50%	0	-1	-1	-1	-2
75%	+1	0	0	0	0
90%	+4	+3	+3	+5	+4
95%	+7	+7	+6	+7	+7
Max	+8	+8	+7	+7	+9

PROCESS: B PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419228 NO. OF UNITS: 70

ERS.	JCSO (VCB - 60V) (Nanoamps)				IEBO (VEB - 5V) (Nanoamps)				BVCEQ (IC - 0.1 ma) (Volts)				BVCFQ (% Change from Initial)			
	Init	168	340	580	1000L	500	2000	3000	Init	168	340	580	1000L	500	2000	3000
Min	0.2	0.9	1.3	2.4	0.3	0.2	0.3	0.5	60	60	60	60	60	60	60	60
5%	0.4	1.3	1.3	2.5	0.6	0.3	0.4	0.7	62	62	62	62	62	62	62	62
10%	0.5	1.2	1.5	2.7	0.7	0.5	0.6	1.0	65	65	66	66	66	65	63	65
25%	0.9	1.6	1.9	3.0	1.1	0.7	1.0	1.9	70	69	70	70	69	70	69	69
50%	2.1	3.4	3.3	5.2	2.3	2.5	2.3	3.6	73	73	73	73	73	73	73	73
75%	3.7	4.5	4.2	7.2	3.5	3.4	3.4	4.0	80	81	81	80	80	80	80	80
90%	4.1	5.0	4.6	7.9	4.0	4.2	4.2	4.6	85	85	86	85	85	85	85	85
95%	4.5	5.3	4.9	8.7	4.7	5.1	5.6	6.7	87	87	87	87	87	87	87	87
Max	4.8	5.8	5.2	10.0	5.2	5.8	6.3	7.1	89	89	89	89	89	89	89	89

ERS.	VCE(SAT) (IC-50 ma, IB-5 ma) (mv.)				VCE(SAT) (% Change from Initial)				VBE(SAT) (IC-50 ma, IB-5 ma) (mv.)				VBE(SAT) (% Change from Initial)			
	Init	168	340	580	1000L	500	2000	3000	Init	168	340	580	1000L	500	2000	3000
Min	085	088	090	086	088	089	086	086	791	794	784	663	780	127	777	727
5%	092	093	094	092	093	092	092	092	795	790	784	783	783	783	780	780
10%	094	096	099	097	097	094	094	094	798	784	785	784	783	783	780	780
25%	100	100	102	100	102	100	100	100	808	794	787	787	786	785	783	783
50%	105	105	107	107	106	105	105	105	807	789	783	783	782	782	782	782
75%	111	113	113	111	114	111	115	115	813	795	797	797	797	795	794	794
90%	124	125	128	127	127	128	128	128	822	791	790	782	780	789	789	789
95%	136	138	137	138	137	139	142	142	833	790	803	803	803	804	801	801
Max	144	145	143	144	143	143	143	143	921	824	822	823	819	820	820	820

ERS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)			
	Init	168	340	580	1000L	500	2000	3000
Min	36	47	50	57	57	58	58	58
5%	58	58	57	59	60	58	57	57
10%	67	70	66	69	70	68	65	65
25%	84	85	87	83	84	86	84	83
50%	93	93	91	93	93	96	97	96
75%	101	101	96	100	99	102	103	104
90%	103	106	103	106	106	107	106	108
95%	105	108	105	108	107	109	109	109
Max	108	110	108	109	109	113	113	115

PROCESS: 8 PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.
 OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419229 NO. OF UNITS: 14-

HRS.	VCE0 (VCE - 60V) (Nanocamp.)				
	Init	168	340	680	1000
5%	0.2	0.7	0.5	0.3	0.1
10%	0.2	0.7	0.5	0.3	0.1
25%	0.4	1.1	0.6	0.3	0.1
50%	1.9	2.5	2.2	1.8	1.3
75%	4.4	4.6	4.2	3.9	3.1
90%	5.1	4.6	4.2	3.5	3.1
95%	5.4	4.6	4.5	3.5	3.2
Max	5.4	4.6	4.5	3.5	3.2

Init	IEBO (VEB - 5V) (Nanocamps)				
	168	340	680	1000	1500
0.1	0.6	0.1	0.2	0.1	0.1
0.1	0.6	0.1	0.2	0.1	0.1
0.1	0.6	0.2	0.2	0.1	0.1
0.1	0.9	0.3	0.3	0.1	0.1
0.1	1.1	0.5	0.5	0.3	0.3
1.1	2.0	1.4	1.2	0.8	1.1
5.5	6.9	6.0	5.6	4.9	5.1
5.7	7.5	6.6	6.0	5.3	5.7
5.7	7.5	6.6	6.0	5.3	5.7

Init	BVCE0 (IC - 0.1 ma) (Volts)				
	168	340	680	1000	1500
61	61	61	61	61	61
61	61	61	61	61	61
61	61	61	61	61	61
68	68	68	68	68	68
74	75	76	75	76	76
78	78	77	77	78	79
89	91	91	90	92	92
91	91	91	91	92	93
91	91	91	91	92	93

Init	BVCF0 (% Change from Initial)				
	168	340	680	1000	1500
-	-15	-12	-15	-9	-2
-	-15	-12	-15	-9	-2
-	-8	-7	-9	-6	-2
-	-	-	-	-	-
-	0	0	0	0	0
-	+18	+19	+18	+21	+21
-	+36	+37	+35	+39	+41
-	+36	+37	+35	+39	+41

HRS.	VCE(SAT) (IC=50ma, IB=5 ma) (Mv.)				
	Init	168	340	680	1000
107	093	010	090	091	059
107	093	010	090	091	059
110	096	015	095	094	080
117	102	101	100	099	102
129	105	106	105	105	106
128	113	114	114	112	114
138	117	116	118	115	118
138	117	116	120	116	120
138	117	116	120	116	120

Init	VCE(SAT) (% Change from Initial)				
	168	340	680	1000	1500
-26	-22	-28	-27	-23	-28
-26	-22	-28	-27	-23	-28
-23	-20	-24	-24	-25	-24
-18	-16	-16	-17	-16	-17
-14	-14	-14	-15	-15	-14
-10	-12	-10	-13	-11	-13
-2	-1	-2	-3	-1	-3
+6	+7	+6	+5	+7	+5
+6	+7	+6	+5	+7	+5

Init	VBE(SAT) (IC=50 ma, IB=5 ma) (Mv.)				
	168	340	680	1000	1500
797	780	510	780	782	715
797	780	510	780	782	715
797	780	647	787	784	776
801	787	787	787	787	783
808	793	794	798	796	794
815	798	798	806	800	799
820	810	801	804	802	804
822	810	812	815	812	804
822	810	812	815	812	804

Init	VBE(SAT) (% Change from Initial)				
	168	340	680	1000	1500
-3	-36	-3	-3	-2	-3
-3	-36	-3	-3	-2	-3
-3	-19	-3	-3	-2	-3
-2	-2	-2	-2	-2	-2
-2	-2	-2	-2	-2	-2
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	680	1000
77	75	75	72	77	78
77	75	75	72	77	78
77	76	75	73	77	78
87	82	81	77	80	81
94	91	90	89	94	95
97	96	95	95	101	102
105	104	102	105	106	107
106	108	103	108	118	124
106	108	103	108	118	124

Init	hFE (% Change from Initial)				
	168	340	680	1000	1500
-15	-16	-21	-21	-19	-17
-15	-16	-21	-21	-19	-17
-11	-12	-15	-14	-12	-11
-6	-7	-7	-8	-1	-2
-1	-1	-5	+1	+2	+7
+2	+3	-2	+3	+4	+10
+5	+4	+1	+5	+6	+23
+5	+4	+1	+5	+7	+22
+5	+4	+1	+5	+7	+22

Init	hFE (% Change from Initial)				
	168	340	680	1000	1500
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-
-	-	-	-	-	-

PROCESS: 6 PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION:

200 mw, 30 V, 150°C.

CELL NO.: 419230 NO. OF UNITS: 29

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	0.4	0.8	0.6	0.5	0.3
5%	0.5	0.9	0.7	0.5	0.4
10%	0.6	1.2	0.8	0.6	0.4
25%	0.9	1.5	1.2	1.0	0.9
50%	1.4	2.0	1.7	1.6	1.3
75%	3.2	3.7	3.4	2.9	2.7
90%	3.8	4.3	4.6	4.0	4.3
95%	4.6	4.8	5.6	6.8	2.2
MAX	4.8	5.0	6.1	7.9	9.0

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	0.1	0.6	0.1	0.1	0.1
5%	0.1	0.7	0.2	0.1	0.1
10%	0.1	0.8	0.3	0.2	0.2
25%	0.2	1.0	0.5	0.4	0.4
50%	1.3	1.9	1.5	1.6	1.2
75%	3.9	4.0	3.6	3.5	3.1
90%	10.9	13.2	12.6	11.7	11.3
95%	24.4	50.6	29.9	17.2	15.0
MAX	25.6	78.3	25.2	24.6	23.5

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	0.1	0.6	0.1	0.1	0.1
5%	0.1	0.7	0.2	0.1	0.1
10%	0.1	0.8	0.3	0.2	0.2
25%	0.2	1.0	0.5	0.4	0.4
50%	1.3	1.9	1.5	1.6	1.2
75%	3.9	4.0	3.6	3.5	3.1
90%	10.9	13.2	12.6	11.7	11.3
95%	24.4	50.6	29.9	17.2	15.0
MAX	25.6	78.3	25.2	24.6	23.5

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	0.1	0.6	0.1	0.1	0.1
5%	0.1	0.7	0.2	0.1	0.1
10%	0.1	0.8	0.3	0.2	0.2
25%	0.2	1.0	0.5	0.4	0.4
50%	1.3	1.9	1.5	1.6	1.2
75%	3.9	4.0	3.6	3.5	3.1
90%	10.9	13.2	12.6	11.7	11.3
95%	24.4	50.6	29.9	17.2	15.0
MAX	25.6	78.3	25.2	24.6	23.5

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	105	083	087	085	084
5%	109	085	089	086	085
10%	119	092	099	094	090
25%	123	102	104	106	101
50%	130	109	111	113	108
75%	139	119	122	124	120
90%	158	138	136	135	138
95%	161	143	142	143	139
MAX	162	144	144	144	140

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	-29	-27	-29	-30	-31
5%	-26	-23	-24	-25	-25
10%	-18	-18	-17	-20	-22
25%	-18	-17	-15	-18	-17
50%	-16	-14	-14	-16	-16
75%	-12	-13	-11	-14	-12
90%	-11	-12	-10	-12	-11
95%	-11	-10	-9	-10	-9
MAX	-10	-9	-8	-9	-8

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	105	083	087	085	084
5%	109	085	089	086	085
10%	119	092	099	094	090
25%	123	102	104	106	101
50%	130	109	111	113	108
75%	139	119	122	124	120
90%	158	138	136	135	138
95%	161	143	142	143	139
MAX	162	144	144	144	140

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	105	083	087	085	084
5%	109	085	089	086	085
10%	119	092	099	094	090
25%	123	102	104	106	101
50%	130	109	111	113	108
75%	139	119	122	124	120
90%	158	138	136	135	138
95%	161	143	142	143	139
MAX	162	144	144	144	140

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	56	20	20	20	20
5%	57	38	38	37	38
10%	70	68	59	58	59
25%	75	86	77	76	77
50%	88	97	88	87	89
75%	97	95	97	96	98
90%	107	108	105	106	103
95%	108	109	107	110	108
MAX	108	109	109	111	114

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	-5	-7	-7	-7	-7
5%	-5	-4	-3	-3	-3
10%	-4	-3	-3	-3	-3
25%	-1	-1	-1	-1	-1
50%	0	0	0	0	0
75%	+1	+1	+1	+1	+1
90%	+2	+4	+4	+4	+4
95%	+6	+8	+8	+8	+8
MAX	+8	+8	+8	+8	+8

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	56	20	20	20	20
5%	57	38	38	37	38
10%	70	68	59	58	59
25%	75	86	77	76	77
50%	88	97	88	87	89
75%	97	95	97	96	98
90%	107	108	105	106	103
95%	108	109	107	110	108
MAX	108	109	109	111	114

RES.	VCE (VCE - 5V) (Microamps)				
	168	340	580	1000	1500
MIN	56	20	20	20	20
5%	57	38	38	37	38
10%	70	68	59	58	59
25%	75	86	77	76	77
50%	88	97	88	87	89
75%	97	95	97	96	98
90%	107	108	105	106	103
95%	108	109	107	110	108
MAX	108	109	109	111	114

PROCESS: B PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C.

CELL NO.: 419231 NO. OF UNITS: 7

S.	ICEO (VCB - 60V) (Nanoamps)			
	Init	168	340	580
Min	0.6	1.3	0.9	0.8
5%	0.6	1.3	0.9	0.8
10%	0.6	1.3	0.9	0.8
25%	1.6	1.9	1.7	0.9
50%	3.2	3.3	2.1	3.3
75%	3.6	3.8	4.3	3.0
90%	5.1	4.5	4.0	3.7
95%	5.1	4.5	4.0	3.7
Max	5.1	4.5	4.0	3.7

S.	IEBO (VEB - 5V) (Nanoamps)			
	Init	168	340	580
Min	0.1	0.5	0.1	0.1
5%	0.1	0.5	0.1	0.1
10%	0.1	0.5	0.1	0.1
25%	0.1	0.5	0.1	0.1
50%	0.8	0.7	1.0	0.3
75%	1.2	2.7	2.3	2.3
90%	2.5	2.7	2.3	2.3
95%	2.5	2.7	2.3	2.3
Max	2.5	2.7	2.3	2.3

S.	BVCEO (IC - 0.1 ma) (Volts)			
	Init	168	340	580
Min	64	63	63	63
5%	64	63	63	63
10%	64	63	63	63
25%	66	66	66	65
50%	73	71	71	71
75%	77	75	75	75
90%	81	77	77	77
95%	81	77	77	77
Max	81	77	77	77

S.	BVCEO (% Change from Initial)			
	Init	168	340	580
Min	-	-8	-6	-3
5%	-	-8	-6	-3
10%	-	-8	-6	-3
25%	-	-4	-5	-2
50%	-	-2	-2	-2
75%	-	0	-1	-1
90%	-	+3	+2	+3
95%	-	+3	+2	+3
Max	-	+3	+2	+3

S.	VCE(SAT) (IC-50ma, IB-5 ma) (Mv.)			
	Init	168	340	580
Min	111	091	094	094
5%	111	091	094	094
10%	114	091	094	094
25%	114	095	097	097
50%	119	103	100	102
75%	129	113	115	120
90%	137	115	115	134
95%	137	115	115	134
Max	137	115	115	134

S.	VCE(SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-23	-21	-20
5%	-	-23	-20	-20
10%	-	-23	-20	-20
25%	-	-16	-17	-14
50%	-	-13	-13	-12
75%	-	-12	-11	-8
90%	-	-11	-11	-4
95%	-	-11	-11	-4
Max	-	-11	-11	-4

S.	VBE(SAT) (IC-50 ma, IB-5 ma) (Mv.)			
	Init	168	340	580
Min	798	780	785	784
5%	798	780	785	784
10%	798	780	785	784
25%	799	785	788	788
50%	800	791	792	790
75%	808	798	797	800
90%	812	801	800	807
95%	812	801	800	807
Max	812	801	800	807

S.	VBE(SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-2	-2	-2
5%	-	-2	-2	-2
10%	-	-2	-2	-2
25%	-	-2	-2	-2
50%	-	-1	-1	-1
75%	-	-1	-1	-1
90%	-	-1	-1	0
95%	-	-1	-1	0
Max	-	-1	-1	0

S.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	580
Min	82	78	79	77
5%	82	78	79	77
10%	82	78	79	77
25%	82	77	86	88
50%	100	108	103	109
75%	106	117	112	115
90%	107	117	113	117
95%	107	117	113	117
Max	107	117	113	117

S.	hFE (% Change from Initial)			
	Init	168	340	580
Min	-	-17	-17	-18
5%	-	-17	-17	-18
10%	-	-17	-17	-18
25%	-	+3	+4	+2
50%	-	+10	+7	+6
75%	-	+42	+36	+43
90%	-	+42	+36	+43
95%	-	+42	+36	+43
Max	-	+42	+36	+43

S.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	580
Min	82	78	79	77
5%	82	78	79	77
10%	82	78	79	77
25%	82	77	86	88
50%	100	108	103	109
75%	106	117	112	115
90%	107	117	113	117
95%	107	117	113	117
Max	107	117	113	117

S.	hFE (% Change from Initial)			
	Init	168	340	580
Min	-	-17	-17	-18
5%	-	-17	-17	-18
10%	-	-17	-17	-18
25%	-	+3	+4	+2
50%	-	+10	+7	+6
75%	-	+42	+36	+43
90%	-	+42	+36	+43
95%	-	+42	+36	+43
Max	-	+42	+36	+43

PROCESS: B FAB-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C.

CELL NO.: 419232 NO. OF UNITS: 15

V.S.	I _{CB} (V _{CB} - 60V) (Nanamps)			
	168	340	580	1000
Min	0.4	0.5	0.5	0.1
5%	0.4	0.5	0.5	0.1
10%	0.5	0.6	0.6	0.2
25%	0.8	1.2	1.0	0.5
50%	1.3	2.1	1.5	1.3
75%	2.6	3.2	3.0	2.7
90%	3.2	3.6	3.4	3.1
95%	3.3	3.9	3.8	3.5
99%	3.3	3.9	3.8	3.5

V.S.	I _{EB} (V _{EB} - 5V) (Nanamps)			
	168	340	580	1000
Min	0.1	0.4	0.1	0.2
5%	0.1	0.4	0.1	0.2
10%	0.1	0.5	0.1	0.3
25%	0.2	0.7	0.3	0.3
50%	0.5	1.1	0.8	0.7
75%	1.7	2.1	1.7	1.6
90%	25.3	23.9	21.6	20.0
95%	31.8	30.5	28.0	26.0
99%	31.8	30.5	28.0	26.0

V.S.	BV _{CEO} (I _C - 0.1 ma) (Volts)			
	168	340	580	1000
Min	62	62	62	61
5%	62	62	62	61
10%	64	63	63	63
25%	65	65	65	65
50%	68	72	72	73
75%	79	84	85	88
90%	88	95	95	96
95%	90	103	104	105
99%	90	103	104	105

V.S.	BV _{CEO} (% Change from Initial)			
	168	340	580	1000
Min	-2	-3	-3	-9
5%	-2	-3	-3	-9
10%	-2	-3	-3	-9
25%	-1	-1	-1	-3
50%	0	0	0	0
75%	+1	+2	+2	+5
90%	+22	+29	+33	+36
95%	+34	+35	+36	+37
99%	+34	+35	+36	+37

V.S.	V _{CE} (SAT) (I _C - 50 ma, I _B - 5 ma) (Mv.)			
	168	340	580	1000
Min	104	089	088	090
5%	104	089	088	090
10%	106	090	089	093
25%	114	099	100	101
50%	126	104	104	107
75%	132	109	113	117
90%	141	118	117	120
95%	145	118	120	122
99%	143	118	120	122

V.S.	V _{CE} (SAT) (% Change from Initial)			
	168	340	580	1000
Min	-2.5	-2.2	-2.1	-2.4
5%	-2.5	-2.2	-2.1	-2.4
10%	-2.4	-2.1	-1.9	-2.2
25%	-1.9	-1.9	-1.7	-1.8
50%	-1.7	-1.7	-1.5	-1.4
75%	-1.4	-1.3	-1.1	-1.1
90%	-1.0	-1.1	-0.8	-0.9
95%	-0.9	-1.1	-0.7	-0.8
99%	-0.9	-1.1	-0.7	-0.8

V.S.	V _{BE} (SAT) (I _C - 50 ma, I _B - 5 ma) (Mv.)			
	168	340	580	1000
Min	721	787	786	786
5%	721	787	786	786
10%	767	787	786	786
25%	804	791	790	793
50%	808	795	794	795
75%	810	796	795	795
90%	816	798	795	799
95%	817	799	795	799
99%	817	799	795	799

V.S.	V _{BE} (SAT) (% Change from Initial)			
	168	340	580	1000
Min	-4	-3	-3	-3
5%	-4	-3	-3	-3
10%	-3	-3	-3	-3
25%	-2	-3	-3	-3
50%	-2	-2	-2	-2
75%	-1	-2	-2	-2
90%	+3	+3	+3	+3
95%	+10	+10	+10	+10
99%	+10	+10	+10	+10

V.S.	h _{FE} (I _C - 20 ma, V _{CE} - 5V)			
	168	340	580	1000
Min	76	58	57	61
5%	76	58	57	61
10%	78	68	66	66
25%	86	80	78	73
50%	93	90	91	94
75%	100	98	99	101
90%	106	102	104	109
95%	110	104	106	112
99%	110	104	106	112

V.S.	h _{FE} (% Change from Initial)			
	168	340	580	1000
Min	-4.2	-4.3	-3.9	-7.7
5%	-4.2	-4.3	-3.9	-7.7
10%	-2.5	-2.6	-2.8	-7.6
25%	-3	-2	-2	-7.5
50%	-2	0	0	-7.2
75%	+1	+4	+3	+4
90%	+7	+9	+14	+16
95%	+11	+13	+16	+18
99%	+11	+13	+16	+18

V.S.	BV _{CEO} (% Change from Initial)			
	168	340	580	1000
Min	-2	-3	-3	-9
5%	-2	-3	-3	-9
10%	-2	-3	-3	-9
25%	-1	-1	-1	-3
50%	0	0	0	0
75%	+1	+2	+2	+5
90%	+22	+29	+33	+36
95%	+34	+35	+36	+37
99%	+34	+35	+36	+37

PROCESS: B FAB-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419233 NO. OF UNITS: 40

FRS.	ICEO (V _{CB} - 60V)(Nanoamps)			
	Init	168	340	580
Min	0.5	0.8	1.2	0.4
5%	0.5	0.9	1.5	0.5
10%	0.7	1.2	1.6	0.7
25%	1.0	1.6	1.8	1.3
50%	1.8	2.6	2.9	2.3
75%	3.7	4.3	4.2	3.9
90%	4.3	5.8	5.2	4.5
95%	4.8	12.8	9.5	12.7
Max	4.9	∞	∞	∞

FRS.	IEBO (V _{EB} - 5V)(Nanoamps)			
	Init	168	340	580
Min	<0.1	0.6	0.3	0.1
5%	<0.1	0.6	0.3	0.1
10%	<0.1	0.7	0.5	0.2
25%	0.1	0.9	0.6	0.4
50%	0.4	1.2	0.8	0.6
75%	0.8	1.7	1.4	1.3
90%	4.8	7.0	8.8	9.7
95%	12.4	∞	∞	∞
Max	12.4	∞	∞	∞

FRS.	BVCEO (I _C - 0.1 ma.)(Volts)			
	Init	168	340	580
Min	60	0.5	0.6	0.8
5%	61	6.0	6.0	6.0
10%	63	6.2	6.3	6.2
25%	66	6.6	6.6	6.6
50%	73	7.2	7.2	7.2
75%	79	8.1	8.0	8.0
90%	86	8.8	8.8	8.8
95%	89	9.2	9.3	9.3
Max	89	12.3	12.5	12.3

FRS.	BVCEO (% Change from Initial)			
	Init	168	340	580
Min	-	-9.3	-9.1	-8.7
5%	-	-1	-1	-2
10%	-	-1	-1	-1
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	+4	+4	+4
95%	-	+5	+5	+5
Max	-	+40	+42	+39

FRS.	VCS (SAT) (I _C 50ma, I _B 5 ma)(Mv.)			
	Init	168	340	580
Min	104	0.84	0.83	0.83
5%	106	0.92	0.93	0.93
10%	116	0.95	0.97	0.97
25%	119	1.01	1.03	1.01
50%	126	1.08	1.09	1.07
75%	132	1.17	1.18	1.18
90%	151	1.28	1.27	1.27
95%	168	1.32	1.33	1.32
Max	160	1.43	1.39	1.39

FRS.	VCE (SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-2.1	-1.9	-2.1
5%	-	-2.1	-1.9	-2.0
10%	-	-1.9	-1.8	-1.8
25%	-	-1.7	-1.7	-1.6
50%	-	-1.5	-1.5	-1.5
75%	-	-1.1	-1.3	-1.1
90%	-	-1.0	-0.9	-0.7
95%	-	-0.8	-0.5	-0.5
Max	-	-0.9	+1.1	+1.3

FRS.	VBE (SAT) (I _C 50 ma, I _B 5 ma)(Mv.)			
	Init	168	340	580
Min	714	780	781	310
5%	793	781	783	310
10%	799	783	785	310
25%	802	786	789	310
50%	805	791	794	310
75%	814	795	799	310
90%	824	802	805	310
95%	830	815	815	310
Max	844	811	815	310

FRS.	VBE (SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-6	-6	-6
5%	-	-4	-3	-6
10%	-	-3	-2	-3
25%	-	-2	-2	-2
50%	-	-2	-2	-2
75%	-	-3	-1	-2
90%	-	-1	-1	-1
95%	-	-1	0	+1
Max	-	+11	+11	+11

FRS.	hFE (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	580
Min	69	20	61	62
5%	69	60	68	68
10%	75	74	73	70
25%	85	84	83	82
50%	90	93	91	91
75%	97	99	97	95
90%	99	100	100	101
95%	102	107	108	108
Max	103	110	109	108

FRS.	hFE (% Change from Initial)			
	Init	168	340	580
Min	-	-22	-37	-36
5%	-	-36	-8	-8
10%	-	-6	-6	-5
25%	-	-1	-3	-3
50%	-	+2	-1	0
75%	-	+6	+4	+3
90%	-	+8	+7	+9
95%	-	+12	+9	+11
Max	-	+16	+15	+11

FRS.	hFE (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	580
Min	69	20	61	62
5%	69	60	68	68
10%	75	74	73	70
25%	85	84	83	82
50%	90	93	91	91
75%	97	99	97	95
90%	99	100	100	101
95%	102	107	108	108
Max	103	110	109	108

FRS.	hFE (% Change from Initial)			
	Init	168	340	580
Min	-	-22	-37	-36
5%	-	-36	-8	-8
10%	-	-6	-6	-5
25%	-	-1	-3	-3
50%	-	+2	-1	0
75%	-	+6	+4	+3
90%	-	+8	+7	+9
95%	-	+12	+9	+11
Max	-	+16	+15	+11

PROCESS: 5 PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419234 NO. OF UNITS: 7

MRS.	IC50 (V _{CB} - 60V)(Nanoamps)				
	Init	168	340	680	1000
Min	0.5	1.0	0.3	0.3	0.7
5%	0.5	1.0	0.3	0.3	0.7
10%	0.5	1.0	0.3	0.3	0.7
25%	0.8	1.3	0.9	0.7	0.7
50%	1.5	1.9	1.6	1.3	1.2
75%	4.4	4.6	4.0	3.8	3.5
90%	4.8	4.7	4.5	4.0	3.5
95%	4.8	4.7	4.5	4.0	3.5
Max	4.8	4.7	4.5	4.0	3.5

MRS.	IC50 (V _{EB} - 5V)(Nanoamps)				
	Init	168	340	680	1000
Min	0.1	0.3	0.1	0.1	0.4
5%	0.1	0.3	0.1	0.1	0.4
10%	0.1	0.3	0.1	0.1	0.4
25%	0.1	0.7	0.1	0.3	0.5
50%	0.4	1.0	0.4	0.5	0.8
75%	0.6	1.2	0.7	0.7	0.8
90%	1.5	1.8	1.7	1.5	0.9
95%	1.5	1.8	1.7	1.5	0.9
Max	1.5	1.8	1.7	1.5	0.9

MRS.	BVCEO (I _C - 0.1 ma)(Volts)				
	Init	168	340	680	1000
Min	71	71	71	71	71
5%	71	71	71	71	71
10%	71	71	71	71	71
25%	71	71	71	71	71
50%	71	71	74	74	74
75%	76	76	90	90	90
90%	90	90	90	90	90
95%	90	90	90	90	90
Max	90	90	90	90	90

MRS.	BVCF0 (% Change from Initial)				
	Init	168	340	680	1000
Min	-	0	0	0	0
5%	-	0	0	0	0
10%	-	0	0	0	0
25%	-	0	0	0	0
50%	-	0	0	0	0
75%	-	0	0	0	0
90%	-	0	0	0	0
95%	-	0	0	0	0
Max	-	0	0	0	0

MRS.	VCE(SAT)(I _C -50ma, I _B -5 ma)(mV.)				
	Init	168	340	680	1000
Min	108	88	101	89	88
5%	108	88	101	89	88
10%	108	88	101	89	88
25%	113	89	92	85	85
50%	120	100	99	102	103
75%	125	112	110	110	109
90%	128	114	113	111	110
95%	128	114	113	111	110
Max	128	114	113	111	110

MRS.	VCE(SAT)(% Change from Initial)				
	Init	168	340	680	1000
Min	-	-19	-99	-99	-18
5%	-	-19	-99	-99	-18
10%	-	-19	-99	-99	-18
25%	-	-18	-18	-18	-15
50%	-	-13	-13	-12	-14
75%	-	-12	-12	-12	-12
90%	-	-9	-11	-11	-10
95%	-	-9	-11	-11	-10
Max	-	-9	-11	-11	-10

MRS.	VBE(SAT)(I _C -50 ma, I _B -5 ma)(mV.)				
	Init	168	340	680	1000
Min	795	781	785	782	786
5%	795	781	785	782	786
10%	795	781	785	782	786
25%	800	783	786	785	786
50%	801	787	794	794	793
75%	804	795	793	795	796
90%	811	795	797	797	798
95%	811	795	797	797	798
Max	811	795	797	797	798

MRS.	VBE(SAT)(% Change from Initial)				
	Init	168	340	680	1000
Min	-	-2	-2	-2	-2
5%	-	-2	-2	-2	-2
10%	-	-2	-2	-2	-2
25%	-	-2	-2	-2	-2
50%	-	-2	-2	-2	-2
75%	-	-2	-2	-2	-2
90%	-	-2	-2	-2	-2
95%	-	-2	-2	-2	-2
Max	-	-2	-2	-2	-2

MRS.	h _{FE} (I _C - 20 ma, V _{CE} - 5V)				
	Init	168	340	680	1000
Min	85	82	76	77	79
5%	85	82	76	77	79
10%	85	82	76	77	79
25%	84	82	76	77	82
50%	94	94	93	87	87
75%	99	97	94	100	105
90%	103	101	98	100	105
95%	103	101	98	100	105
Max	103	101	98	100	105

MRS.	h _{FE} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-3	-10	-9	-7
5%	-	-3	-10	-9	-7
10%	-	-3	-10	-9	-7
25%	-	-2	-5	-8	-6
50%	-	-1	-2	-7	-2
75%	-	0	-1	-3	+1
90%	-	0	-1	-3	+2
95%	-	0	-1	-3	+2
Max	-	0	-1	-3	+2

MRS.	h _{FE} (I _C - 20 ma, V _{CE} - 5V)				
	Init	168	340	680	1000
Min	85	82	76	77	79
5%	85	82	76	77	79
10%	85	82	76	77	79
25%	84	82	76	77	82
50%	94	94	93	87	87
75%	99	97	94	100	105
90%	103	101	98	100	105
95%	103	101	98	100	105
Max	103	101	98	100	105

MRS.	h _{FE} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-3	-10	-9	-7
5%	-	-3	-10	-9	-7
10%	-	-3	-10	-9	-7
25%	-	-2	-5	-8	-6
50%	-	-1	-2	-7	-2
75%	-	0	-1	-3	+1
90%	-	0	-1	-3	+2
95%	-	0	-1	-3	+2
Max	-	0	-1	-3	+2

PROCESS: B PAK-SCREEN STRESS: 25 Kg Centrifuge Only.
 OPERATING POWER CONDITIONS: 200 mw, 30 V, 150°C.

CELL NO.: 419235 NO. OF UNITS: 15

MRS.	ICBO (Vcs - 60V) (Microamps)			
	Init	168	340	580
100	0.6	1.4	1.0	0.8
102	0.6	1.4	1.0	0.8
104	0.7	1.4	1.0	0.9
106	1.3	1.7	1.3	1.2
108	2.0	2.5	2.3	2.3
110	3.0	3.8	3.8	3.0
112	4.5	14.9	12.5	12.5
114	4.9	30.1	28.2	28.2
116	4.9	30.1	28.2	28.2

MRS.	IEBO (Vcs - 5V) (Microamps)			
	Init	168	340	580
100	0.1	0.8	0.2	0.3
102	0.1	0.8	0.2	0.3
104	0.1	0.8	0.2	0.3
106	0.2	0.8	0.3	0.4
108	0.3	1.0	0.5	0.5
110	0.7	1.5	1.1	1.3
112	9.1	7.0	6.4	5.3
114	12.2	7.8	7.9	7.4
116	12.2	7.8	7.4	7.4

MRS.	BVCFD (IC - 0.1 ma) (Volts)			
	Init	168	340	580
100	61	61	61	61
102	61	61	61	61
104	63	63	63	63
106	68	68	68	68
108	73	74	74	74
110	80	81	82	82
112	86	86	86	86
114	89	89	89	89
116	89	89	89	89

MRS.	BVCFD (% Change from Initial)			
	Init	168	340	580
100	-	-3	-4	-5
102	-	-3	-4	-5
104	-	-1	-2	-3
106	-	0	0	0
108	-	0	0	0
110	-	0	+1	+1
112	-	+1	+3	+2
114	-	+1	+3	+2
116	-	+1	+3	+2

MRS.	VCE(SAT) (IC-20ma, Ib=5 ma) (mv.)			
	Init	168	340	580
102	0.88	0.87	0.88	0.88
104	0.88	0.87	0.88	0.88
106	0.89	0.89	0.89	0.89
108	0.96	0.92	0.94	0.95
110	1.23	1.02	1.05	1.02
112	1.26	1.09	1.08	1.07
114	1.37	1.21	1.19	1.19
116	1.34	1.33	1.33	1.33

MRS.	VCE(SAT) (% Change from Initial)			
	Init	168	340	580
102	-	-22	-20	-19
104	-	-23	-20	-19
106	-	-19	-18	-18
108	-	-15	-17	-15
110	-	-14	-14	-14
112	-	-13	-13	-13
114	-	-11	-11	-11
116	-	-10	-10	-10

MRS.	VBE(SAT) (IC-50 ma, Ib=5 ma) (mv.)			
	Init	168	340	580
102	793	591	780	780
104	793	591	780	780
106	794	707	787	787
108	795	783	784	784
110	800	786	787	787
112	803	793	790	790
114	816	802	800	800
116	823	807	806	806

MRS.	VBE(SAT) (% Change from Initial)			
	Init	168	340	580
102	-	-24	-3	-3
104	-	-24	-3	-3
106	-	-11	-8	-2
108	-	-2	-2	-2
110	-	-2	-2	-2
112	-	-1	-1	-1
114	-	-1	-1	-1
116	-	-1	-1	-1

MRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	580
102	72	26	26	26
104	72	26	26	26
106	79	83	82	84
108	91	90	93	91
110	93	94	96	95
112	96	97	99	96
114	98	98	101	100
116	101	103	102	101

MRS.	hFE (% Change from Initial)			
	Init	168	340	580
102	-	-3	-10	-2
104	-	-3	-10	-2
106	-	-2	-6	-1
108	-	0	-2	+1
110	-	+1	+3	+5
112	-	+4	+7	+7
114	-	+7	+8	+11
116	-	+8	+9	+12

MRS.	BVCFD (IC - 0.1 ma) (Volts)			
	Init	168	340	580
102	61	61	61	61
104	61	61	61	61
106	63	63	63	63
108	68	68	68	68
110	73	74	74	74
112	80	81	82	82
114	86	86	86	86
116	89	89	89	89

MRS.	BVCFD (% Change from Initial)			
	Init	168	340	580
102	-	-3	-4	-5
104	-	-3	-4	-5
106	-	-1	-2	-3
108	-	0	0	0
110	-	0	0	0
112	-	0	+1	+1
114	-	+1	+3	+2
116	-	+1	+3	+2

PROCESS: β PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C.

CELL NO.: 419236 NO. OF UNITS: 7

I _{CFO} (V _{CB} - 60V)(Nanamps)	I _{CFO} (V _{CB} - 60V)(Nanamps)			
	Init	168	340	680
Min	0.7	1.0	1.8	4.1
5%	0.7	1.0	1.8	4.1
10%	0.7	1.0	1.8	4.1
25%	0.9	1.4	2.7	4.4
50%	2.6	3.2	3.5	4.4
75%	3.9	3.7	3.9	4.4
90%	4.0	3.8	4.1	4.0
95%	4.0	3.8	4.1	4.0
Max	4.0	3.8	4.1	4.0

I _{EBO} (V _{EB} - 5V)(Nanamps)	I _{EBO} (V _{EB} - 5V)(Nanamps)			
	Init	168	340	680
Min	0.1	0.3	0.5	0.1
5%	0.1	0.3	0.5	0.1
10%	0.1	0.3	0.5	0.1
25%	0.1	0.5	0.8	0.1
50%	0.5	1.8	1.0	0.5
75%	2.0	2.2	2.5	2.1
90%	5.8	6.4	7.9	5.3
95%	5.8	6.4	7.9	5.3
Max	5.8	6.4	7.9	5.3

V _{CEFO} (I _C - 0.1 ma)(Volts)	V _{CEFO} (I _C - 0.1 ma)(Volts)			
	Init	168	340	680
Min	68	66	66	66
5%	68	66	66	66
10%	68	66	66	66
25%	70	69	69	69
50%	72	73	72	71
75%	77	76	72	71
90%	88	92	94	90
95%	88	92	94	90
Max	88	92	94	90

V _{CEFO} (% Change from Initial)	V _{CEFO} (% Change from Initial)			
	Init	168	340	680
Min	-	-3	-4	-4
5%	-	-3	-4	-4
10%	-	-3	-4	-4
25%	-	-2	-1	-2
50%	-	-1	0	-1
75%	-	0	+4	+8
90%	-	+4	22	23
95%	-	+4	22	23
Max	-	+4	22	23

V _{CE} (SAT)(I _C -50ma, I _B -5 ma)(Mv.)	V _{CE} (SAT)(I _C -50ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	120	103	103	105
5%	120	103	103	105
10%	120	105	103	105
25%	123	105	109	110
50%	124	109	112	115
75%	134	114	117	119
90%	135	118	120	120
95%	135	118	120	120
Max	135	118	120	120

V _{CE} (SAT)(% Change from Initial)	V _{CE} (SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	-21	-19	-19
5%	-	-21	-19	-19
10%	-	-21	-19	-19
25%	-	-15	-14	-13
50%	-	-12	-11	-11
75%	-	-11	-9	-10
90%	-	-11	29	28
95%	-	-11	29	28
Max	-	-11	29	28

V _{BE} (SAT)(I _C -50 ma, I _B -5 ma)(Mv.)	V _{BE} (SAT)(I _C -50 ma, I _B -5 ma)(Mv.)			
	Init	168	340	680
Min	797	754	756	798
5%	797	754	756	798
10%	797	754	756	798
25%	800	780	780	785
50%	802	791	796	796
75%	806	799	803	803
90%	821	814	800	800
95%	821	814	800	800
Max	821	814	800	800

V _{BE} (SAT)(% Change from Initial)	V _{BE} (SAT)(% Change from Initial)			
	Init	168	340	680
Min	-	-2	-2	-2
5%	-	-2	-2	-2
10%	-	-2	-2	-2
25%	-	-2	-1	-1
50%	-	-1	-1	-1
75%	-	-1	-1	-1
90%	-	-1	-1	-1
95%	-	-1	-1	-1
Max	-	-1	-1	-1

h _{FE} (I _C - 20 ma, V _{CE} - 5V)	h _{FE} (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	680
Min	69	71	20	20
5%	69	71	20	20
10%	69	71	20	20
25%	76	81	20	21
50%	85	87	20	21
75%	95	101	102	106
90%	100	104	106	107
95%	100	104	106	107
Max	100	104	106	107

h _{FE} (% Change from Initial)	h _{FE} (% Change from Initial)			
	Init	168	340	680
Min	-	-4	-4	-4
5%	-	-4	-4	-4
10%	-	-4	-4	-4
25%	-	+3	-2	-8
50%	-	+4	+3	+7
75%	-	+6	+7	+8
90%	-	+12	+17	+14
95%	-	+12	+17	+14
Max	-	+12	+17	+14

h _{FE} (I _C - 20 ma, V _{CE} - 5V)	h _{FE} (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	680
Min	69	71	20	20
5%	69	71	20	20
10%	69	71	20	20
25%	76	81	20	21
50%	85	87	20	21
75%	95	101	102	106
90%	100	104	106	107
95%	100	104	106	107
Max	100	104	106	107

h _{FE} (% Change from Initial)	h _{FE} (% Change from Initial)			
	Init	168	340	680
Min	-	-4	-4	-4
5%	-	-4	-4	-4
10%	-	-4	-4	-4
25%	-	+3	-2	-8
50%	-	+4	+3	+7
75%	-	+6	+7	+8
90%	-	+12	+17	+14
95%	-	+12	+17	+14
Max	-	+12	+17	+14

PROCESS: B PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 700 mw, 30 V; 25°C.

HRS.	ICEO (VCB - 60V) (Nanoamps)				
	Init	168	340	680	1000
Min	0.4	1.4	0.8	0.3	1.0
5%	0.4	1.4	0.8	0.3	1.0
10%	0.5	1.4	0.8	0.7	1.0
25%	1.4	2.1	1.6	1.4	1.3
50%	3.0	4.1	3.4	3.0	3.7
75%	3.8	4.5	3.7	3.8	3.6
90%	4.9	6.9	4.9	4.3	6.4
95%	5.4	9.1	5.1	4.8	6.8
Max	5.4	9.1	5.9	4.8	6.8

HRS.	IEBO (VEB - 5V) (Nanoamps)				
	Init	168	340	680	1000
Min	0.1	0.6	0.1	0.1	0.1
5%	0.1	0.6	0.1	0.1	0.1
10%	0.1	0.6	0.1	0.1	0.1
25%	0.1	0.7	0.3	0.1	0.2
50%	0.6	1.2	0.7	0.7	0.5
75%	2.0	2.8	2.2	1.9	1.5
90%	4.2	4.3	3.8	4.2	4.2
95%	5.0	4.9	4.1	4.4	5.0
Max	5.0	4.9	4.1	4.4	5.0

HRS.	BVCEO (IC - 0.1 ma) (Volts)				
	Init	168	340	680	1000
Min	64	63	63	62	62
5%	64	63	63	62	62
10%	66	65	65	64	64
25%	68	67	68	67	68
50%	73	73	73	73	72
75%	80	82	83	84	85
90%	86	90	88	90	91
95%	86	93	90	91	93
Max	86	93	90	91	93

HRS.	BVCEO (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-2	-2	-3	-3
5%	-	-2	-2	-3	-3
10%	-	-2	-5	-3	-3
25%	-	-1	-2	-1	-1
50%	-	0	0	-1	-1
75%	-	+1	+2	+1	+4
90%	-	+9	+9	+10	+12
95%	-	+9	+11	+13	+13
Max	-	+9	+11	+13	+13

HRS.	VCE(SAT) (IC-50ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000
Min	110	094	096	096	099
5%	110	094	096	096	099
10%	112	095	096	098	098
25%	118	097	099	100	100
50%	128	110	108	111	110
75%	131	116	115	116	115
90%	153	134	133	134	134
95%	168	148	148	147	149
Max	168	148	148	147	149

HRS.	VCE(SAT) (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-2	-2	-1	-2
5%	-	-2	-2	-1	-2
10%	-	-2	-2	-1	-2
25%	-	-1	-1	-1	-1
50%	-	+1	+1	+1	+1
75%	-	+1	+1	+1	+1
90%	-	+1	+1	+1	+1
95%	-	+1	+1	+1	+1
Max	-	+1	+1	+1	+1

HRS.	VBE(SAT) (IC-50 ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000
Min	788	725	725	727	727
5%	788	725	725	727	727
10%	788	725	725	727	727
25%	795	782	783	780	779
50%	805	789	786	790	784
75%	815	802	803	802	798
90%	826	812	812	813	813
95%	830	817	815	816	816
Max	830	817	815	816	816

HRS.	VBE(SAT) (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-2	-3	-3	-3
5%	-	-2	-3	-3	-3
10%	-	-2	-3	-3	-3
25%	-	-2	-2	-2	-2
50%	-	-1	-1	-1	-1
75%	-	-1	-1	-1	-1
90%	-	-1	-1	-1	-1
95%	-	-1	-1	-1	-1
Max	-	-1	-1	-1	-1

HRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	680	1000
Min	64	65	63	64	66
5%	64	65	63	64	66
10%	65	68	68	69	70
25%	77	72	76	76	77
50%	89	88	89	86	87
75%	94	101	102	103	103
90%	101	110	112	111	114
95%	105	111	114	115	115
Max	105	111	114	115	115

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-6	-15	-8	-8
5%	-	-6	-15	-8	-8
10%	-	-4	-11	-7	-6
25%	-	0	+0	-1	0
50%	-	+3	+4	+4	+3
75%	-	+8	+11	+8	+9
90%	-	+14	+17	+17	+16
95%	-	+14	+18	+19	+16
Max	-	+14	+18	+19	+16

HRS.	BVCE0 (IC - 0.1 ma) (Volts)				
	Init	168	340	680	1000
Min	64	63	63	62	62
5%	64	63	63	62	62
10%	66	65	65	64	64
25%	68	67	68	67	68
50%	73	73	73	73	72
75%	80	82	83	84	85
90%	86	90	88	90	91
95%	86	93	90	91	93
Max	86	93	90	91	93

HRS.	BVCE0 (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-2	-2	-3	-3
5%	-	-2	-2	-3	-3
10%	-	-2	-5	-3	-3
25%	-	-1	-2	-1	-1
50%	-	0	0	-1	-1
75%	-	+1	+2	+1	+4
90%	-	+9	+9	+10	+12
95%	-	+9	+11	+13	+13
Max	-	+9	+11	+13	+13

PROCESS: δ PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419230 NO. OF UNITS: 37

HRS.	ICEO (VCB - 60V) (nanamps)			
	Init	168	340	580
Min	0.2	0.4	1.3	0.2
5%	0.4	0.4	1.4	0.6
10%	0.7	0.5	1.6	0.8
25%	1.0	1.2	1.8	1.0
50%	1.5	1.8	2.3	1.6
75%	3.1	4.0	3.9	3.6
90%	4.4	6.1	6.5	5.0
95%	5.0	11.0	14.5	11.3
Max	5.6	∞	∞	∞

HRS.	IEBO (VEB - 5V) (nanamps)			
	Init	168	340	580
Min	0.1	0.3	0.2	0.1
5%	0.1	0.4	0.3	0.1
10%	0.1	0.5	0.3	0.2
25%	0.1	0.8	0.6	0.3
50%	0.4	1.0	0.8	0.6
75%	1.5	2.1	1.8	1.5
90%	3.5	4.2	3.5	3.2
95%	4.0	4.4	4.5	3.6
Max	4.1	4.7	4.5	4.2

HRS.	BVCEO (IC - 0.1 ma) (Volts)			
	Init	168	340	580
Min	61	58	57	57
5%	61	61	60	61
10%	64	62	62	62
25%	68	67	66	68
50%	72	72	71	72
75%	80	79	80	80
90%	85	85	85	86
95%	89	89	89	89
Max	90	90	90	91

HRS.	BVCEO (% Change from Initial)			
	Init	168	340	580
Min	-	-24	-23	-25
5%	-	-20	-19	-5
10%	-	-2	-1	-1
25%	-	0	0	0
50%	-	0	0	0
75%	-	0	0	0
90%	-	+2	+1	+1
95%	-	+15	+2	+2
Max	-	+29	+4	+3

HRS.	VCE(SAT) (IC-50 ma, IB-5 ma) (mv.)			
	Init	168	340	580
Min	0.99	0.83	0.73	0.79
5%	1.01	0.89	0.85	0.87
10%	1.21	0.94	0.93	0.92
25%	1.29	1.05	1.03	1.04
50%	1.36	1.11	1.13	1.13
75%	1.41	1.20	1.28	1.20
90%	1.49	1.42	1.46	1.31
95%	1.61	1.72	∞	1.40
Max	∞	∞	∞	∞

HRS.	VCE(SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-21	-26	-21
5%	-	-21	-19	-20
10%	-	-18	-18	-18
25%	-	-15	-15	-15
50%	-	-13	-13	-13
75%	-	-10	-12	-11
90%	-	-5	-10	-9
95%	-	+12	+20	-7
Max	-	+24	+24	-6

HRS.	VBE(SAT) (IC-50 ma, IB-5 ma) (mv.)			
	Init	168	340	580
Min	7.94	7.12	7.80	7.80
5%	7.95	7.17	7.84	7.79
10%	7.97	7.32	7.83	7.83
25%	8.03	7.84	7.88	7.85
50%	8.07	7.91	7.94	7.92
75%	8.11	7.96	7.97	7.96
90%	8.16	8.00	8.03	8.00
95%	8.22	8.04	8.04	8.06
Max	8.51	8.68	8.30	8.25

HRS.	VBE(SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-14	-2	-3
5%	-	-11	-2	-3
10%	-	-10	-2	-2
25%	-	-2	-2	-2
50%	-	-2	-2	-2
75%	-	-2	-1	-2
90%	-	-1	-1	-1
95%	-	0	+14	-1
Max	-	+1	+14	-1

HRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	580
Min	61	40	25	20
5%	64	56	56	57
10%	76	72	71	71
25%	83	84	81	82
50%	89	93	88	93
75%	100	102	99	102
90%	101	106	101	107
95%	103	110	109	110
Max	105	113	110	114

HRS.	hFE (% Change from Initial)			
	Init	168	340	580
Min	-	-7	-29	-25
5%	-	-6	-15	-12
10%	-	-4	-6	-3
25%	-	-1	-3	-1
50%	-	+2	-1	+3
75%	-	+4	0	+5
90%	-	+7	+4	+7
95%	-	+10	+6	+10
Max	-	+12	+8	+12

HRS.	hFE			
	Init	168	340	580
Min	61	40	25	20
5%	64	56	56	57
10%	76	72	71	71
25%	83	84	81	82
50%	89	93	88	93
75%	100	102	99	102
90%	101	106	101	107
95%	103	110	109	110
Max	105	113	110	114

PROCESS: B FAB-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419239 NO. OF UNITS: 7

		I _{FB} (V _{CB} - 60V) (Microamps)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	0.2	0.9	0.3	0.4	0.2	0.5
5%	0.2	0.9	0.3	0.4	0.2	0.5
10%	0.2	0.9	0.3	0.4	0.2	0.5
25%	0.6	1.3	0.7	0.7	0.6	0.6
50%	1.1	2.0	1.4	1.3	1.2	1.2
75%	3.7	4.2	3.6	3.4	3.1	3.0
90%	4.3	5.0	4.3	3.6	3.4	3.0
95%	4.3	5.0	4.3	3.6	3.4	3.0
Max	4.3	5.0	4.3	3.6	3.4	3.0

		I _{CEO} (V _{EB} - 5V) (Nanocamps)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	0.1	0.5	0.1	0.1	0.1	0.1
5%	0.1	0.5	0.1	0.1	0.1	0.1
10%	0.1	0.5	0.1	0.1	0.1	0.1
25%	0.1	0.7	0.1	0.1	0.1	0.1
50%	0.3	0.9	0.2	0.2	0.2	0.3
75%	1.5	2.6	2.3	1.7	1.5	1.9
90%	1.5	2.6	2.3	1.7	1.5	1.9
95%	1.5	2.6	2.3	1.7	1.5	1.9
Max	1.5	2.6	2.3	1.7	1.5	1.9

		BV _{CEO} (I _C - 0.1 ma.) (Volts)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	62	61	61	61	61	61
5%	62	61	61	61	61	61
10%	62	61	61	61	61	61
25%	63	63	63	72	73	72
50%	74	77	73	77	77	77
75%	81	80	80	86	85	85
90%	86	86	86	86	86	86
95%	86	86	86	86	86	86
Max	86	86	86	86	86	86

		BV _{CFO} (% Change from Initial)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	-	-1	-1	-1	-1	-1
5%	-	-1	-1	-1	-1	-1
10%	-	-1	-1	-1	-1	-1
25%	-	-1	-1	-1	-1	-1
50%	-	-1	0	+1	0	-1
75%	-	+8	+1	+1	+1	0
90%	-	+8	+1	+1	+1	+1
95%	-	+8	+1	+1	+1	+1
Max	-	+8	+1	+1	+1	+1

		V _{CE} (SAT) (I _C 50ma., I _B 5 ma.) (Mv.)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	111	093	093	094	093	090
5%	111	093	093	094	093	090
10%	111	093	093	094	093	090
25%	114	098	100	102	106	105
50%	118	102	102	111	112	113
75%	122	112	107	111	112	113
90%	131	149	145	140	145	146
95%	131	149	145	140	145	146
Max	131	149	145	140	145	146

		V _{CE} (SAT) (% Change from Initial)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	-	-16	-16	-17	-16	-16
5%	-	-16	-16	-17	-16	-16
10%	-	-16	-16	-17	-16	-16
25%	-	-15	-15	-16	-16	-15
50%	-	-15	-13	-15	-15	-14
75%	-	-12	-12	-12	-12	-11
90%	-	+64	-12	867	867	+1
95%	-	+64	-12	867	867	+1
Max	-	+64	-12	867	867	+1

		V _{BE} (SAT) (I _C 50 ma., I _B 5 ma.) (Mv.)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	800	779	785	784	786	786
5%	800	779	785	784	786	786
10%	800	779	785	784	786	786
25%	801	782	786	786	789	787
50%	802	791	794	795	797	798
75%	809	797	798	803	802	802
90%	813	115	799	800	800	800
95%	813	115	799	800	800	800
Max	813	115	799	800	800	800

		V _{BE} (SAT) (% Change from Initial)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	-	-3	-3	-2	-2	-2
5%	-	-3	-3	-2	-2	-2
10%	-	-3	-3	-2	-2	-2
25%	-	-2	-2	-2	-2	-2
50%	-	-2	-2	-1	-1	-2
75%	-	-1	-1	-1	-1	-2
90%	-	+44	-1	1148	1148	1148
95%	-	+44	-1	1148	1148	1148
Max	-	+44	-1	1148	1148	1148

		h _{FE} (I _C - 20 ma., V _{CE} - 5V)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	61	60	61	19	20	20
5%	61	60	61	19	20	20
10%	61	60	61	19	20	20
25%	92	90	89	59	60	61
50%	103	96	101	98	102	104
75%	105	100	104	102	104	104
90%	111	103	110	105	108	108
95%	111	103	110	105	108	108
Max	111	103	110	105	108	108

		h _{FE} (% Change from Initial)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	-	-8	-3	-8	-8	-8
5%	-	-8	-3	-8	-8	-8
10%	-	-8	-3	-8	-8	-8
25%	-	-7	-3	-7	-4	-3
50%	-	-3	-1	-4	-2	0
75%	-	-2	0	-1	+1	+2
90%	-	-2	+1	0	+3	+1
95%	-	-2	+1	0	+3	+1
Max	-	-2	+1	0	+3	+1

		BV _{CEO} (% Change from Initial)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	-	-	-	-	-	-
5%	-	-	-	-	-	-
10%	-	-	-	-	-	-
25%	-	-	-	-	-	-
50%	-	-	-	-	-	-
75%	-	-	-	-	-	-
90%	-	-	-	-	-	-
95%	-	-	-	-	-	-
Max	-	-	-	-	-	-

		BV _{CFO} (% Change from Initial)				
		Init	168	340	580	1000
SPS.	Init	168	340	580	1000	1500
Min	-	-	-	-	-	-
5%	-	-	-	-	-	-
10%	-	-	-	-	-	-
25%	-	-	-	-	-	-
50%	-	-	-	-	-	-
75%	-	-	-	-	-	-
90%	-	-	-	-	-	-
95%	-	-	-	-	-	-
Max	-	-	-	-	-	-

PROCESS: B PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 200 mw, 30 V, 150°C.

CELL NO.: 419240 NO. OF UNITS: 14.

SRS.	IC50 (VCE - 60V)(Microamps)				
	Init	168	340	580	1000L50020003000
Min	0.3	0.9	0.5	0.6	0.4
5%	0.3	0.9	0.5	0.6	0.4
10%	0.4	1.1	0.7	0.6	0.5
25%	1.0	1.4	1.2	1.1	1.0
50%	1.2	1.9	1.9	1.8	1.7
75%	2.4	3.4	3.4	3.3	3.2
90%	3.5	4.3	4.3	4.2	4.1
95%	3.8	4.5	4.5	4.4	4.3
Max	3.8	4.5	4.5	4.4	4.3

SRS.	IC50 (IC - 0.1 ma)(Volts)				
	Init	168	340	580	1000L50020003000
Min	50	50	50	50	50
5%	50	50	50	50	50
10%	56	55	56	55	55
25%	64	64	64	64	64
50%	73	73	73	73	73
75%	82	82	82	82	82
90%	86	89	90	90	90
95%	89	90	90	90	90
Max	89	90	90	90	90

SRS.	VCE(SAT)(% Change from Initial)				
	Init	168	340	580	1000L50020003000
Min	-1	-1	-1	-1	-1
5%	-1	-1	-1	-1	-1
10%	-1	-1	-1	-1	-1
25%	0	0	0	0	0
50%	0	0	0	0	0
75%	+1	+1	+1	+1	+1
90%	+4	+5	+5	+5	+5
95%	+7	+8	+8	+8	+8
Max	+7	+8	+8	+8	+8

SRS.	VCE(SAT)(IC-50ma, IB-5 ma)(mv.)				
	Init	168	340	580	1000L50020003000
Min	100	084	083	084	082
5%	100	084	083	084	082
10%	103	086	088	087	087
25%	115	099	100	101	098
50%	126	109	109	111	109
75%	130	117	118	118	120
90%	147	133	131	137	134
95%	153	143	139	148	142
Max	153	143	139	148	142

SRS.	VCE(SAT)(% Change from Initial)				
	Init	168	340	580	1000L50020003000
Min	-17	-17	-17	-16	-17
5%	-17	-17	-17	-16	-17
10%	-17	-17	-17	-16	-17
25%	-16	-15	-15	-14	-15
50%	-12	-11	-12	-13	-13
75%	-10	-9	-9	-11	-11
90%	-8	-9	-5	-9	-8
95%	-7	-8	-3	-8	-7
Max	-7	-8	-3	-8	-7

SRS.	VBE(SAT)(IC-50 ma, IB-5 ma)(mv.)				
	Init	168	340	580	1000L50020003000
Min	787	637	787	783	785
5%	787	637	787	783	785
10%	791	711	782	784	786
25%	800	785	785	784	787
50%	805	790	793	794	790
75%	810	796	797	798	799
90%	828	815	815	814	817
95%	829	818	815	818	817
Max	829	818	815	818	817

SRS.	VBE(SAT)(% Change from Initial)				
	Init	168	340	580	1000L50020003000
Min	-20	-20	-20	-20	-20
5%	-20	-20	-20	-20	-20
10%	-11	-11	-11	-11	-11
25%	-2	-2	-2	-2	-2
50%	-2	-2	-2	-2	-2
75%	-1	-1	-1	-1	-1
90%	-1	-1	-1	-1	-1
95%	0	0	0	0	0
Max	0	0	0	0	0

SRS.	hFE (IC - 20 ma, VCE - 5V)				
	Init	168	340	580	1000L50020003000
Min	57	56	55	55	54
5%	57	56	55	55	54
10%	60	58	59	58	58
25%	78	78	78	75	77
50%	92	90	90	88	90
75%	97	94	95	96	93
90%	106	104	105	104	105
95%	103	107	107	106	104
Max	106	107	107	106	104

SRS.	hFE (% Change from Initial)				
	Init	168	340	580	1000L50020003000
Min	-7	-8	-7	-8	-6
5%	-7	-8	-7	-8	-6
10%	-7	-8	-7	-8	-6
25%	-6	-4	-3	-6	-4
50%	-2	-3	-2	-4	-2
75%	-1	-1	-1	-1	-1
90%	+2	+1	+1	0	+1
95%	+2	+1	+1	0	+1
Max	+2	+1	+1	0	+1

SRS.	BVCF0 (% Change from Initial)				
	Init	168	340	580	1000L50020003000
Min	-1	-1	-1	-1	-1
5%	-1	-1	-1	-1	-1
10%	-1	-1	-1	-1	-1
25%	0	0	0	0	0
50%	0	0	0	0	0
75%	+1	+1	+1	+1	+1
90%	+4	+5	+5	+5	+5
95%	+7	+8	+8	+8	+8
Max	+7	+8	+8	+8	+8

PROCESS: C FAE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C.

CELL NO.: 419241 NO. OF UNITS: 6

HRS.	ICBO (VCB - 60V)(Nanoamps)				
	Init	168	340	680	1000
Min	0.2	1.1	0.6	0.4	0.8
5%	0.2	1.1	0.6	0.4	0.8
10%	0.2	1.1	0.6	0.4	0.8
25%	0.2	1.1	0.6	0.4	0.8
50%	50.4	50.0	41.6	33.1	33.1
75%	> 1µA	607.0	416.0	331.9	331.9
90%	> 1µA	718.9	808.0	622.8	622.8
95%	> 1µA	908.9	808.0	622.8	622.8
Max	> 1µA	908.9	808.0	622.8	622.8

HRS.	IPEO (VEB - 5V)(Nanoamps)				
	Init	168	340	680	1000
Min	0.7	1.0	0.6	0.3	0.1
5%	0.7	1.0	0.6	0.3	0.1
10%	0.7	1.0	0.6	0.3	0.1
25%	0.9	1.2	0.7	0.4	0.2
50%	2.8	51.4	9.5	48.6	52.5
75%	282.3	343.3	335.3	346.5	655.0
90%	> 1µA	∞	∞	∞	∞
95%	> 1µA	∞	∞	∞	∞
Max	> 1µA	∞	∞	∞	∞

HRS.	BVCEO (IC - 0.1 ma)(Volts)				
	Init	168	340	680	1000
Min	1	8.6	8.6	8.6	8.6
5%	1	8.6	8.6	8.6	8.6
10%	1	8.6	8.6	8.6	8.6
25%	58	9.9	10.2	10.3	10.2
50%	100	10.5	10.8	11.2	11.3
75%	108	11.3	11.2	11.8	11.9
90%	112	11.9	11.8	11.9	11.9
95%	112	11.9	11.8	11.9	11.9
Max	112	11.9	11.8	11.9	11.9

HRS.	BVCEO (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-1	-1	-1	-1
5%	-	-1	-1	-1	-1
10%	-	-1	-1	-1	-1
25%	-	+3	+4	+4	+4
50%	-	+9	+10	+11	+11
75%	-	18.4	19.7	20.0	21.4
90%	-	23.8	24.6	29.7	29.7
95%	-	23.8	24.6	29.7	29.7
Max	-	23.8	24.6	29.7	29.7

HRS.	VCE(SAT)(IC-50ma, IB-5 ma)(Mv.)				
	Init	168	340	680	1000
Min	791	776	700	777	776
5%	791	776	700	777	776
10%	791	776	700	777	776
25%	792	781	765	783	781
50%	794	789	795	798	785
75%	809	803	802	806	792
90%	815	804	808	810	799
95%	815	804	808	810	799
Max	815	804	808	810	799

HRS.	VCE(SAT)(% Change from Initial)				
	Init	168	340	680	1000
Min	-	-12	-8	-13	-13
5%	-	-12	-8	-13	-13
10%	-	-12	-8	-13	-13
25%	-	-12	-11	-11	-12
50%	-	-9	-9	-8	-6
75%	-	-3	+3	+10	-2
90%	-	+2	+7	+4	-1
95%	-	+2	+7	+4	-1
Max	-	+2	+7	+4	-1

HRS.	VBE(SAT)(IC-50 ma, IB-5 ma)(Mv.)				
	Init	168	340	680	1000
Min	791	776	700	777	776
5%	791	776	700	777	776
10%	791	776	700	777	776
25%	792	781	765	783	781
50%	794	789	795	798	785
75%	809	803	802	806	792
90%	815	804	808	810	799
95%	815	804	808	810	799
Max	815	804	808	810	799

HRS.	VBE(SAT)(% Change from Initial)				
	Init	168	340	680	1000
Min	-	-2	-2	-2	-2
5%	-	-2	-2	-2	-2
10%	-	-2	-2	-2	-2
25%	-	-2	-5	-2	-3
50%	-	-2	-1	-2	-2
75%	-	-1	+1	+2	-1
90%	-	+1	+2	+2	-1
95%	-	+1	+2	+2	-1
Max	-	+1	+2	+2	-1

HRS.	hFE (IC - 20 mA, VCE - 5V)				
	Init	168	340	680	1000
Min	51	46	46	46	20
5%	51	46	46	46	20
10%	51	46	46	46	20
25%	55	51	50	49	42
50%	69	68	63	67	68
75%	89	82	79	82	84
90%	129	115	107	114	117
95%	129	115	107	114	117
Max	129	115	107	114	117

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-10	-17	-12	-11
5%	-	-10	-17	-12	-11
10%	-	-10	-17	-12	-11
25%	-	-9	-12	-11	-10
50%	-	-7	-9	-8	-6
75%	-	-1	-8	-3	-1
90%	-	0	-6	-2	0
95%	-	0	-6	-2	0
Max	-	0	-6	-2	0

HRS.	BVCE0 (IC - 0.1 ma)(Volts)				
	Init	168	340	680	1000
Min	1	8.6	8.6	8.6	8.6
5%	1	8.6	8.6	8.6	8.6
10%	1	8.6	8.6	8.6	8.6
25%	58	9.9	10.2	10.3	10.2
50%	100	10.5	10.8	11.2	11.3
75%	108	11.3	11.2	11.8	11.9
90%	112	11.9	11.8	11.9	11.9
95%	112	11.9	11.8	11.9	11.9
Max	112	11.9	11.8	11.9	11.9

HRS.	BVCE0 (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-1	-1	-1	-1
5%	-	-1	-1	-1	-1
10%	-	-1	-1	-1	-1
25%	-	+3	+4	+4	+4
50%	-	+9	+10	+11	+11
75%	-	18.4	19.7	20.0	21.4
90%	-	23.8	24.6	29.7	29.7
95%	-	23.8	24.6	29.7	29.7
Max	-	23.8	24.6	29.7	29.7

PROCESS: C PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.
 OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419242 NO. OF UNITS: 16.

FRS.	IC50 (VCB - 60V) (Nanoamps)			IEBO (VEB - 5V) (Nanoamps)			BVCEO (IC - 0.1 ma) (Volts)			BVCF0 (% Change from Initial)						
	Init	168	340	680	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
Min	0.1	0.7	1.0	0.5	0.5	0.1	0.1	0.1	45	61	61	61	61	61	61	61
5%	0.1	0.7	1.0	0.5	0.5	0.1	0.1	0.1	45	61	61	61	61	61	61	61
10%	0.1	0.8	1.0	0.5	0.5	0.1	0.1	0.1	56	62	63	63	66	67	36	48
25%	0.2	0.8	1.3	0.6	0.7	0.3	0.3	0.3	63	74	74	74	74	74	71	74
50%	1.5	5.1	11.7	4.3	7.5	5.2	12.6	9.8	90	93	90	90	92	89	84	90
75%	533.1	949	575	779	1163	634	1359	139.0	118	123	124	124	125	125	117	125
90%	1.1A	0.0	0.0	0.0	0.0	0.0	0.0	0.0	140	163	163	164	155	163	199	168
95%	1.1A	0.0	0.0	0.0	0.0	0.0	0.0	0.0	151	200	199	199	199	199	198	199
Max	1.1A	0.0	0.0	0.0	0.0	0.0	0.0	0.0	151	200	199	199	199	198	198	199

FRS.	VCE (SAT) (IC-50ma, IB-5 ma) (Mv.)			VBE (SAT) (IC-50 ma, IB-5 ma) (Mv.)				
	Init	168	340	680	1000	1500	2000	3000
Min	103	826	890	890	890	890	890	890
5%	103	826	890	890	890	890	890	890
10%	110	873	892	894	893	892	892	892
25%	117	899	103	102	104	104	103	102
50%	126	117	118	120	119	120	119	117
75%	142	126	127	123	129	136	141	135
90%	165	167	153	145	142	147	177	196
95%	194	123	173	158	153	150	215	213
Max	194	173	173	158	153	150	215	203

FRS.	hFE (IC - 20 ma, VCE - 5V)			hFE (% Change from Initial)				
	Init	168	340	680	1000	1500	2000	3000
Min	49	48	47	49	48	49	48	50
5%	49	48	47	49	48	49	48	50
10%	50	51	49	51	50	51	50	50
25%	55	54	53	54	54	54	53	53
50%	69	69	68	69	69	69	67	68
75%	102	101	100	101	101	101	101	101
90%	124	123	121	123	122	124	124	123
95%	131	130	128	131	129	131	130	129
Max	131	130	128	131	129	131	130	129

FRS.	VCE (SAT) (% Change from Initial)			VBE (SAT) (% Change from Initial)				
	Init	168	340	680	1000	1500	2000	3000
Min	-	-82	-18	-19	-29	-29	-19	-18
5%	-	-82	-18	-19	-29	-29	-19	-18
10%	-	-37	-17	-18	-21	-20	-18	-17
25%	-	-14	-13	-15	-14	-14	-14	-12
50%	-	-11	-11	-10	-10	-10	-11	-11
75%	-	-7	-6	-6	-7	-5	-7	-3
90%	-	+7	+1	+2	+2	+5	+3	+18
95%	-	+36	+5	+3	+7	+13	+65	+48
Max	-	+36	+5	+3	+7	+13	+65	+48

FRS.	BVCEO (IC - 0.1 ma) (Volts)			BVCF0 (% Change from Initial)				
	Init	168	340	680	1000	1500	2000	3000
Min	45	61	61	61	61	61	61	61
5%	45	61	61	61	61	61	61	61
10%	56	62	63	63	66	67	36	48
25%	63	74	74	74	74	74	71	74
50%	90	93	90	90	92	89	84	90
75%	118	123	124	124	125	125	117	125
90%	140	163	163	164	155	163	199	168
95%	151	200	199	199	199	199	198	199
Max	151	200	199	199	199	198	198	199

FRS.	VBE (SAT) (IC-50 ma, IB-5 ma) (Mv.)			VBE (SAT) (% Change from Initial)				
	Init	168	340	680	1000	1500	2000	3000
Min	778	693	767	765	767	765	765	767
5%	778	693	767	765	767	765	765	767
10%	778	744	767	766	768	765	765	767
25%	786	769	775	774	775	776	772	774
50%	796	787	788	785	787	786	785	786
75%	802	794	797	797	792	795	795	801
90%	829	845	819	815	812	1119	823	831
95%	874	852	853	836	815	1799	837	881
Max	874	852	853	836	815	1799	837	881

FRS.	BVCEO (IC - 0.1 ma) (Volts)			BVCF0 (% Change from Initial)				
	Init	168	340	680	1000	1500	2000	3000
Min	45	61	61	61	61	61	61	61
5%	45	61	61	61	61	61	61	61
10%	56	62	63	63	66	67	36	48
25%	63	74	74	74	74	74	71	74
50%	90	93	90	90	92	89	84	90
75%	118	123	124	124	125	125	117	125
90%	140	163	163	164	155	163	199	168
95%	151	200	199	199	199	199	198	199
Max	151	200	199	199	199	198	198	199

FRS.	VBE (SAT) (IC-50 ma, IB-5 ma) (Mv.)			VBE (SAT) (% Change from Initial)				
	Init	168	340	680	1000	1500	2000	3000
Min	778	693	767	765	767	765	765	767
5%	778	693	767	765	767	765	765	767
10%	778	744	767	766	768	765	765	767
25%	786	769	775	774	775	776	772	774
50%	796	787	788	785	787	786	785	786
75%	802	794	797	797	792	795	795	801
90%	829	845	819	815	812	1119	823	831
95%	874	852	853	836	815	1799	837	881
Max	874	852	853	836	815	1799	837	881

PROCESS: C PRE-SCREEN STRESS: 168 Hrs. of 250°C/30V - 300°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 200 mw, 30 V, 150°C. CELL NO.: 419243 NO. OF UNITS: 6

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	0.3	0.2	0.1	0.5	104	0.3	0.2	0.4
5%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
10%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
25%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
50%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
75%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
90%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
95%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
Max	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5
5%	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5
10%	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5
25%	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5
50%	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5
75%	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5
90%	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5
95%	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5
Max	0.1	0.6	0.6	0.5	0.8	1.3	0.4	0.5

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	108	095	093	094	094	095	092	089
5%	108	095	093	094	094	095	092	089
10%	108	095	093	094	094	095	092	089
25%	108	095	093	094	094	095	092	089
50%	108	095	093	094	094	095	092	089
75%	108	095	093	094	094	095	092	089
90%	108	095	093	094	094	095	092	089
95%	108	095	093	094	094	095	092	089
Max	108	095	093	094	094	095	092	089

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	108	095	093	094	094	095	092	089
5%	108	095	093	094	094	095	092	089
10%	108	095	093	094	094	095	092	089
25%	108	095	093	094	094	095	092	089
50%	108	095	093	094	094	095	092	089
75%	108	095	093	094	094	095	092	089
90%	108	095	093	094	094	095	092	089
95%	108	095	093	094	094	095	092	089
Max	108	095	093	094	094	095	092	089

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	0.3	0.2	0.1	0.5	104	0.3	0.2	0.4
5%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
10%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
25%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
50%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
75%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
90%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
95%	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4
Max	0.3	0.2	0.1	0.5	106	0.3	0.2	0.4

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	786	771	773	775	775	772	769	768
5%	786	771	773	775	775	772	769	768
10%	786	771	773	775	775	772	769	768
25%	786	771	773	775	775	772	769	768
50%	786	771	773	775	775	772	769	768
75%	786	771	773	775	775	772	769	768
90%	786	771	773	775	775	772	769	768
95%	786	771	773	775	775	772	769	768
Max	786	771	773	775	775	772	769	768

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	108	095	093	094	094	095	092	089
5%	108	095	093	094	094	095	092	089
10%	108	095	093	094	094	095	092	089
25%	108	095	093	094	094	095	092	089
50%	108	095	093	094	094	095	092	089
75%	108	095	093	094	094	095	092	089
90%	108	095	093	094	094	095	092	089
95%	108	095	093	094	094	095	092	089
Max	108	095	093	094	094	095	092	089

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	786	771	773	775	775	772	769	768
5%	786	771	773	775	775	772	769	768
10%	786	771	773	775	775	772	769	768
25%	786	771	773	775	775	772	769	768
50%	786	771	773	775	775	772	769	768
75%	786	771	773	775	775	772	769	768
90%	786	771	773	775	775	772	769	768
95%	786	771	773	775	775	772	769	768
Max	786	771	773	775	775	772	769	768

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	43	37	32	31	31	29	28	
5%	43	37	32	31	31	29	28	
10%	43	37	32	31	31	29	28	
25%	43	37	32	31	31	29	28	
50%	43	37	32	31	31	29	28	
75%	43	37	32	31	31	29	28	
90%	43	37	32	31	31	29	28	
95%	43	37	32	31	31	29	28	
Max	43	37	32	31	31	29	28	

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	43	37	32	31	31	29	28	
5%	43	37	32	31	31	29	28	
10%	43	37	32	31	31	29	28	
25%	43	37	32	31	31	29	28	
50%	43	37	32	31	31	29	28	
75%	43	37	32	31	31	29	28	
90%	43	37	32	31	31	29	28	
95%	43	37	32	31	31	29	28	
Max	43	37	32	31	31	29	28	

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	43	37	32	31	31	29	28	
5%	43	37	32	31	31	29	28	
10%	43	37	32	31	31	29	28	
25%	43	37	32	31	31	29	28	
50%	43	37	32	31	31	29	28	
75%	43	37	32	31	31	29	28	
90%	43	37	32	31	31	29	28	
95%	43	37	32	31	31	29	28	
Max	43	37	32	31	31	29	28	

UNITS	Init	168	340	580	1000	1500	2000	3000
Min	43	37	32	31	31	29	28	
5%	43	37	32	31	31	29	28	
10%	43	37	32	31	31	29	28	
25%	43	37	32	31	31	29	28	
50%	43	37	32	31	31	29	28	
75%	43	37	32	31	31	29	28	
90%	43	37	32	31	31	29	28	
95%	43	37	32	31	31	29	28	
Max	43	37	32	31	31	29	28	

PROCESS: C FRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C. Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C.

CELL NO.: 419244 NO. OF UNITS: 14

MRS.	ICBO (VCB - 60V) (Nanamps)				IEBO (VEB - 5V) (Nanamps)				BV _{CEO} (Ic - 0.1 ma.) (Volts)				BV _{CFO} (% Change from Initial)			
	Init	168	340	580	1000L	500L	2000L	3000L	Init	168	340	580	1000L	500L	2000L	3000L
Min	<0.1	0.4	<0.1	<0.1	<0.1	<0.1	0.1	0.1	61	61	61	61	61	61	61	61
5%	<0.1	0.4	<0.1	<0.1	<0.1	<0.1	0.1	0.1	61	61	61	61	61	61	61	61
10%	<0.1	0.4	<0.1	<0.1	<0.1	<0.1	0.1	0.1	61	61	61	61	61	61	61	61
25%	0.2	0.6	0.3	0.2	0.3	0.1	0.5	0.2	64	64	64	65	66	65	64	64
50%	0.5	0.9	1.0	0.6	0.7	0.8	1.9	1.9	70	72	74	74	76	76	71	79
75%	0.8	2.1	1.8	1.9	1.4	30.1	146.6	105	95	95	96	96	96	93	99	108
90%	1.0	144.3	378.2	405.1	448.8	513.4	592.2	142	117	118	120	121	121	124	129	139
95%	1.1	224.8	724.3	802.2	872.0	900	963.0	152	152	152	150	149	146	141	151	164
Max	1.1	220.8	745.3	822.9	872.0	900	963.0	152	166	163	162	162	158	149	149	159

MRS.	VCE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)				VBE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	101	083	082	087	088	089	084	082
5%	101	083	082	087	088	089	084	082
10%	105	085	085	089	089	092	086	086
25%	113	096	098	087	099	100	096	089
50%	126	113	112	113	115	119	110	113
75%	140	126	129	130	131	129	127	132
90%	155	134	133	133	134	143	143	144
95%	160	134	135	134	135	150	150	148
Max	160	134	135	134	135	150	150	148

MRS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	54	55	55	55	55	54	53	53
5%	54	55	55	55	55	54	53	53
10%	60	61	61	60	61	60	54	54
25%	66	67	68	67	68	67	59	59
50%	81	80	80	80	81	82	77	77
75%	107	107	105	105	107	108	107	107
90%	112	112	114	112	113	114	113	112
95%	114	115	116	115	116	115	113	113
Max	114	115	116	115	116	115	113	113

MRS.	VCE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)				VBE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	776	766	763	767	765	765	767	768
5%	776	766	763	767	765	765	767	768
10%	781	770	766	770	766	766	767	770
25%	788	776	771	775	770	772	772	779
50%	793	780	779	780	779	780	780	786
75%	798	787	786	787	786	786	786	794
90%	813	794	792	794	791	802	801	807
95%	819	794	794	794	791	813	812	819
Max	819	794	794	794	791	813	812	819

MRS.	BV _{CEO} (Ic - 0.1 ma.) (Volts)				BV _{CFO} (% Change from Initial)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	63	61	61	61	61	61	61	61
5%	63	61	61	61	61	61	61	61
10%	66	64	64	64	65	66	65	64
25%	70	72	74	74	74	76	76	71
50%	95	95	96	96	96	93	99	108
75%	105	117	118	120	121	121	124	129
90%	142	152	150	149	149	146	141	151
95%	152	166	163	162	162	158	149	159
Max	152	166	163	162	162	158	149	159

MRS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	54	55	55	55	55	54	53	53
5%	54	55	55	55	55	54	53	53
10%	60	61	61	60	61	60	54	54
25%	66	67	68	67	68	67	59	59
50%	81	80	80	80	81	82	77	77
75%	107	107	105	105	107	108	107	107
90%	112	112	114	112	113	114	113	112
95%	114	115	116	115	116	115	113	113
Max	114	115	116	115	116	115	113	113

MRS.	VCE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)				VBE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	776	766	763	767	765	765	767	768
5%	776	766	763	767	765	765	767	768
10%	781	770	766	770	766	766	767	770
25%	788	776	771	775	770	772	772	779
50%	793	780	779	780	779	780	780	786
75%	798	787	786	787	786	786	786	794
90%	813	794	792	794	791	802	801	807
95%	819	794	794	794	791	813	812	819
Max	819	794	794	794	791	813	812	819

MRS.	BV _{CEO} (Ic - 0.1 ma.) (Volts)				BV _{CFO} (% Change from Initial)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	63	61	61	61	61	61	61	61
5%	63	61	61	61	61	61	61	61
10%	66	64	64	64	65	66	65	64
25%	70	72	74	74	74	76	76	71
50%	95	95	96	96	96	93	99	108
75%	105	117	118	120	121	121	124	129
90%	142	152	150	149	149	146	141	151
95%	152	166	163	162	162	158	149	159
Max	152	166	163	162	162	158	149	159

MRS.	VCE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)				VBE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	776	766	763	767	765	765	767	768
5%	776	766	763	767	765	765	767	768
10%	781	770	766	770	766	766	767	770
25%	788	776	771	775	770	772	772	779
50%	793	780	779	780	779	780	780	786
75%	798	787	786	787	786	786	786	794
90%	813	794	792	794	791	802	801	807
95%	819	794	794	794	791	813	812	819
Max	819	794	794	794	791	813	812	819

MRS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	54	55	55	55	55	54	53	53
5%	54	55	55	55	55	54	53	53
10%	60	61	61	60	61	60	54	54
25%	66	67	68	67	68	67	59	59
50%	81	80	80	80	81	82	77	77
75%	107	107	105	105	107	108	107	107
90%	112	112	114	112	113	114	113	112
95%	114	115	116	115	116	115	113	113
Max	114	115	116	115	116	115	113	113

MRS.	VCE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)				VBE (SAT) (IC-50 ma., IB-5 ma.) (Mv.)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	776	766	763	767	765	765	767	768
5%	776	766	763	767	765	765	767	768
10%	781	770	766	770	766	766	767	770
25%	788	776	771	775	770	772	772	779
50%	793	780	779	780	779	780	780	786
75%	798	787	786	787	786	786	786	794
90%	813	794	792	794	791	802	801	807
95%	819	794	794	794	791	813	812	819
Max	819	794	794	794	791	813	812	819

MRS.	BV _{CEO} (Ic - 0.1 ma.) (Volts)				BV _{CFO} (% Change from Initial)			
	Init	168	340	580	1000L	500L	2000L	3000L
Min	63	61	61	61	61	61	61	61
5%	63	61	61	61	61	61	61	61
10%	66	64	64	64	65	66	65	64
25%	70	72	74	74	74	76	76	71
50%	95	95	96	96	96	93	99	108
75%	105	117	118	120	121	121	124	129
90%	142	152	150	1				

PROCESS: C PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C. CELL NO.: 419245 NO. OF UNITS: 28

HRS.	ICEO (Vc = Gov) (Nanamps)				IEBO (VEB - 5V) (Nanamps)				BVCEO (IC - 0.1 ma) (Volts)				BVCF0 (% Change from Initial)							
	Init	168	340	500	Init	168	340	500	Init	168	340	580	1000	1500	2000	3000				
Min	0.1	0.4	0.1	0.1	0.1	0.1	0.1	0.1	56	57	57	56	0.9	0.1	-90	-4	-5	-5	-96	-99
5%	0.1	0.5	0.1	0.1	0.1	0.1	0.1	0.1	57	57	57	57	0.5	0.1	-5	-4	-5	-5	-93	-99
10%	0.1	0.6	0.2	0.1	0.1	0.1	0.1	0.1	58	57	58	58	0.1	0.1	-2	-3	-4	-1	-2	-34
25%	0.1	0.7	0.2	0.1	0.1	0.1	0.2	0.1	69	67	70	70	0.6	0.1	-1	-2	-2	-2	-3	-5
50%	0.1	0.9	0.5	0.3	0.4	0.4	0.4	0.6	80	79	80	79	0.8	0.1	-1	-1	-1	-1	-1	-2
75%	0.2	1.4	1.2	1.2	3.3	3.3	2.8	3.3	101	101	114	116	116	106	+2	+9	+6	+6	+7	+5
90%	0.6	3.6	3.1	4.3	5.8	5.8	5.8	5.8	148	148	149	147	147	147	+2	+23	+21	+20	+24	+25
95%	8.0	6.5	6.2	134	148	9	15.9	44.1	150	157	130	177	178	182	+28	+32	+25	+26	+31	+27
Max	14.0	7.0	0.38	245	180	0	54.5	134.2	160	159	0	193	195	206	+36	+57	+25	+26	+33	+28

HRS.	VCE (SAT) (IC-50 ma, IB-5 ma) (mv.)				VCE (SAT) (% Change from Initial)				VBE (SAT) (IC-50 ma, IB-5 ma) (mv.)				VBE (SAT) (% Change from Initial)							
	Init	168	340	500	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
Min	103	080	082	080	-23	-21	-21	-21	775	769	758	765	757	-3	-3	-3	-4	-3	-3	-3
5%	103	081	082	084	-21	-21	-21	-21	777	761	760	760	760	-3	-3	-3	-4	-3	-3	-3
10%	104	085	084	085	-20	-21	-20	-18	781	766	763	767	765	-3	-3	-3	-3	-3	-3	-3
25%	114	095	094	096	-18	-19	-17	-17	785	771	770	775	768	-2	-3	-2	-3	-3	-3	-3
50%	125	105	106	106	-15	-16	-15	-14	794	777	777	779	776	-2	-2	-2	-2	-2	-2	-2
75%	139	125	121	120	-11	-12	-12	-11	802	785	785	786	780	-1	-2	-1	-1	-1	-1	-1
90%	152	130	130	134	-9	-7	-8	-7	809	794	799	796	791	-1	-1	-1	-1	-1	-1	-1
95%	167	153	153	150	-6	-6	-6	-5	818	803	801	805	800	0	+59	0	0	0	0	0
Max	171	153	149	152	-6	-6	-5	-5	823	807	809	807	800	0	+98	0	0	0	0	0

HRS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)							
	Init	168	340	500	Init	168	340	580	1000	1500	2000	3000
Min	35	56	30	56	-9	-8	-7	-7	-31	-31	-38	-40
5%	36	57	36	57	-8	-8	-8	-8	-31	-31	-37	-36
10%	36	57	36	57	-2	-1	-4	-3	-19	-9	-2	-3
25%	68	68	63	67	0	-2	0	-4	-2	-2	-2	-2
50%	90	79	81	87	+1	-5	-1	+1	+1	+1	+1	+1
75%	110	110	109	109	+2	0	0	+3	+3	+3	+3	+3
90%	132	134	120	133	+2	+1	+2	+4	+4	+4	+6	+11
95%	136	137	134	134	+4	+4	+3	+5	+5	+5	+9	+18
Max	139	139	137	135	+4	+4	+3	+5	+5	+5	+9	+22

PROCESS: C PRE-SCREEN STRESS:

OPERATING POWER CONDITION:

168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.

500 mw, 30 V, 25°C.

CELL NO.: 419246 NO. OF UNITS: 79

MRS.	ICBO (V _{CB} - 60V)(Nanamps)				IEBO (V _{EB} - 5V)(Nanamps)				BVCF0 (IC - 0.1 ma)(Volts)				BVCF0 (% Change from Initial)											
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
5%	0.1	0.5	0.7	4.1	4.1	4.1	4.1	4.1	0.1	0.2	0.2	0.2	0.1	0.1	0.1	0.1	-	-13	-14	-14	-20	-23	-23	-23
10%	0.1	0.4	0.7	4.1	4.1	4.1	4.1	4.1	0.1	0.2	0.2	0.2	0.1	0.1	0.1	0.1	-	-2	-2	-2	-5	-9	-26	-11
25%	0.1	0.4	1.0	4.1	4.1	4.1	4.1	4.1	0.1	0.3	0.3	0.3	0.1	0.1	0.1	0.1	-	-1	-1	-1	-2	-2	-3	-2
50%	0.1	0.7	1.3	4.1	4.1	4.1	4.1	4.1	0.2	0.4	0.5	0.2	0.2	0.2	0.2	0.1	-	-1	-1	-1	-1	-1	-1	-1
75%	0.2	1.2	1.9	4.1	4.1	4.1	4.1	4.1	0.3	0.4	0.5	0.2	0.2	0.2	0.2	0.2	0	0	0	0	0	0	0	0
90%	0.6	4.0	5.4	5.9	13.0	6.7	14.6	19.1	2.3	2.9	2.4	2.6	2.7	2.3	2.3	2.9	+2	+3	+3	+7	+7	+11	+10	+18
95%	2.3	23.7	22.2	31.3	45.3	12.9	24.5	12.9	4.0	5.0	4.6	4.5	6.6	5.2	5.5	6.7	+11	+13	+11	+11	+11	+18	+19	+24
95%	7.6	59.1	17.1	19.1	19.1	0.0	0.0	0.0	7.5	7.4	7.5	7.5	9.9	7.4	7.4	7.5	+20	+16.3	+2.9	+2.1	+2.1	+2.1	+2.2	+2.3

MRS.	VCE(SAT)(IC-50ma, IB-5 ma)(Mv.)				VBE(SAT)(IC-50 ma, IB-5 ma)(Mv.)											
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
0%	0.0	0.1	0.1	0.1	0.1	0.1	0.1	0.1	7.58	6.22	6.22	6.22	6.22	6.22	6.22	6.22
10%	0.1	0.4	0.7	0.7	0.7	0.7	0.7	0.7	7.77	7.60	7.60	7.60	7.60	7.60	7.60	7.60
25%	0.1	0.4	1.0	0.7	0.7	0.7	0.7	0.7	7.83	7.64	7.65	7.66	7.63	7.63	7.60	7.65
50%	0.1	0.7	1.3	0.7	0.7	0.7	0.7	0.7	7.87	7.68	7.69	7.70	7.68	7.67	7.65	7.67
75%	0.2	1.2	1.9	1.1	1.4	0.7	1.6	1.7	7.94	7.75	7.75	7.77	7.74	7.75	7.70	7.73
90%	0.6	4.0	5.4	5.9	13.0	6.7	14.6	19.1	8.02	7.83	7.80	7.83	7.83	7.82	7.79	7.87
95%	2.3	23.7	22.2	31.3	45.3	12.9	24.5	12.9	8.11	7.91	7.94	7.96	7.90	7.92	7.90	7.91
95%	7.6	59.1	17.1	19.1	19.1	0.0	0.0	0.0	8.23	7.99	7.96	8.00	7.97	7.97	7.93	8.00

MRS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)											
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
0%	53	53	53	53	53	53	53	53	-	-10	-13	-11	-7	-14	-17	-29
10%	57	57	56	56	57	57	57	57	-	-7	-9	-9	-2	-1	-12	-8
25%	60	61	61	60	62	63	66	66	-	-4	-7	-8	-1	0	-7	-2
50%	74	72	71	73	75	76	70	70	-	0	-3	-2	0	+1	-5	-1
75%	84	84	82	84	85	87	80	80	-	+1	0	-1	0	+2	-4	0
90%	102	103	101	102	103	105	99	99	-	+2	+1	+1	+1	+3	-3	+1
95%	121	122	120	121	124	125	118	118	-	+2	+1	+1	+1	+3	-2	+3
95%	133	132	130	128	134	137	129	129	-	+3	+1	+1	+1	+3	+6	0
95%	159	154	159	154	151	153	154	154	-	+4	+4	+4	+9	+11	+7	+21

MRS.	VBE(SAT)(IC-50ma, IB-5 ma)(Mv.)				VCE(SAT)(IC-50ma, IB-5 ma)(Mv.)											
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
0%	0.0	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.0	0.1	0.1	0.1	0.1	0.1	0.1	0.1
10%	0.1	0.4	0.7	0.7	0.7	0.7	0.7	0.7	0.1	0.2	0.2	0.2	0.2	0.2	0.2	0.2
25%	0.1	0.4	1.0	0.7	0.7	0.7	0.7	0.7	0.1	0.3	0.3	0.3	0.3	0.3	0.3	0.3
50%	0.1	0.7	1.3	0.7	0.7	0.7	0.7	0.7	0.2	0.4	0.5	0.2	0.2	0.2	0.2	0.2
75%	0.2	1.2	1.9	1.1	1.4	0.7	1.6	1.7	0.3	0.4	0.5	0.2	0.2	0.2	0.2	0.2
90%	0.6	4.0	5.4	5.9	13.0	6.7	14.6	19.1	0.3	0.4	0.5	0.2	0.2	0.2	0.2	0.2
95%	2.3	23.7	22.2	31.3	45.3	12.9	24.5	12.9	0.4	0.5	0.6	0.3	0.3	0.3	0.3	0.3
95%	7.6	59.1	17.1	19.1	19.1	0.0	0.0	0.0	0.4	0.5	0.6	0.3	0.3	0.3	0.3	0.3

MRS.	VBE(SAT)(IC-50ma, IB-5 ma)(Mv.)				VBE(SAT)(% Change from Initial)											
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
0%	0.0	0.1	0.1	0.1	0.1	0.1	0.1	0.1	-	-2	-3	-3	-3	-3	-3	-3
10%	0.1	0.4	0.7	0.7	0.7	0.7	0.7	0.7	-	-4	-4	-3	-3	-3	-3	-3
25%	0.1	0.4	1.0	0.7	0.7	0.7	0.7	0.7	-	-3	-3	-3	-3	-3	-3	-3
50%	0.1	0.7	1.3	0.7	0.7	0.7	0.7	0.7	-	-3	-3	-3	-3	-3	-3	-3
75%	0.2	1.2	1.9	1.1	1.4	0.7	1.6	1.7	-	-2	-2	-2	-2	-2	-2	-2
90%	0.6	4.0	5.4	5.9	13.0	6.7	14.6	19.1	-	-2	-1	-2	-2	-2	-2	-2
95%	2.3	23.7	22.2	31.3	45.3	12.9	24.5	12.9	-	-1	-1	-1	-1	-1	-1	-1
95%	7.6	59.1	17.1	19.1	19.1	0.0	0.0	0.0	-	-1	-1	-1	-1	-1	-1	-1

MRS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)											
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
0%	53	53	53	53	53	53	53	53	-	-	-	-	-	-	-	-
10%	57	57	56	56	57	57	57	57	-	-	-	-	-	-	-	-
25%	60	61	61	60	62	63	66	66	-	-	-	-	-	-	-	-
50%	74	72	71	73	75	76	70	70	-	-	-	-	-	-	-	-
75%	84	84	82	84	85	87	80	80	-	-	-	-	-	-	-	-
90%	102	103	101	102	103	105	99	99	-	-	-	-	-	-	-	-
95%	121	122	120	121	124	125	118	118	-	-	-	-	-	-	-	-
95%	133	132	130	128	134	137	129	129	-	-	-	-	-	-	-	-
95%	159	154	159	154	151	153	154	154	-	-	-	-	-	-	-	-

MRS.	VBE(SAT)(IC-50ma, IB-5 ma)(Mv.)				VBE(SAT)(% Change from Initial)											
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
0%	0.0	0.1	0.1	0.1	0.1	0.1	0.1	0.1	-	-26	-21	-22	-20	-22	-21	-22
10%	0.1	0.4	0.7	0.7	0.7	0.7	0.7	0.7	-	-21	-22	-19	-19	-20	-20	-20
25%	0.1	0.4	1.0	0.7	0.7	0.7	0.7	0.7	-	-20	-20	-19	-19	-20	-20	-20
50%	0.1	0.7	1.3	0.7	0.7	0.7	0.7	0.7	-	-19	-18	-17	-17	-17	-18	-18
75%	0.2	1.2	1.9	1.1	1.4	0.7	1.6	1.7	-	-16	-16	-14	-14	-15	-16	-16
90%	0.6	4.0	5.4	5.9	13.0	6.7	14.6	19.1	-	-13	-13	-11	-12	-13	-13	-13
95%	2.3	23.7	22.2	31.3	45.3	12.9	24.5	12.9	-	-10	-10	-8	-10	-9	-9	-10
95%	7.6	59.1	17.1	19.1	19.1	0.0	0.0	0.0	-	-9	-7	-6	-6	-5	-8	-9

MRS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)											
	Init	168	340	580	1000	1500	2000	3000	Init	168	340	580	1000	1500	2000	3000
0%	53	53	53	53	54	55	55	55	-	-10	-13	-11	-7	-14	-17	-29
10%	57	57	56	56	57	57	57	57	-	-7	-9	-9	-2	-1	-12	-8
25%	60	61	61	60	62	63	66	66	-	-4	-7	-8	-1	0	-7	-2
50%	74	72	71	73	75	76	70	70	-	0	-3	-2	0	+1	-5	-1
75%	84	84	82	84	85	87	80	80	-	+1	0	-1	0	+2		

PROCESS: C PRE-SCREEN STRESS: 168 Hrs. of 200°C/30V - 200°C Stabilization Bake - 25 Kg Centrifuge.
 OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419247 NO. OF UNITS: 14.

SPS.	ICEO (VCB - 60V) (nanamps)				IEBO (VEB - 5V) (nanamps)				BVCEO (IC - 0.1 ma.) (Volts)				BVCF0 (% Change from Initial)											
	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000
5%	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	-97	-99	-99	-99	-99	-99	-99	-99
10%	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	-97	-99	-99	-99	-99	-99	-99	-99
25%	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	-50	-95	-98	-97	-99	-99	-99	-99
50%	0.4	1.3	2.4	4.6	22.9	3.9	1.3	0.4	0.4	0.7	1.3	0.6	0.7	0.3	0.4	0.4	-1	-3	-16	-2	-2	-2	-2	-2
75%	0.4	4.1	28.0	175.2	∞	∞	∞	482.2	1554	1.2	2.3	4.0	4.5	4.7	5.2	3.7	+7	+8	+14	+12	+36	+26	+5	+29
90%	0.8	236.2	∞	∞	∞	∞	∞	36.7	107	6.6	8.7	505.1	601.9	812.1	619.3	475	+90	+92	+95	+98	+99	+99	+99	+99
95%	0.9	412.0	∞	∞	∞	∞	∞	451.8	111	8.5	8.9	∞	∞	1130.6	859	+90	+92	+95	+98	+99	+99	+99	+99	+99
Max	0.9	412.0	∞	∞	∞	∞	∞	451.8	111	8.5	8.9	∞	∞	1130.6	859	+90	+92	+95	+98	+99	+99	+99	+99	+99

SPS.	VCE (SAT) (IC-50ma, Ib-5 ma.) (Mv.)				VCE (SAT) (% Change from Initial)				VBE (SAT) (IC-50 ma, Ib-5 ma.) (Mv.)				VBE (SAT) (% Change from Initial)											
	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000	Init	168	340	680	1000	1500	2000	3000
5%	101	084	088	090	088	019	027	088	-20	646	738	749	742	701	619	766	-20	-6	-5	-5	-5	-5	-5	-5
10%	101	084	088	090	088	019	027	088	-20	646	738	749	742	701	619	766	-20	-6	-5	-5	-5	-5	-5	-5
25%	103	085	088	091	088	053	044	089	-19	696	751	754	755	720	692	767	-12	-5	-5	-5	-5	-5	-5	-5
50%	107	093	096	097	097	091	102	099	-17	767	768	770	769	764	769	770	-3	-3	-3	-3	-3	-3	-3	-3
75%	125	105	115	115	114	107	123	125	-15	792	780	778	781	793	792	792	-2	-2	-2	-2	-2	-2	-2	-2
90%	137	121	134	127	128	121	∞	∞	-12	806	787	791	793	797	∞	∞	-2	-2	-2	-2	-2	-2	-2	-2
95%	150	128	417	418	416	416	∞	∞	-7	811	791	794	795	798	∞	∞	-1	0	+1	+1	+1	+1	+1	+1
Max	150	130	699	211	201	894	∞	∞	-5	813	792	795	797	798	∞	∞	0	+1	+1	+1	+1	+1	+1	+1

SPS.	hFE (IC - 20 ma, VCE - 5V)				hFE (% Change from Initial)			
	Init	168	340	680	1000	1500	2000	3000
5%	59	20	20	19	20	20	20	20
10%	59	20	20	19	20	20	20	20
25%	60	39	39	33	27	30	20	20
50%	63	60	60	56	54	60	20	20
75%	104	93	84	76	78	93	58	45
90%	118	115	112	101	105	114	126	84
95%	121	120	121	109	117	124	149	111
Max	122	121	122	111	119	124	156	116

PROCESS: C PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C.

CELL NO.: 419249 NO. OF UNITS: 10.

HRS.	ICBO (VCB - 60V)(Nanoamps)			
	Init	168	340	580
Min	0.1	0.1	0.1	0.1
5%	0.5	0.5	0.5	0.5
10%	0.5	0.5	0.5	0.5
25%	0.5	0.5	0.5	0.5
50%	0.6	0.6	0.6	0.6
75%	1.2	1.2	1.2	1.2
90%	5.8	5.8	5.8	5.8
95%	6.0	6.0	6.0	6.0
MAX	6.5	6.5	6.5	6.5

HRS.	IEBO (VEB - 5V)(Nanoamps)			
	Init	168	340	580
Min	0.1	0.1	0.1	0.1
5%	0.5	0.5	0.5	0.5
10%	0.5	0.5	0.5	0.5
25%	0.5	0.5	0.5	0.5
50%	0.6	0.6	0.6	0.6
75%	1.2	1.2	1.2	1.2
90%	11.1	11.1	11.1	11.1
95%	12.0	12.0	12.0	12.0
MAX	12.0	12.0	12.0	12.0

HRS.	BVCEO (IC - 0.1 ma)(Volts)			
	Init	168	340	580
Min	72	71	71	71
5%	72	71	71	71
10%	72	73	73	73
25%	84	93	93	93
50%	101	103	104	104
75%	129	139	138	138
90%	148	145	148	148
95%	148	145	148	148
MAX	148	145	148	148

HRS.	BVCEO (% Change from Initial)			
	Init	168	340	580
Min	-	-14	-5	-2
5%	-	-14	-5	-2
10%	-	-13	-5	-2
25%	-	-1	-2	-1
50%	-	0	-1	-1
75%	-	+1	+4	+5
90%	-	+33	+37	+38
95%	-	+37	+40	+41
MAX	-	+37	+40	+41

HRS.	VCE(SAT)(IC-50ma, IB-5 ma)(Mv.)			
	Init	168	340	580
Min	101	101	101	101
5%	101	101	101	101
10%	101	101	101	101
25%	103	103	103	103
50%	127	113	115	117
75%	135	118	122	124
90%	146	127	133	139
95%	146	127	133	139
MAX	146	127	133	139

HRS.	VCE(SAT)(% Change from Initial)			
	Init	168	340	580
Min	-	-86	-19	-18
5%	-	-86	-19	-18
10%	-	-79	-19	-18
25%	-	-16	-14	-15
50%	-	-13	-11	-11
75%	-	-9	-6	-6
90%	-	-9	-6	-6
95%	-	-9	-6	-6
MAX	-	-9	-6	-6

HRS.	VBE(SAT)(IC-50 ma, IB-5 ma)(Mv.)			
	Init	168	340	580
Min	770	694	723	765
5%	779	684	722	765
10%	780	702	722	766
25%	788	773	727	776
50%	800	783	785	780
75%	802	789	789	790
90%	807	791	792	790
95%	807	791	792	790
MAX	807	791	792	790

HRS.	VBE(SAT)(% Change from Initial)			
	Init	168	340	580
Min	-	-11	-3	-3
5%	-	-11	-3	-3
10%	-	-10	-3	-3
25%	-	-2	-2	-2
50%	-	-2	-2	-2
75%	-	-2	-1	-2
90%	-	-2	0	0
95%	-	-2	0	0
MAX	-	-2	0	0

HRS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	580
Min	49	50	49	50
5%	49	50	49	50
10%	50	50	50	50
25%	61	59	62	63
50%	77	78	73	79
75%	88	88	82	88
90%	106	109	101	110
95%	106	110	101	110
MAX	106	110	101	110

HRS.	hFE (% Change from Initial)			
	Init	168	340	580
Min	-	-4	-10	-1
5%	-	-4	-10	-1
10%	-	-4	-10	-1
25%	-	+1	-7	0
50%	-	+3	-2	+3
75%	-	+6	+1	+8
90%	-	+6	+1	+8
95%	-	+6	+1	+8
MAX	-	+6	+1	+8

HRS.	BVCEO (IC - 0.1 ma)(Volts)			
	Init	168	340	580
Min	72	71	71	71
5%	72	71	71	71
10%	72	73	73	73
25%	84	93	93	93
50%	101	103	104	104
75%	129	139	138	138
90%	148	145	148	148
95%	148	145	148	148
MAX	148	145	148	148

HRS.	BVCEO (% Change from Initial)			
	Init	168	340	580
Min	-	-14	-5	-2
5%	-	-14	-5	-2
10%	-	-13	-5	-2
25%	-	-1	-2	-1
50%	-	0	-1	-1
75%	-	+1	+4	+5
90%	-	+33	+37	+38
95%	-	+37	+40	+41
MAX	-	+37	+40	+41

PROCESS: C PAB-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 700 mw, 30 V, 25°C.

CELL NO.: 419250 NO. OF UNITS: 20

IERS.	ICBO (VCB - 60V) (Nanocamps)			
	Init	168	340	580
Min	0.1	0.6	4.1	4.1
5%	0.1	0.6	4.1	4.1
10%	0.1	0.6	4.1	4.1
25%	0.1	0.7	0.1	0.1
50%	0.1	0.8	0.2	0.3
75%	0.1	1.2	0.5	2.3
90%	0.2	2.3	2.2	7.0
95%	1.2	20.6	6.9	10.3
Max	1.3	32.1	7.1	10.5

IERS.	IEBO (VEB - 5V) (Nanocamps)			
	Init	168	340	580
Min	0.1	0.4	4.1	4.1
5%	0.1	0.4	4.1	4.1
10%	0.1	0.4	4.1	4.1
25%	0.1	0.7	0.2	0.3
50%	0.1	1.4	0.5	0.7
75%	3.3	4.2	3.0	3.4
90%	6.2	7.0	5.1	5.3
95%	6.4	7.5	6.3	6.4
Max	6.4	7.5	6.4	6.5

IERS.	BVCEO (IC - 0.1 ma) (Volts)			
	Init	168	340	580
Min	62	61	61	61
5%	62	61	61	61
10%	63	64	63	63
25%	73	73	73	73
50%	88	87	86	86
75%	105	109	109	111
90%	137	134	135	135
95%	148	160	159	158
Max	148	161	160	159

IERS.	BVCF0 (% Change from Initial)			
	Init	168	340	580
Min	-	-17	-30	-34
5%	-	-16	-29	-32
10%	-	-2	-3	-3
25%	-	-2	-2	-3
50%	-	-1	-1	-1
75%	-	+3	+4	+4
90%	-	+9	+9	+9
95%	-	+23	+26	+25
Max	-	+24	+27	+26

IERS.	VCE (SAT) (IC-50ma, IB-5 ma) (Mv.)			
	Init	168	340	580
Min	102	089	085	087
5%	102	089	085	087
10%	105	089	088	092
25%	115	097	098	101
50%	129	113	113	114
75%	140	124	123	127
90%	150	132	131	134
95%	154	135	136	136
Max	154	135	136	136

IERS.	VCE (SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-19	-19	-17
5%	-	-19	-19	-17
10%	-	-17	-17	-16
25%	-	-15	-15	-13
50%	-	-13	-13	-12
75%	-	-11	-12	-9
90%	-	-9	-8	-8
95%	-	-9	-8	-7
Max	-	-9	-8	-7

IERS.	VBE (SAT) (IC-50 ma, IB-5 ma) (Mv.)			
	Init	168	340	580
Min	777	761	763	760
5%	777	761	763	760
10%	783	761	763	763
25%	788	768	769	771
50%	799	781	779	780
75%	807	789	785	787
90%	814	792	794	796
95%	816	792	796	799
Max	816	792	796	799

IERS.	VBE (SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-4	-3	-3
5%	-	-4	-3	-3
10%	-	-3	-3	-3
25%	-	-3	-3	-3
50%	-	-3	-2	-2
75%	-	-2	-2	-2
90%	-	-1	-1	-1
95%	-	-1	-1	-1
Max	-	-1	-1	-1

IERS.	hFE (IC - 20 ma, VCE - 5V)			
	Init	168	340	580
Min	48	49	48	48
5%	48	49	48	48
10%	50	51	50	50
25%	58	59	58	57
50%	96	94	97	98
75%	106	109	109	110
90%	122	113	116	122
95%	125	124	125	128
Max	125	124	125	128

IERS.	hFE (% Change from Initial)			
	Init	168	340	580
Min	-	-19	-11	-1
5%	-	-18	-11	-1
10%	-	-8	-4	-1
25%	-	-7	+1	+1
50%	-	+2	+3	+2
75%	-	+2	+3	+2
90%	-	+4	+7	+5
95%	-	+4	+7	+5
Max	-	+4	+7	+5

IERS.	BVCE0 (IC - 20 ma, VCE - 5V)			
	Init	168	340	580
Min	48	49	48	48
5%	48	49	48	48
10%	50	51	50	50
25%	58	59	58	57
50%	96	94	97	98
75%	106	109	109	110
90%	122	113	116	122
95%	125	124	125	128
Max	125	124	125	128

IERS.	BVCE0 (% Change from Initial)			
	Init	168	340	580
Min	-	-17	-30	-34
5%	-	-16	-29	-32
10%	-	-2	-3	-3
25%	-	-2	-2	-3
50%	-	-1	-1	-1
75%	-	+3	+4	+4
90%	-	+9	+9	+9
95%	-	+23	+26	+25
Max	-	+24	+27	+26

PROCESS: C PRE-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419251 NO. OF UNITS: 52.

FRS.	V _{CE} (V _{CB} - 60V) (Nanoamps)			
	Init	168	340	580
Min	0.1	0.2	0.8	0.1
5%	0.1	0.3	0.7	0.1
10%	0.1	0.4	0.9	0.2
25%	0.1	0.5	1.0	0.3
50%	0.1	0.7	1.3	0.5
75%	0.3	1.2	2.2	1.0
90%	1.8	3.4	5.1	3.2
95%	3.4	5.7	7.8	4.5
Max	6.3	6.9	13.5	11.5

FRS.	V _{EB} (V _{EB} - 5V) (Nanoamps)			
	Init	168	340	580
Min	0.1	0.1	0.2	0.1
5%	0.1	0.2	0.2	0.1
10%	0.1	0.2	0.2	0.1
25%	0.1	0.2	0.2	0.1
50%	0.1	0.2	0.2	0.1
75%	0.1	0.2	0.2	0.1
90%	0.1	0.2	0.2	0.1
95%	0.1	0.2	0.2	0.1
Max	0.1	0.2	0.2	0.1

FRS.	V _{CE} (I _C - 0.1 ma) (Volts)			
	Init	168	340	580
Min	55	53	53	53
5%	58	57	57	57
10%	60	59	59	59
25%	68	68	68	68
50%	83	83	83	83
75%	108	108	108	108
90%	129	140	140	141
95%	151	152	151	153
Max	167	173	171	170

FRS.	V _{CE} (% Change from Initial)			
	Init	168	340	580
Min	-	-4	-4	-6
5%	-	-3	-3	-5
10%	-	-2	-3	-4
25%	-	-1	-2	-2
50%	-	-1	-1	-1
75%	-	0	0	0
90%	-	+5	+7	+10
95%	-	+13	+11	+10
Max	-	+32	+32	+37

FRS.	V _{BE} (I _C - 50ma, I _B - 5 ma) (Mv.)			
	Init	168	340	580
Min	92	85	80	80
5%	102	88	85	82
10%	105	87	84	81
25%	114	94	95	96
50%	123	104	105	107
75%	135	116	115	117
90%	146	124	127	128
95%	170	137	138	137
Max	265	170	167	167

FRS.	V _{BE} (% Change from Initial)			
	Init	168	340	580
Min	-	-8	-11	-11
5%	-	-6	-10	-10
10%	-	-5	-10	-10
25%	-	-4	-10	-10
50%	-	-3	-10	-10
75%	-	-2	-10	-10
90%	-	-1	-10	-10
95%	-	-1	-10	-10
Max	-	-6	-8	-7

FRS.	V _{BE} (I _C - 50 ma, I _B - 5 ma) (Mv.)			
	Init	168	340	580
Min	774	678	663	668
5%	779	735	723	759
10%	782	759	744	763
25%	792	768	771	769
50%	797	777	777	778
75%	804	783	784	783
90%	815	791	793	793
95%	835	796	798	797
Max	908	840	843	843

FRS.	V _{BE} (% Change from Initial)			
	Init	168	340	580
Min	-	-23	-15	-14
5%	-	-13	-3	-7
10%	-	-4	-3	-3
25%	-	-3	-3	-3
50%	-	-3	-3	-3
75%	-	-3	-3	-3
90%	-	-2	-2	-2
95%	-	-2	-2	-2
Max	-	-2	-1	-1

FRS.	h _{FE} (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	580
Min	48	49	49	50
5%	54	54	52	53
10%	59	58	55	59
25%	70	69	68	71
50%	86	85	82	86
75%	108	106	108	109
90%	124	123	122	126
95%	134	131	126	133
Max	140	141	138	137

FRS.	h _{FE} (% Change from Initial)			
	Init	168	340	580
Min	-	-16	-12	-13
5%	-	-7	-10	-9
10%	-	-4	-9	-7
25%	-	-1	-5	-4
50%	-	+1	-1	-2
75%	-	+1	0	+1
90%	-	+3	+2	+3
95%	-	+6	+4	+6
Max	-	+13	+5	+5

FRS.	h _{FE} (% Change from Initial)			
	Init	168	340	580
Min	-	-	-	-
5%	-	-	-	-
10%	-	-	-	-
25%	-	-	-	-
50%	-	-	-	-
75%	-	-	-	-
90%	-	-	-	-
95%	-	-	-	-
Max	-	-	-	-

PROCESS: C PRE-SCREEN SIRESS: 25 Kg Centrifuge Only.

OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419252 NO. OF UNITS: 10

EIRS.	VCE (VCE ~ 60V) (Nanoamps)			
	Init	168	340	580
Min	0.1	0.7	0.2	0.1
5%	0.1	0.7	0.2	0.1
10%	0.1	0.7	0.2	0.1
25%	0.1	0.8	0.3	0.2
50%	0.1	1.1	0.8	0.7
75%	0.1	4.28	9.21	12.1
90%	0.6	24.2	96.7	117.2
95%	0.7	8.136	0	0
Max	0.7	8.136	0	0

EIRS.	I _{EBO} (V _{EB} ~ 5V) (Nanoamps)			
	Init	168	340	580
Min	0.1	0.3	0.1	0.1
5%	0.1	0.3	0.1	0.1
10%	0.1	0.3	0.1	0.1
25%	0.2	0.7	0.2	0.2
50%	1.1	1.6	2.4	2.4
75%	4.9	4.6	6.1	5.8
90%	7.9	6.6	15.1	4.24
95%	8.2	6.6	16.1	46.2
Max	8.2	6.6	16.1	46.2

EIRS.	BV _{CBO} (I _C ~ 0.1 ma) (Volts)			
	Init	168	340	580
Min	52	51	51	11
5%	52	51	51	11
10%	53	52	52	15
25%	61	57	59	56
50%	74	74	67	67
75%	84	82	91	92
90%	149	141	145	145
95%	155	147	151	151
Max	155	147	151	151

EIRS.	BV _{CFO} (% Change from Initial)			
	Init	168	340	580
Min	-	-10	-27	-87
5%	-	-10	-27	-87
10%	-	-10	-25	-79
25%	-	-6	-4	-4
50%	-	-2	-2	-2
75%	-	0	0	0
90%	-	+6	+36	+31
95%	-	+6	+29	+39
Max	-	+6	+29	+39

EIRS.	VCE (SAT) (I _C ~ 50ma, I _B ~ 5 ma) (mv.)			
	Init	168	340	580
Min	102	086	089	088
5%	102	086	089	088
10%	102	086	089	088
25%	106	093	092	093
50%	107	099	097	100
75%	155	136	139	139
90%	173	165	162	154
95%	174	167	163	160
Max	174	167	163	160

EIRS.	VCE (SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-18	-15	-18
5%	-	-18	-15	-18
10%	-	-18	-15	-18
25%	-	-14	-13	-11
50%	-	-10	-12	-10
75%	-	-7	-8	-8
90%	-	-3	-6	-2
95%	-	-3	-6	-1
Max	-	-3	-6	-1

EIRS.	VBE (SAT) (I _C ~ 50 ma, I _B ~ 5 ma) (mv.)			
	Init	168	340	580
Min	773	758	760	763
5%	773	758	760	763
10%	774	759	761	764
25%	781	770	770	779
50%	813	796	798	800
75%	851	843	840	837
90%	854	846	843	838
95%	854	846	843	838
Max	854	846	843	838

EIRS.	VBE (SAT) (% Change from Initial)			
	Init	168	340	580
Min	-	-3	-2	-2
5%	-	-3	-2	-2
10%	-	-3	-2	-2
25%	-	-2	-2	-2
50%	-	-1	-1	-1
75%	-	0	0	0
90%	-	0	0	0
95%	-	0	0	0
Max	-	0	0	0

EIRS.	h _{FE} (I _C ~ 20 ma, VCE ~ 5V)			
	Init	168	340	580
Min	54	54	54	52
5%	54	54	54	52
10%	55	55	55	54
25%	71	71	71	63
50%	96	98	95	83
75%	101	104	102	90
90%	114	114	114	111
95%	115	116	116	112
Max	115	115	116	112

EIRS.	h _{FE} (% Change from Initial)			
	Init	168	340	580
Min	-	-1	-1	-1
5%	-	-1	-1	-1
10%	-	-1	-1	-1
25%	-	+1	0	-13
50%	-	+1	+1	-10
75%	-	+3	+3	-8
90%	-	+4	+4	-4
95%	-	+4	+4	-4
Max	-	+4	+4	-4

EIRS.	h _{FE} (I _C ~ 20 ma, VCE ~ 5V)			
	Init	168	340	580
Min	54	54	54	52
5%	54	54	54	52
10%	55	55	55	54
25%	71	71	71	63
50%	96	98	95	83
75%	101	104	102	90
90%	114	114	114	111
95%	115	116	116	112
Max	115	115	116	112

PROCESS: C FRP-SCREEN STRESS: 25 Kg Centrifuge Only.

OPERATING POWER COMPONENT:

200 mw, 30 V, 150°C.

CELL NO.: 419253 NO. OF UNITS: 20

ERS.	VCE (VCE = 60V) (Microamps)			
	168	340	580	1000/1500/2000/3000
MIN	0.1	0.1	0.1	0.1
5%	0.1	0.1	0.1	0.1
10%	0.1	0.1	0.1	0.1
25%	0.1	0.1	0.1	0.1
50%	0.1	0.1	0.1	0.1
75%	0.1	0.1	0.1	0.1
90%	0.1	0.1	0.1	0.1
95%	0.1	0.1	0.1	0.1
MAX	0.1	0.1	0.1	0.1

ERS.	I _{CEO} (V _{CB} = 5V) (Microamps)			
	168	340	580	1000/1500/2000/3000
MIN	0.1	0.1	0.1	0.1
5%	0.1	0.1	0.1	0.1
10%	0.1	0.1	0.1	0.1
25%	0.1	0.1	0.1	0.1
50%	0.1	0.1	0.1	0.1
75%	0.1	0.1	0.1	0.1
90%	0.1	0.1	0.1	0.1
95%	0.1	0.1	0.1	0.1
MAX	0.1	0.1	0.1	0.1

ERS.	BV _{CEO} (I _C = 0.1 ma) (Volts)			
	168	340	580	1000/1500/2000/3000
MIN	59	61	61	58
5%	59	61	61	58
10%	63	67	67	62
25%	70	74	74	67
50%	75	84	83	75
75%	85	84	83	87
90%	114	118	113	119
95%	139	115	119	124
MAX	139	115	119	124

ERS.	BV _{CEO} (% Change from Initial)			
	168	340	580	1000/1500/2000/3000
MIN	-99	-99	-99	-10
5%	-94	-94	-96	-11
10%	-7	-7	-38	-9
25%	-4	-5	-7	-5
50%	-1	-2	-2	-2
75%	0	0	0	0
90%	+23	+23	+60	+59
95%	+42	+28	+64	+66
MAX	+44	+60	+64	+66

ERS.	VCE (SAT) (I _C = 50 ma, I _B = 5 ma) (Mv.)			
	168	340	580	1000/1500/2000/3000
MIN	0.06	0.75	0.74	0.73
5%	0.13	0.75	0.71	0.73
10%	0.84	0.84	0.84	0.84
25%	0.87	0.84	0.84	0.84
50%	0.88	0.84	0.84	0.84
75%	1.19	1.22	1.26	1.20
90%	1.31	1.32	1.33	1.29
95%	1.59	1.34	1.35	1.31
MAX	1.59	1.34	1.35	1.31

ERS.	VCE (SAT) (% Change from Initial)			
	168	340	580	1000/1500/2000/3000
MIN	-30	-26	-23	-31
5%	-30	-26	-23	-31
10%	-21	-22	-20	-25
25%	-18	-18	-16	-19
50%	-16	-14	-13	-14
75%	-11	-11	-9	-11
90%	-9	-9	-6	-10
95%	+24	+23	+26	+22
MAX	+28	+25	+25	+25

ERS.	VBE (SAT) (I _C = 50 ma, I _B = 5 ma) (Mv.)			
	168	340	580	1000/1500/2000/3000
MIN	705	782	759	760
5%	709	782	759	760
10%	782	782	762	762
25%	784	766	764	764
50%	799	774	775	777
75%	810	788	786	790
90%	814	792	785	799
95%	818	801	795	800
MAX	818	801	795	800

ERS.	VBE (SAT) (% Change from Initial)			
	168	340	580	1000/1500/2000/3000
MIN	-5	-5	-4	-4
5%	-5	-5	-4	-4
10%	-3	-4	-4	-3
25%	-3	-3	-3	-3
50%	-2	-2	-2	-2
75%	-1	-2	-2	-2
90%	+8	+8	+8	+9
95%	+8	+8	+8	+9
MAX	+8	+8	+8	+9

ERS.	h _{FE} (I _C = 20 ma, VCE = 5V)			
	168	340	580	1000/1500/2000/3000
MIN	51	51	20	20
5%	51	51	21	21
10%	53	53	51	51
25%	60	63	59	58
50%	102	103	104	100
75%	116	117	118	118
90%	124	124	127	126
95%	125	126	127	128
MAX	125	126	127	128

ERS.	h _{FE} (% Change from Initial)			
	168	340	580	1000/1500/2000/3000
MIN	-7	-7	-8	-8
5%	-7	-7	-8	-8
10%	-2	-5	-9	-9
25%	-5	-1	-4	-3
50%	0	+1	+3	+1
75%	+1	+2	+3	+2
90%	+2	+3	+4	+4
95%	+6	+9	+12	+12
MAX	+6	+9	+12	+12

ERS.	BV _{CEO} (% Change from Initial)			
	168	340	580	1000/1500/2000/3000
MIN	-99	-99	-99	-10
5%	-94	-94	-96	-11
10%	-7	-7	-38	-9
25%	-4	-5	-7	-5
50%	-1	-2	-2	-2
75%	0	0	0	0
90%	+23	+23	+60	+59
95%	+42	+28	+64	+66
MAX	+44	+60	+64	+66

ERS.	VBE (SAT) (% Change from Initial)			
	168	340	580	1000/1500/2000/3000
MIN	-5	-5	-4	-4
5%	-5	-5	-4	-4
10%	-3	-4	-4	-3
25%	-3	-3	-3	-3
50%	-2	-2	-2	-2
75%	-1	-2	-2	-2
90%	+8	+8	+8	+9
95%	+8	+8	+8	+9
MAX	+8	+8	+8	+9

PROCESS: C PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 800 mw, 30 V, 25°C.

CELL NO.: 419254 NO. OF UNITS: 10

FRS. Min	ICBO (VCB ~ 60V) (Nanoamps)			
	Init	168	340	680
5%	0.1	0.1	0.1	0.1
10%	0.1	0.1	0.1	0.1
25%	0.1	0.1	0.1	0.1
50%	0.1	0.2	0.2	0.2
75%	0.1	0.2	0.4	0.4
90%	0.4	1.5	0.6	1.7
95%	0.4	3.7	1.8	3.3
Max	0.4	3.7	1.9	3.4

FRS. Min	IEBO (VEB ~ 5V) (Nanoamps)			
	Init	168	340	680
5%	0.1	0.7	0.3	0.1
10%	0.1	0.7	0.3	0.1
25%	0.1	0.7	0.3	0.1
50%	0.2	0.9	0.9	0.3
75%	1.3	2.4	1.7	1.4
90%	3.2	3.5	4.5	3.6
95%	5.4	4.4	8.8	8.3
Max	5.5	4.5	9.0	8.7

FRS. Min	BV _{CEO} (I _C ~ 0.1 ma) (Volts)			
	Init	168	340	680
5%	62	61	62	62
10%	62	61	62	62
25%	62	62	62	62
50%	68	68	71	70
75%	81	94	77	100
90%	129	126	138	130
95%	161	166	167	185
Max	162	169	168	188

FRS. Min	BV _{CEO} (% Change from Initial)			
	Init	168	340	680
5%	-	-49	-28	-2
10%	-	-49	-28	-2
25%	-	-44	-25	-2
50%	-	-3	+4	0
75%	-	+6	+10	+12
90%	-	+13	+16	+34
95%	-	+143	+16	+35
Max	-	+143	+16	+35

FRS. Min	VCE(SAT) (I _C ~ 50ma, I _B ~ 5 ma) (Mv.)			
	Init	168	340	680
5%	102	083	085	089
10%	102	083	085	089
25%	103	084	086	085
50%	112	092	099	100
75%	126	113	111	116
90%	147	131	130	130
95%	154	137	137	137
Max	154	138	138	135

FRS. Min	VCE(SAT) (% Change from Initial)			
	Init	168	340	680
5%	-	-19	-17	-18
10%	-	-19	-17	-18
25%	-	-19	-17	-18
50%	-	-17	-16	-14
75%	-	-13	-14	-12
90%	-	-10	-10	-9
95%	-	+1	-5	-5
Max	-	+1	-5	-5

FRS. Min	VBE(SAT) (I _C ~ 50 ma, I _B ~ 5 ma) (Mv.)			
	Init	168	340	680
5%	783	764	763	765
10%	783	764	763	765
25%	783	764	763	765
50%	785	768	769	770
75%	799	784	779	780
90%	808	791	791	790
95%	811	796	795	797
Max	811	796	795	797

FRS. Min	VBE(SAT) (% Change from Initial)			
	Init	168	340	680
5%	-	-3	-3	-3
10%	-	-3	-3	-3
25%	-	-3	-3	-3
50%	-	-2	-2	-3
75%	-	-2	-2	-2
90%	-	-2	-2	-2
95%	-	-1	-1	-1
Max	-	-1	-1	-1

FRS. Min	hFE (I _C ~ 20 ma, VCE ~ 5V)			
	Init	168	340	680
5%	51	53	43	49
10%	51	53	43	49
25%	52	54	43	50
50%	65	65	54	65
75%	89	91	61	89
90%	120	118	88	106
95%	131	133	95	118
Max	131	134	96	119

FRS. Min	hFE (% Change from Initial)			
	Init	168	340	680
5%	-	-30	-53	-28
10%	-	-30	-53	-28
25%	-	-28	-51	-26
50%	-	-1	-29	-10
75%	-	+2	-24	-6
90%	-	+3	-14	-2
95%	-	+33	-9	+16
Max	-	+36	-9	+16

FRS. Min	hFE (% Change from Initial)			
	Init	168	340	680
5%	-	-3	-3	-3
10%	-	-3	-3	-3
25%	-	-3	-3	-3
50%	-	-2	-2	-3
75%	-	-2	-2	-2
90%	-	-2	-2	-2
95%	-	-1	-1	-1
Max	-	-1	-1	-1

PROCESS: C PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 700 mw, 30 V; 25°C.

CELL NO.: 419255 NO. OF UNITS: 20

HRS.	IC _{EO} (V _{CE} - 60V) (Nanoamps)				
	Init	168	340	680	1000
Min	0.1	0.4	0.1	0.1	0.1
5%	0.1	0.4	0.1	0.1	0.1
10%	0.1	0.6	0.1	0.1	0.1
25%	0.1	0.7	0.1	0.1	0.1
50%	0.1	0.9	0.3	0.6	0.3
75%	0.2	1.7	1.3	2.2	2.5
90%	0.5	2.2	2.4	2.4	2.5
95%	1.2	3.9	3.9	3.9	4.2
Max	1.2	6.1	5.6	5.5	6.6

HRS.	IEBO (V _{EB} - 5V) (Nanoamps)				
	Init	168	340	680	1000
Min	0.1	0.3	0.1	0.1	0.1
5%	0.1	0.3	0.1	0.1	0.1
10%	0.1	0.3	0.1	0.1	0.1
25%	0.3	0.6	0.3	0.3	0.4
50%	1.1	1.7	1.1	1.2	1.3
75%	2.5	2.9	2.3	2.5	2.4
90%	3.9	4.9	4.0	3.9	3.9
95%	5.4	6.1	5.6	5.5	6.6
Max	5.5	6.2	5.7	5.4	6.7

HRS.	BV _{CEO} (I _C - 0.1 ma) (Volts)				
	Init	168	340	680	1000
Min	61	61	61	60	60
5%	62	61	61	60	62
10%	63	63	63	63	62
25%	68	67	67	68	67
50%	78	77	76	76	86
75%	101	106	97	96	92
90%	119	111	110	109	107
95%	142	138	137	137	141
Max	144	140	132	118	112

HRS.	BV _{CEO} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-24	-10	-11	-18
5%	-	-23	-10	-11	-18
10%	-	-9	-8	-8	-11
25%	-	-5	-4	-7	-7
50%	-	-1	-1	-2	-2
75%	-	0	0	-1	-1
90%	-	+22	0	+1	+6
95%	-	+108	+1	+4	+10
Max	-	+109	+1	+4	+10

HRS.	V _{CE} (SAT) (I _C -50ma, I _B -5 ma) (mv.)				
	Init	168	340	680	1000
Min	0.96	0.20	0.87	0.87	0.89
5%	0.96	0.23	0.87	0.87	0.89
10%	1.03	0.84	0.88	0.89	0.89
25%	1.09	0.93	0.95	0.96	0.97
50%	1.22	1.01	1.03	1.05	1.03
75%	1.27	1.15	1.15	1.19	1.15
90%	1.42	1.46	1.19	1.23	1.23
95%	1.62	1.48	1.52	1.49	1.51
Max	1.63	1.80	1.53	1.50	1.52

HRS.	V _{CE} (SAT) (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-83	-22	-22	-20
5%	-	-80	-22	-22	-20
10%	-	-21	-21	-19	-20
25%	-	-18	-17	-16	-14
50%	-	-13	-13	-12	-11
75%	-	-9	-9	-7	-7
90%	-	-6	-6	-2	-5
95%	-	+655	-5	-1	-4
Max	-	+690	-5	-1	-4

HRS.	V _{BE} (SAT) (I _C -50 ma, I _B -5 ma) (mv.)				
	Init	168	340	680	1000
Min	777	258	262	260	259
5%	777	258	262	260	259
10%	779	260	269	263	264
25%	783	267	270	269	268
50%	794	277	273	272	272
75%	800	286	281	283	278
90%	813	298	291	298	290
95%	823	289	297	290	289
Max	823	289	297	290	289

HRS.	V _{BE} (SAT) (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-4	-4	-4	-4
5%	-	-4	-4	-4	-4
10%	-	-4	-3	-3	-4
25%	-	-3	-3	-3	-3
50%	-	-2	-2	-2	-2
75%	-	-2	-2	-2	-2
90%	-	+13	-2	-1	-2
95%	-	+14	-1	0	-1
Max	-	+14	-1	0	-1

HRS.	hFE (I _C - 20 ma, V _{CE} - 5V)				
	Init	168	340	680	1000
Min	36	49	48	48	20
5%	36	49	49	49	20
10%	48	58	58	58	49
25%	64	67	65	69	58
50%	84	85	84	87	88
75%	91	92	100	95	104
90%	118	119	115	121	123
95%	126	123	122	126	128
Max	126	123	122	126	128

HRS.	hFE (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-6	-9	-3	-25
5%	-	-6	-9	-3	-25
10%	-	-5	-6	0	-44
25%	-	-2	-3	0	+1
50%	-	+3	+2	+2	+3
75%	-	+7	+4	+5	+7
90%	-	+120	+131	+136	+149
95%	-	+126	+137	+153	+158
Max	-	+126	+137	+153	+158

HRS.	BV _{CEO} (I _C - 0.1 ma) (Volts)				
	Init	168	340	680	1000
Min	61	61	61	60	60
5%	62	61	61	60	62
10%	63	63	63	63	62
25%	68	67	67	68	67
50%	78	77	76	76	86
75%	101	106	97	96	92
90%	119	111	110	109	107
95%	142	138	137	137	141
Max	144	140	132	118	112

HRS.	BV _{CEO} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-24	-10	-11	-18
5%	-	-23	-10	-11	-18
10%	-	-9	-8	-8	-11
25%	-	-5	-4	-7	-7
50%	-	-1	-1	-2	-2
75%	-	0	0	-1	-1
90%	-	+22	0	+1	+6
95%	-	+108	+1	+4	+10
Max	-	+109	+1	+4	+10

ACCESS: C PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 500 mw, 30 V, 25°C.

CELL NO.: 419256 NO. OF UNITS: 55

RS.	ICBO (V _{CB} - 60V)(Nanamps)			
	Init	168	340	580
1	0.1	0.4	0.2	0.1
2	0.1	0.5	0.8	0.1
3	0.1	0.5	1.0	0.1
4	0.1	0.7	1.0	0.3
5	0.1	0.9	1.3	0.5
6	0.4	1.7	1.7	1.2
7	0.6	3.4	4.3	3.2
8	1.1	10.4	21.7	21.9
9	1.2	∞	∞	∞

RS.	I _{CEO} (V _{EB} - 5V)(Nanamps)			
	Init	168	340	580
1	0.1	0.1	0.2	0.1
2	0.1	0.2	0.3	0.1
3	0.1	0.3	0.3	0.1
4	0.2	0.4	0.5	0.1
5	0.5	1.2	0.9	0.6
6	1.6	2.8	2.5	1.9
7	5.1	6.5	6.0	5.9
8	7.1	8.1	7.5	7.4
9	7.2	12.8	14.1	16.5

RS.	BV _{CEO} (I _C - 0.1 ma)(Volts)			
	Init	168	340	580
1	53	54	52	51
2	58	59	54	54
3	63	61	61	59
4	71	70	71	71
5	78	82	80	81
6	97	99	99	99
7	130	133	132	131
8	149	143	143	141
9	156	153	147	145

RS.	BV _{CEO} (% Change from Initial)			
	Init	168	340	580
1	-	-94	-45	-99
2	-	-5	-6	-44
3	-	-3	-3	-6
4	-	-1	-1	-2
5	-	0	0	0
6	-	+4	+10	+14
7	-	+18	+20	+28
8	-	+26	+23	+51

RS.	V _{CE} (SAT)(I _C -50ma, I _B -5 ma)(Mv.)			
	Init	168	340	580
1	103	83	85	85
2	105	87	87	89
3	107	89	89	89
4	112	94	96	98
5	122	104	105	107
6	136	116	117	117
7	148	132	133	133
8	157	135	141	144
9	203	147	142	152

RS.	V _{CE} (SAT) (% Change from Initial)			
	Init	168	340	580
1	-	-22	-22	-22
2	-	-24	-20	-23
3	-	-19	-17	-18
4	-	-17	-15	-15
5	-	-14	-14	-12
6	-	-11	-11	-9
7	-	-9	-9	-9
8	-	-9	-7	-4
9	-	-7	+10	+8

RS.	V _{BE} (SAT)(I _C -50 ma, I _B -5 ma)(Mv.)			
	Init	168	340	580
1	778	684	610	660
2	782	759	760	762
3	785	764	766	765
4	789	789	769	769
5	797	775	777	777
6	803	785	785	784
7	811	790	794	795
8	821	798	797	800
9	956	813	814	813

RS.	V _{BE} (SAT) (% Change from Initial)			
	Init	168	340	580
1	-	-25	-99	-19
2	-	-9	-3	-4
3	-	-3	-3	-3
4	-	-3	-3	-3
5	-	-2	-2	-2
6	-	-2	-2	-2
7	-	-2	-2	-2
8	-	-2	-2	-2
9	-	-2	-1	+1

RS.	h _{FE} (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	580
1	52	53	20	53
2	56	57	55	57
3	60	63	60	63
4	68	71	70	68
5	79	87	80	82
6	102	100	95	101
7	119	115	111	116
8	126	126	128	127
9	140	141	139	141

RS.	h _{FE} (% Change from Initial)			
	Init	168	340	580
1	-	-31	-84	-48
2	-	-6	-22	-12
3	-	-3	-11	-3
4	-	0	-6	-1
5	-	+2	+1	0
6	-	+3	+3	+2
7	-	+8	+30	+9
8	-	+14	+100	+107

RS.	BV _{CEO} (I _C - 0.1 ma)(Volts)			
	Init	168	340	580
1	53	54	52	51
2	58	59	54	54
3	63	61	61	59
4	71	70	71	71
5	78	82	80	81
6	97	99	99	99
7	130	133	132	131
8	149	143	143	141
9	156	153	147	145

RS.	BV _{CEO} (% Change from Initial)			
	Init	168	340	580
1	-	-94	-45	-99
2	-	-5	-6	-44
3	-	-3	-3	-6
4	-	-1	-1	-2
5	-	0	0	0
6	-	+4	+10	+14
7	-	+18	+20	+28
8	-	+26	+23	+51

PROCESS: C PRE-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 400 mw, 30 V, 150°C.

CELL NO.: 419257 NO. OF UNITS: 10

IRS.	ICEO (V _{CE} - 60V) (Nanamps)			
	Init	168	340	580
4in	0.1	0.6	0.2	0.1
5%	0.1	0.6	0.2	0.1
10%	0.1	0.6	0.2	0.1
20%	0.1	0.6	0.2	0.1
30%	0.1	0.6	0.2	0.1
40%	0.1	0.6	0.2	0.1
50%	0.1	0.6	0.2	0.1
60%	0.1	0.6	0.2	0.1
70%	0.1	0.6	0.2	0.1
80%	0.1	0.6	0.2	0.1
90%	0.1	0.6	0.2	0.1
100%	0.1	0.6	0.2	0.1

IRS.	IEBO (V _{EB} - 5V) (Nanamps)			
	Init	168	340	580
4in	0.1	0.7	0.2	0.2
5%	0.1	0.7	0.2	0.2
10%	0.1	0.7	0.2	0.2
20%	0.1	0.7	0.2	0.2
30%	0.1	0.7	0.2	0.2
40%	0.1	0.7	0.2	0.2
50%	0.1	0.7	0.2	0.2
60%	0.1	0.7	0.2	0.2
70%	0.1	0.7	0.2	0.2
80%	0.1	0.7	0.2	0.2
90%	0.1	0.7	0.2	0.2
100%	0.1	0.7	0.2	0.2

IRS.	BV _{CEO} (I _C - 0.1 ma) (Volts)			
	Init	168	340	580
4in	71	0.7	0.7	0.7
5%	71	0.7	0.7	0.7
10%	72	1.0	1.3	1.3
20%	84	6.3	2.4	2.5
30%	91	3.4	3.8	3.7
40%	113	4.5	1.4	1.4
50%	147	11.2	1.6	1.5
60%	151	11.3	1.6	1.5
70%	151	11.3	1.6	1.5

IRS.	BV _{CEO} (% Change from Initial)			
	Init	168	340	580
4in	-	-96	-95	-95
5%	-	-96	-95	-95
10%	-	-92	-87	-78
20%	-	-23	-7	-8
30%	-	+1	+4	+1
40%	-	+8	+4	+3
50%	-	+8	+4	+3
60%	-	+8	+4	+3
70%	-	+8	+4	+3
80%	-	+8	+4	+3
90%	-	+8	+4	+3
100%	-	+8	+4	+3

IRS.	VCE (SAT) (I _C - 50ma, I _B - 5 ma) (mv.)			
	Init	168	340	580
4in	100	004	019	095
5%	100	004	019	095
10%	101	013	090	095
20%	110	097	096	099
30%	122	106	107	109
40%	133	116	120	121
50%	139	131	128	132
60%	139	132	129	133
70%	139	132	129	133

IRS.	VCE (SAT) (% Change from Initial)			
	Init	168	340	580
4in	-	-96	-16	-13
5%	-	-96	-16	-13
10%	-	-88	-16	-13
20%	-	-14	-13	-13
30%	-	-12	-11	-9
40%	-	-9	-9	-8
50%	-	-5	-7	-4
60%	-	-5	-7	-4
70%	-	-5	-7	-4

IRS.	VBE (SAT) (I _C - 50 ma, I _B - 5 ma) (mv.)			
	Init	168	340	580
4in	779	618	266	269
5%	779	618	266	269
10%	779	633	266	269
20%	783	721	272	274
30%	796	780	280	282
40%	799	784	285	285
50%	805	794	286	286
60%	805	794	287	287
70%	805	794	287	287

IRS.	VBE (SAT) (% Change from Initial)			
	Init	168	340	580
4in	-	-21	-2	-3
5%	-	-21	-2	-3
10%	-	-19	-2	-3
20%	-	-3	-2	-2
30%	-	-2	-1	-1
40%	-	-1	-1	-1
50%	-	-1	-1	-1
60%	-	-1	-1	-1
70%	-	-1	-1	-1

IRS.	hFE (I _C - 20 ma, V _{CE} - 5V)			
	Init	168	340	580
4in	41	49	40	32
5%	41	49	40	32
10%	42	50	41	33
20%	63	65	56	50
30%	81	82	77	77
40%	111	113	106	101
50%	129	130	124	120
60%	131	131	126	122
70%	131	131	126	122

IRS.	hFE (% Change from Initial)			
	Init	168	340	580
4in	-	-6	-24	-40
5%	-	-6	-24	-40
10%	-	-5	-23	-39
20%	-	0	-9	-16
30%	-	+1	-5	-8
40%	-	+4	-3	-5
50%	-	+30	+22	+18
60%	-	+33	+15	+19
70%	-	+33	+15	+19

IRS.	hFE (I _C - 0.1 ma) (Volts)			
	Init	168	340	580
4in	71	0.7	0.7	0.7
5%	71	0.7	0.7	0.7
10%	72	1.0	1.3	1.3
20%	84	6.3	2.4	2.5
30%	91	3.4	3.8	3.7
40%	113	4.5	1.4	1.4
50%	147	11.2	1.6	1.5
60%	151	11.3	1.6	1.5
70%	151	11.3	1.6	1.5

IRS.	hFE (% Change from Initial)			
	Init	168	340	580
4in	-	-96	-95	-95
5%	-	-96	-95	-95
10%	-	-92	-87	-78
20%	-	-23	-7	-8
30%	-	+1	+4	+1
40%	-	+8	+4	+3
50%	-	+8	+4	+3
60%	-	+8	+4	+3
70%	-	+8	+4	+3

PROCESS: C PMS-SCREEN STRESS: None (Control).

OPERATING POWER CONDITION: 200 mw, 30 V, 150°C.

CELL NO.: 419258 NO. OF UNITS: 19

ERS.	IC60 (V _{CS} = 60V) (Microamps)				
	Init	168	340	680	1000
Min	0.1	0.1	0.1	0.1	0.1
5%	0.1	0.1	0.1	0.1	0.1
10%	0.1	0.1	0.1	0.1	0.1
25%	0.1	0.1	0.1	0.1	0.1
50%	0.2	0.2	0.2	0.2	0.2
75%	0.6	1.5	1.5	1.8	1.6
90%	1.9	2.1	2.9	4.7	4.6
95%	5.8	7.0	7.3	7.2	7.7
Max	5.8	7.0	7.3	7.2	7.7

ERS.	IE60 (V _{EB} = 5V) (Microamps)				
	Init	168	340	680	1000
Min	0.1	0.1	0.1	0.1	0.1
5%	0.1	0.1	0.1	0.1	0.1
10%	0.1	0.1	0.1	0.1	0.1
25%	0.3	0.6	0.1	0.1	0.2
50%	0.9	1.9	1.2	1.1	0.8
75%	4.6	5.1	4.0	2.5	2.9
90%	6.9	7.9	7.1	7.4	6.9
95%	7.8	8.0	7.3	7.6	7.2
Max	7.8	8.0	7.3	7.6	7.2

ERS.	BV _{CFO} (IC = 0.1 ma.) (Volts)				
	Init	168	340	680	1000
Min	63	62	62	62	61
5%	63	62	62	62	61
10%	68	65	65	62	61
25%	71	70	70	68	67
50%	79	74	73	73	72
75%	100	89	82	82	85
90%	133	127	126	125	125
95%	137	134	131	129	126
Max	137	134	131	129	126

ERS.	BV _{CFO} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-42	-40	-44	-48
5%	-	-42	-40	-44	-48
10%	-	-6	-7	-10	-12
25%	-	-3	-4	-6	-7
50%	-	-1	-2	-2	-3
75%	-	0	0	-1	-1
90%	-	0	0	0	-1
95%	-	+1	+1	0	0
Max	-	+1	+1	0	0

ERS.	VCE (SAT) (IC = 50 ma., I _B = 5 ma.) (Mv.)				
	Init	168	340	680	1000
Min	107	104	103	104	103
5%	107	104	103	103	102
10%	109	109	109	109	108
25%	114	105	105	107	107
50%	119	103	104	101	103
75%	135	114	110	118	113
90%	144	128	125	123	125
95%	154	134	135	133	131
Max	154	134	135	133	131

ERS.	VCE (SAT) (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-8	-24	-24	-24
5%	-	-8	-24	-24	-24
10%	-	-24	-22	-23	-22
25%	-	-17	-18	-17	-18
50%	-	-15	-13	-15	-13
75%	-	-11	-12	-11	-10
90%	-	-8	-8	-11	-8
95%	-	-7	-4	-6	-6
Max	-	-7	-4	-6	-6

ERS.	VBE (SAT) (IC = 50 ma., I _B = 5 ma.) (Mv.)				
	Init	168	340	680	1000
Min	782	698	767	765	770
5%	782	698	767	765	770
10%	784	766	770	767	765
25%	787	770	773	775	771
50%	793	775	777	777	773
75%	799	783	784	784	782
90%	803	786	787	785	783
95%	811	786	787	785	784
Max	811	786	787	785	784

ERS.	VBE (SAT) (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-12	-4	-4	-5
5%	-	-12	-4	-4	-5
10%	-	-4	-3	-3	-4
25%	-	-3	-3	-2	-3
50%	-	-2	-2	-2	-2
75%	-	-2	-2	-1	-2
90%	-	-1	-1	-1	-2
95%	-	0	0	0	-1
Max	-	0	0	0	-1

ERS.	hFE (IC = 20 ma., V _{CE} = 5V)				
	Init	168	340	680	1000
Min	35	54	54	52	53
5%	35	54	54	52	53
10%	54	54	55	55	55
25%	58	60	60	57	60
50%	80	79	76	77	78
75%	104	107	104	107	110
90%	120	116	114	110	119
95%	120	121	120	114	120
Max	120	121	120	114	120

ERS.	hFE (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-7	-14	-9	-6
5%	-	-7	-14	-9	-6
10%	-	-3	-7	-8	-5
25%	-	-1	-1	-6	-3
50%	-	0	+1	-5	-2
75%	-	+2	+2	-1	+1
90%	-	+39	+41	+56	+59
95%	-	+56	+56	+58	+66
Max	-	+56	+56	+58	+66

ERS.	BV _{CEO} (% Change from Initial)				
	Init	168	340	680	1000
Min	-	-	-	-	-
5%	-	-	-	-	-
10%	-	-	-	-	-
25%	-	-	-	-	-
50%	-	-	-	-	-
75%	-	-	-	-	-
90%	-	-	-	-	-
95%	-	-	-	-	-
Max	-	-	-	-	-